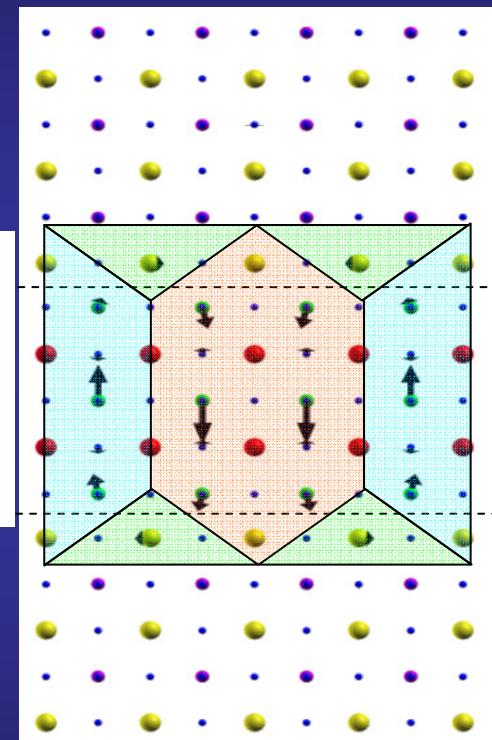
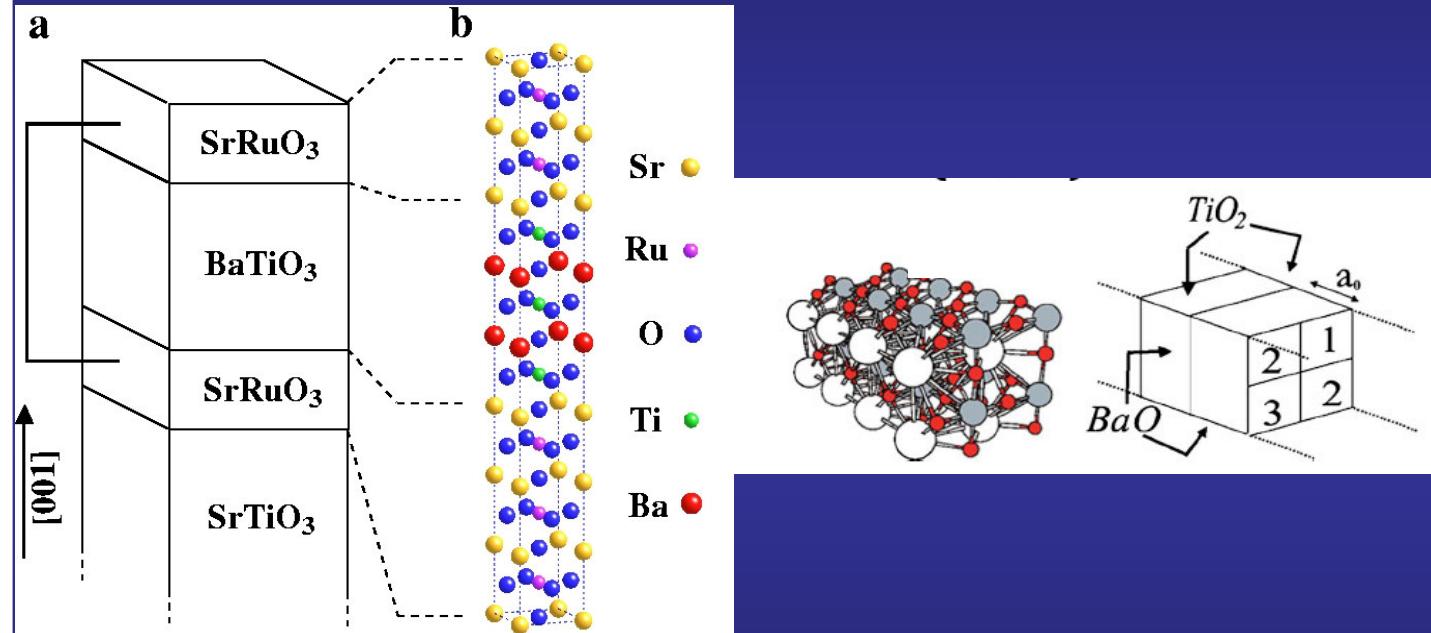


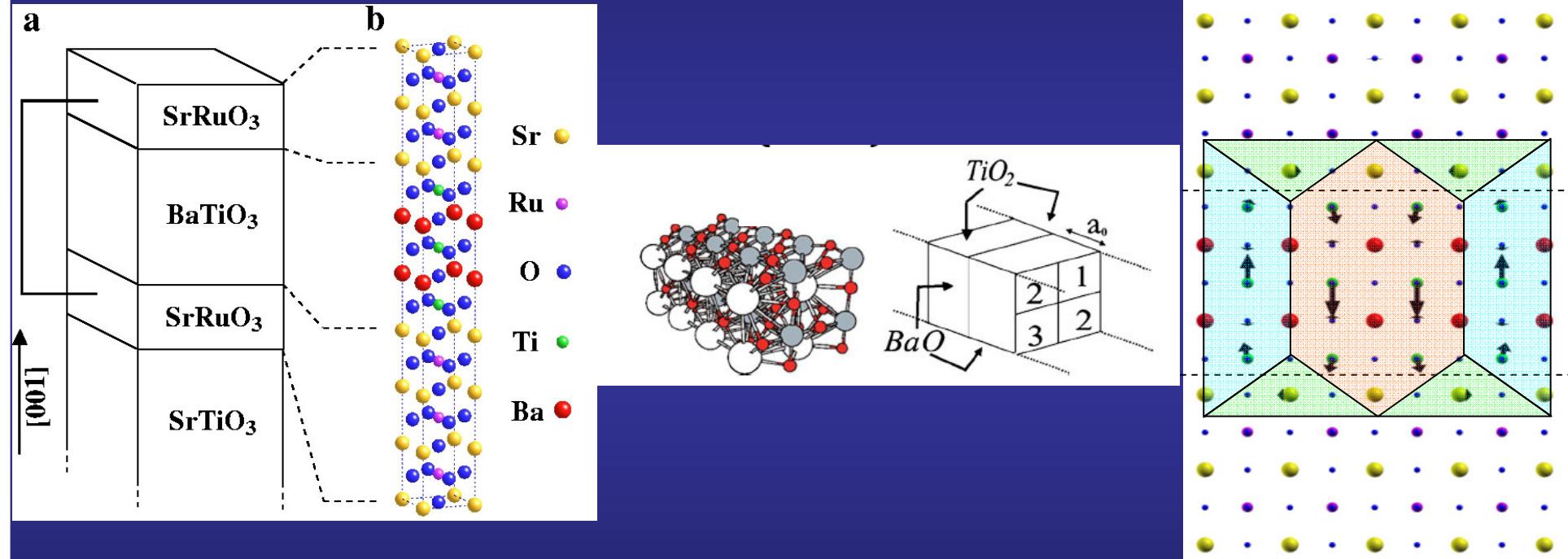
First-principles modeling of ferroelectric oxide nanostructures



Javier Junquera



First-principles modeling of ferroelectric oxide nanostructures



Javier Junquera



Transition metal oxide compounds

Simple structures with different phase transitions

Insulating

Semi-conducting

OXIDES

Metallic

Superconducting

Transition metal oxide compounds

Simple structures with different fundamental properties

Ferroelectricity

**High T_c
superconductivity**

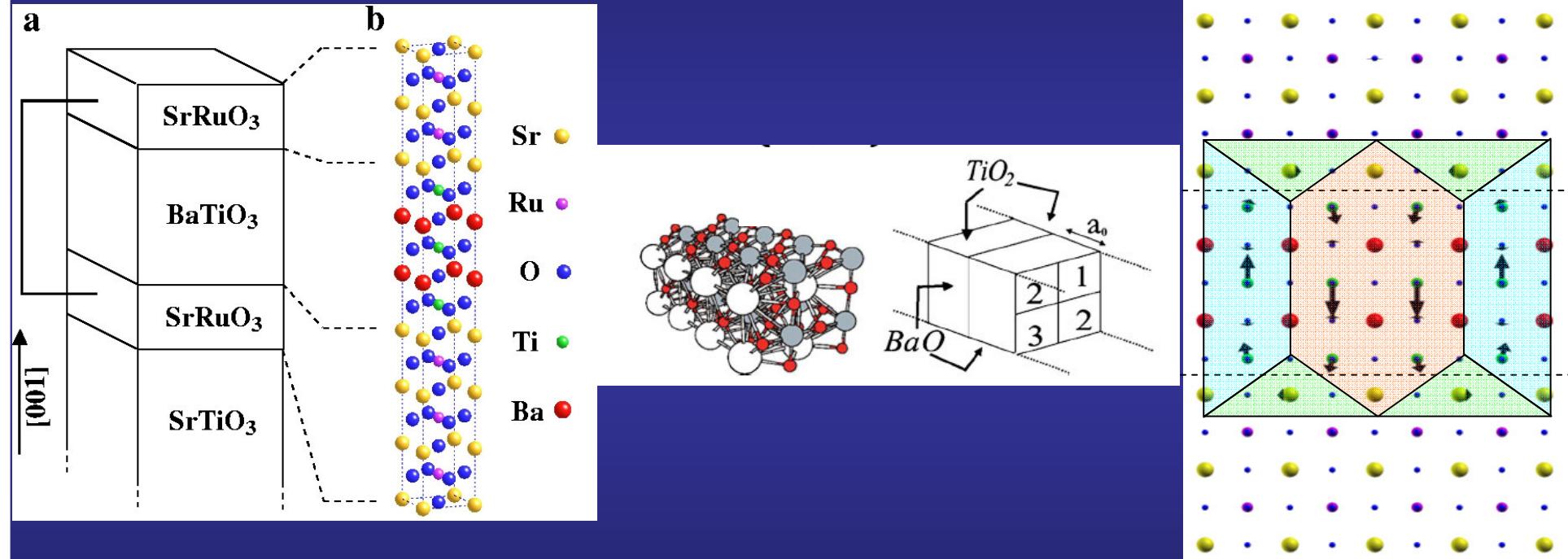
Ferromagnetism

OXIDES

**Colossal
magnetoresistance**

Multiferroics

First-principles modeling of ferroelectric oxide nanostructures



Javier Junquera



Atomically precise methods for preparing thin films and multilayer structures

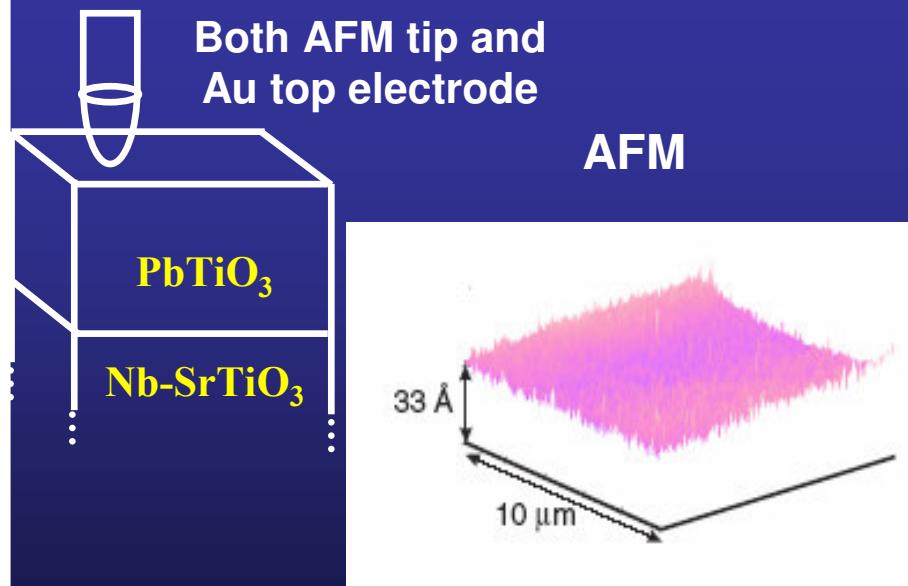
Methods

Pulsed Laser Deposition (PLD)

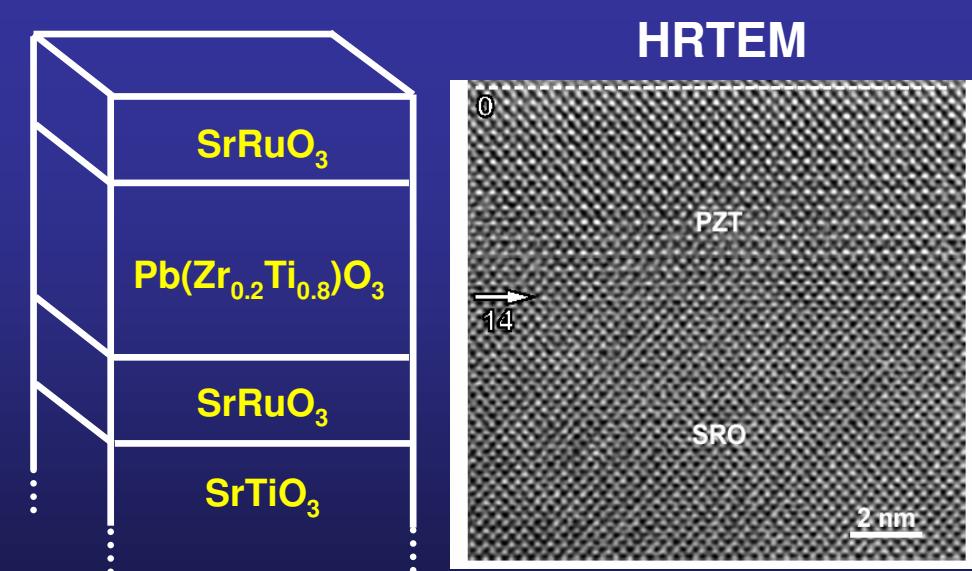
Molecular Beam Epitaxy (MBE)

Off-axis rf magnetron sputtering

→ Control at the atomic level
Crystalline and surface quality ≈ semiconductor heterostructures



C. Lichtensteiger *et al.*,
Phys. Rev. Lett. 94, 047603 (2005)



V. Nagarajan, J. Junquera *et al.*,
J. Appl. Phys. 100, 051609 (2006)

Accurate characterization methods

Methods

X-ray scattering

analysis of satellites

COBRA

**High resolution Transmission
Electron Microscopy (HRTEM)**

**Reflection High-energy Electron
Diffraction (RHEED)**

Atomic Force Microscopy (AFM)

Piezoelectric Force Microscopy (PFM)

**Photoemission based photoelectron
diffraction (XPD)**

PUND Hysteresis loops

...

Results

High (atomic) resolution

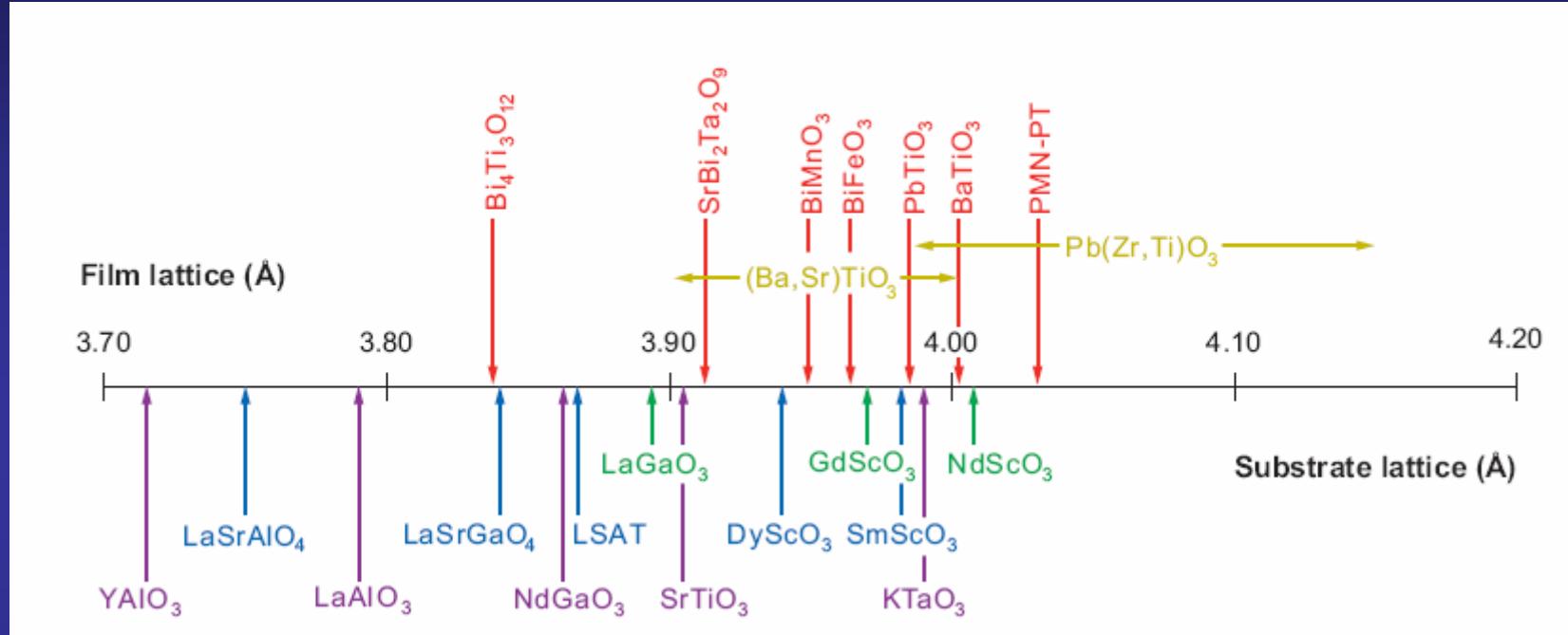
Local proofs of:

atomic structure

piezoelectric properties

ferroelectric properties

Many oxides have similar lattice constants allowing for a good match at the interfaces



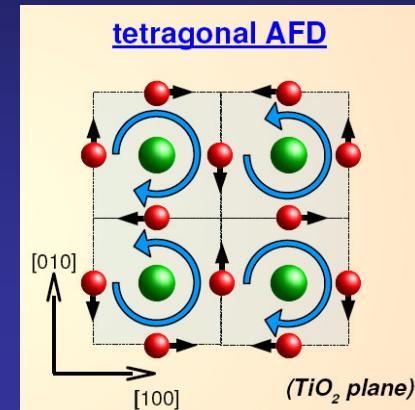
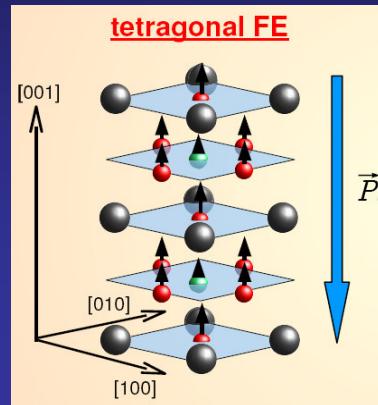
D. G. Schlom *et al.*, Annu. Rev. Mater. Res. 37, 589 (2007)

What would happen if we could mix materials with different properties?

Potential for novel behaviour

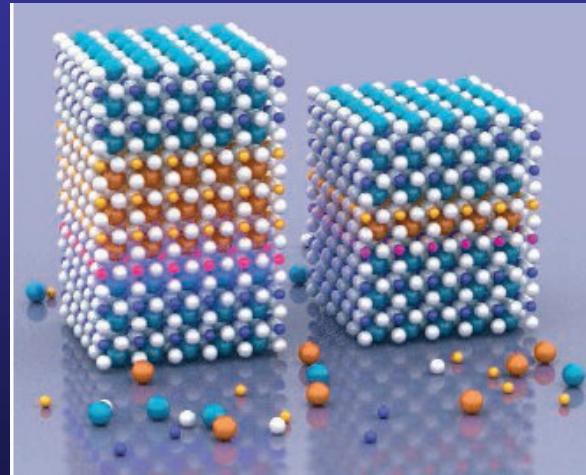
Some surprises at the interfaces between two oxides

New type of ferroelectricity in $\text{PbTiO}_3/\text{SrTiO}_3$ superlattices



E. Bousquet *et al.*, Nature (in press)

The interface between two good insulators (LaAlO_3 and SrTiO_3) is metallic



A. Ohtomo and H. Y. Hwang, Nature 427, 423 (2004)

Recent discoveries on transition metal oxides: one of the “top tens” scientific breakthroughs of 2007

Breakthrough of the Year

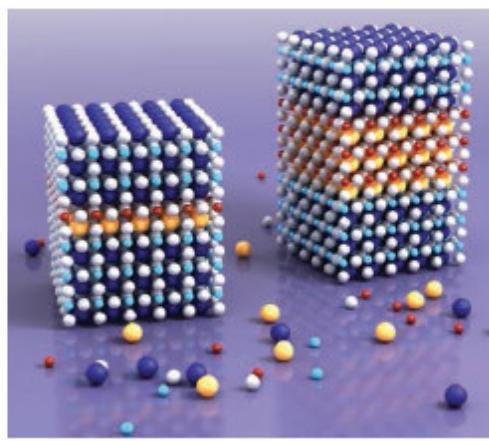
5

BEYOND SILICON? Sixty years ago, semiconductors were a scientific curiosity. Then researchers tried putting one type of semiconductor up against another, and suddenly we had diodes, transistors, microprocessors, and the whole electronic age. Startling results this year may herald a similar burst of discoveries at the interfaces of a different class of materials: transition metal oxides.

Transition metal oxides first made headlines in 1986 with the Nobel Prize-winning discovery of high-temperature superconductors. Since then, solid-state physicists keep finding unexpected properties in these materials—including colossal magnetoresistance, in which small changes in applied magnetic fields cause huge changes in electrical resistance. But the fun should really start when one oxide rubs shoulders with another.

If different oxide crystals are grown in layers with sharp interfaces, the effect of one crystal structure on another can shift the positions of atoms at the interface, alter the population of electrons, and even change how

Tunable sandwich. In lanthanum aluminate sandwiched between layers of strontium titanate, a thick middle layer (*right*) produces conduction at the lower interface; a thin one does not.



Science, 318, 1846 (2007)

**The field is still in an incipient stage,
comparable to that of semiconductors 60 years ago**

PERSPECTIVES

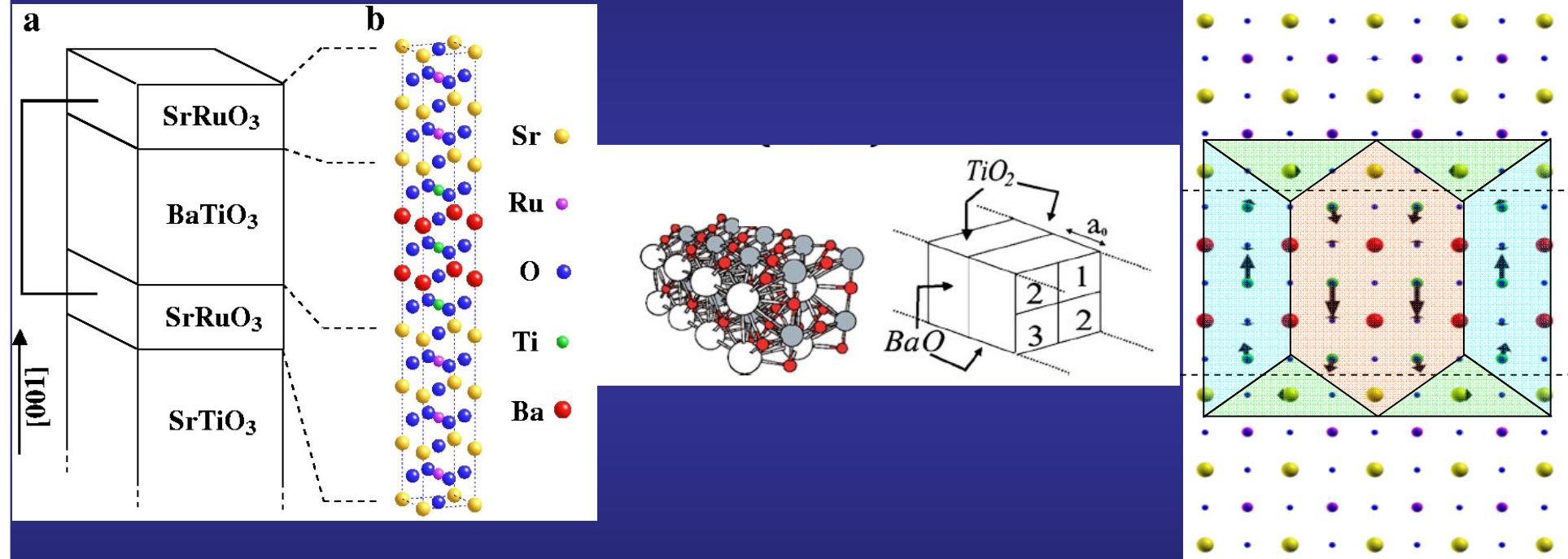
PHYSICS

When Oxides Meet Face to Face

Elbio Dagotto

Despite recent activity, the field of oxide interfaces remains virtually unexplored. What might happen if we could mix materials with vastly different properties such as ferromagnets, antiferromagnets, superconductors, ferroelectrics, multiferroics, geometrically frustrated spin systems, heavy fermions, and others? Considering this enormous number of

First-principles modeling of ferroelectric oxide nanostructures



Javier Junquera

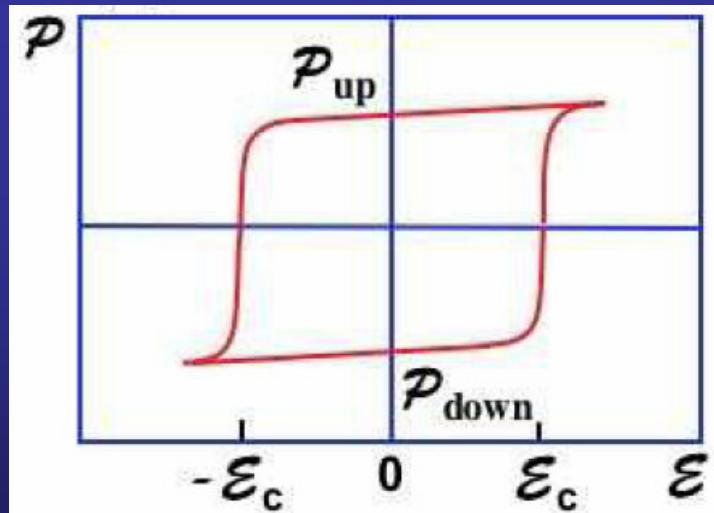


Ferroelectricity: Basic definitions

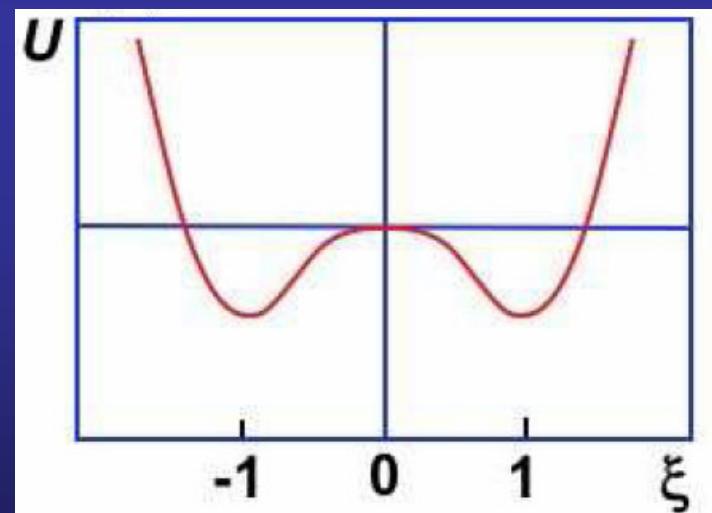
Existence of **two or more states** with a **non-zero polarization** in the **absence** of an electric field

Can be **shifted** from one to another of these states by the application of an electric field

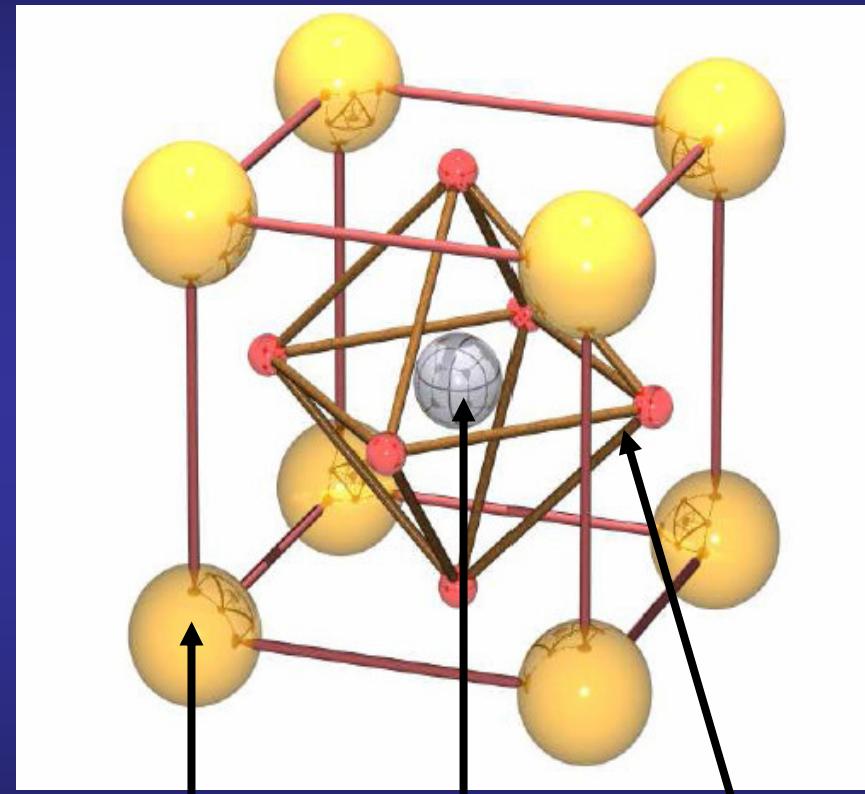
Hysteresis loop



Double well energy



Perovskite oxides ABO_3 : prototypes of ferroelectric materials

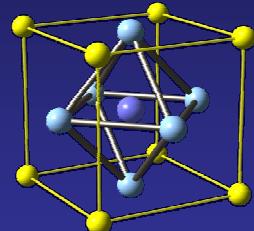


First ferroelectric without hydrogen bonds
First ferroelectric with a paraelectric phase
First ferroelectric with more than one ferroelectric phase
Very simple (5 atoms per unit cell)
⇒ lot of theoretical models

Phase transitions of BaTiO_3 as a function of the temperature

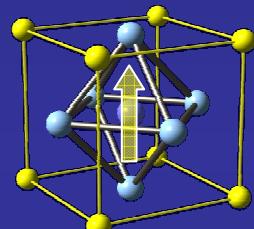


High T



Cubic

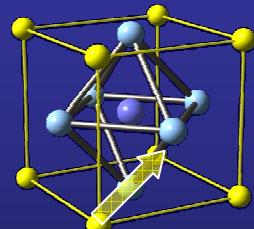
130 °C



Tetragonal

P along [001]

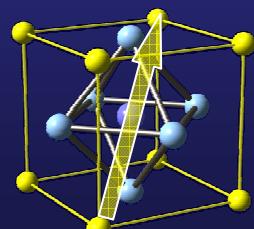
5 °C



Orthorhombic

P along [110]

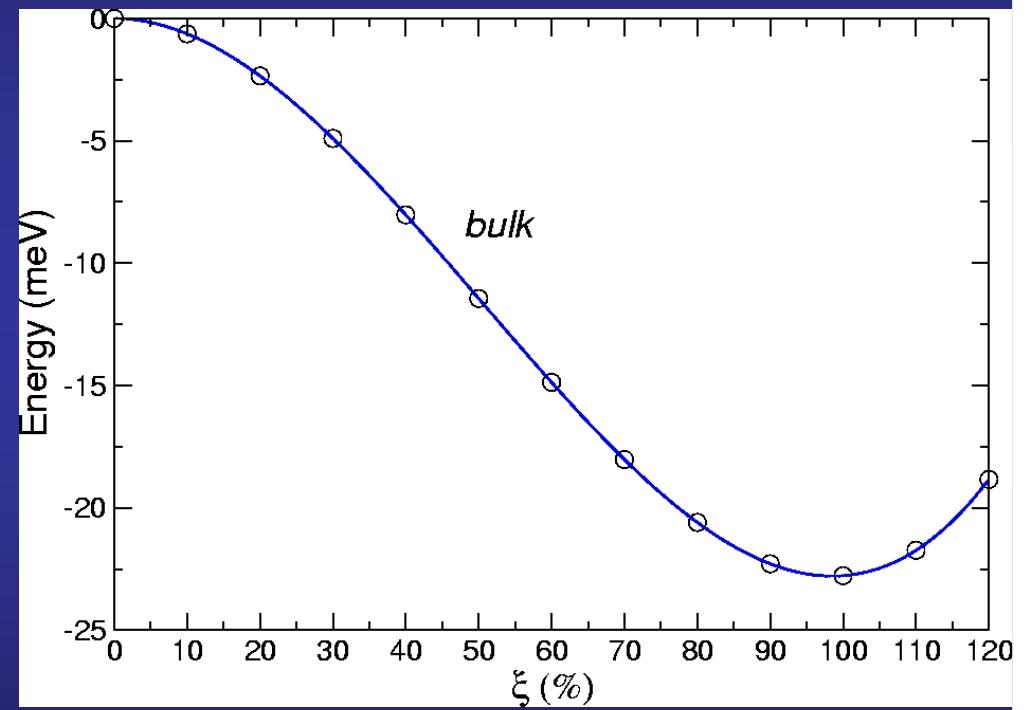
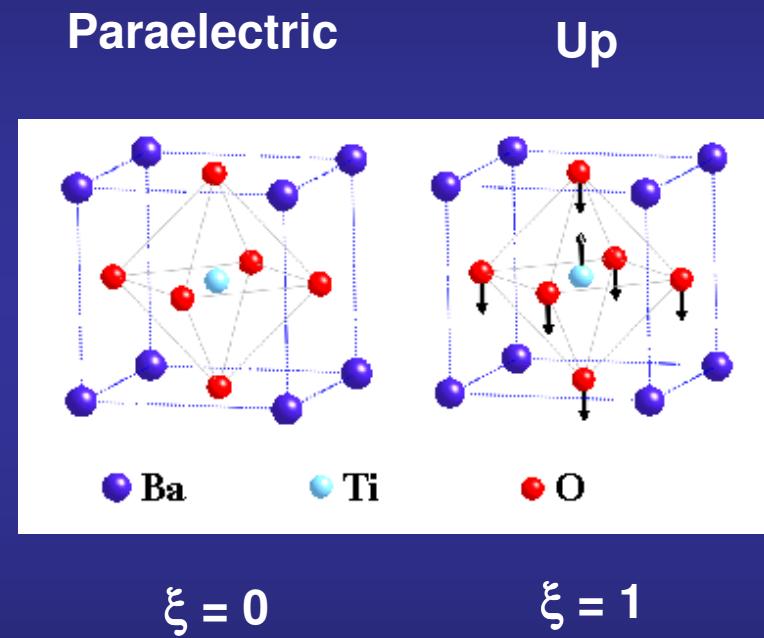
-90 °C



Rhombohedral

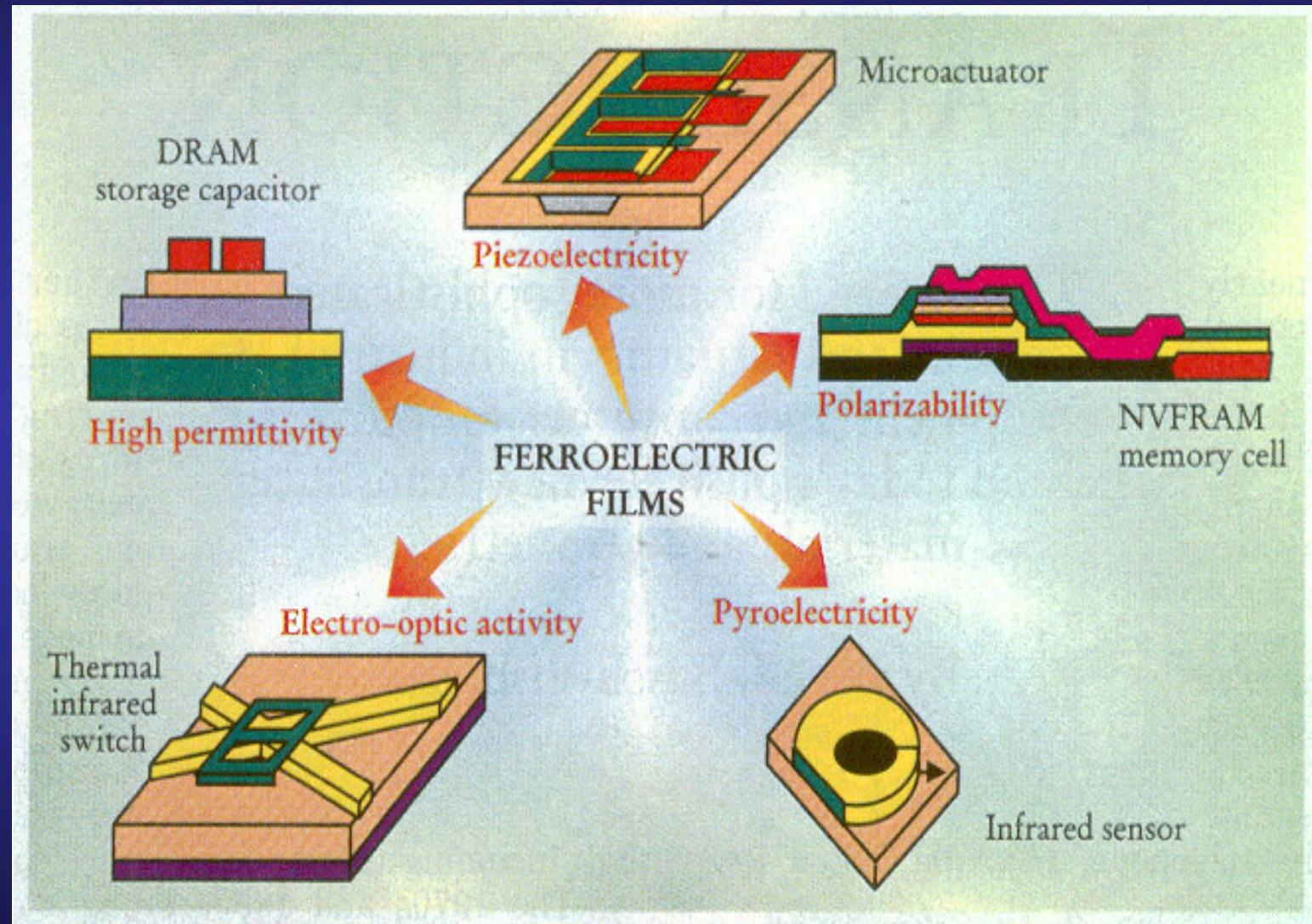
P along [111]

Phase transitions from cubic to tetragonal, pattern of cooperative polar atomic displacements



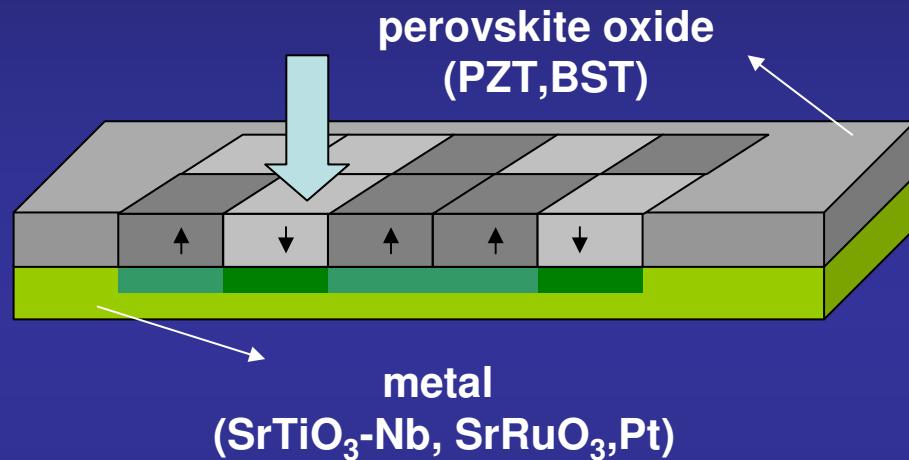
Continuum evolution of ξ

Technological applications: ABO_3 perovskites oxides as multifunctional materials

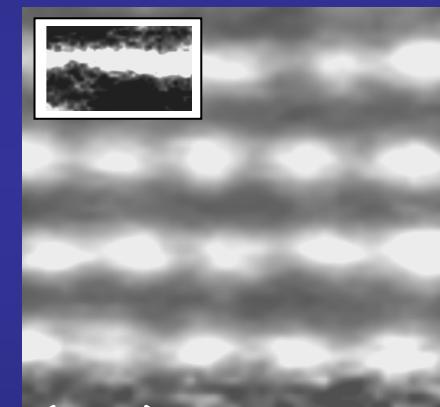


Many applications depend on the stability of films with a switchable polarization along the film normal

NV-FRAM



28 Gbit/cm²
Line width < 20nm

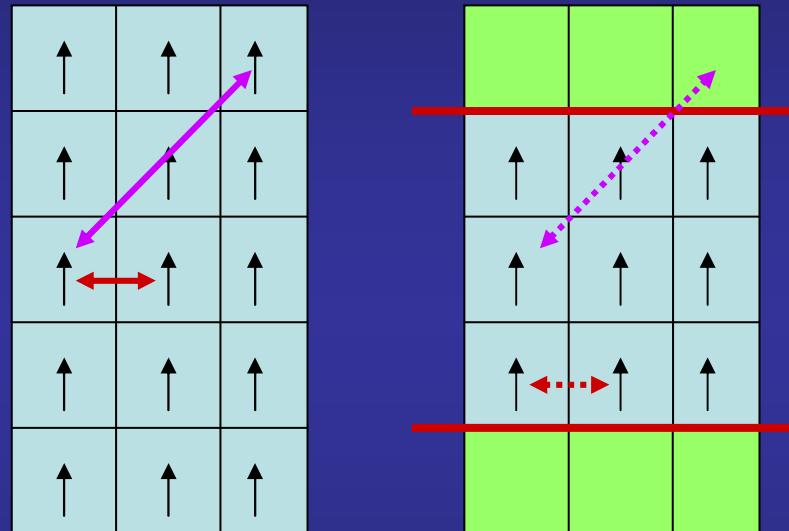


100 nm



... is there a fundamental limit?

Ferroelectricity is a collective effect with delicate balance between short and long range interactions

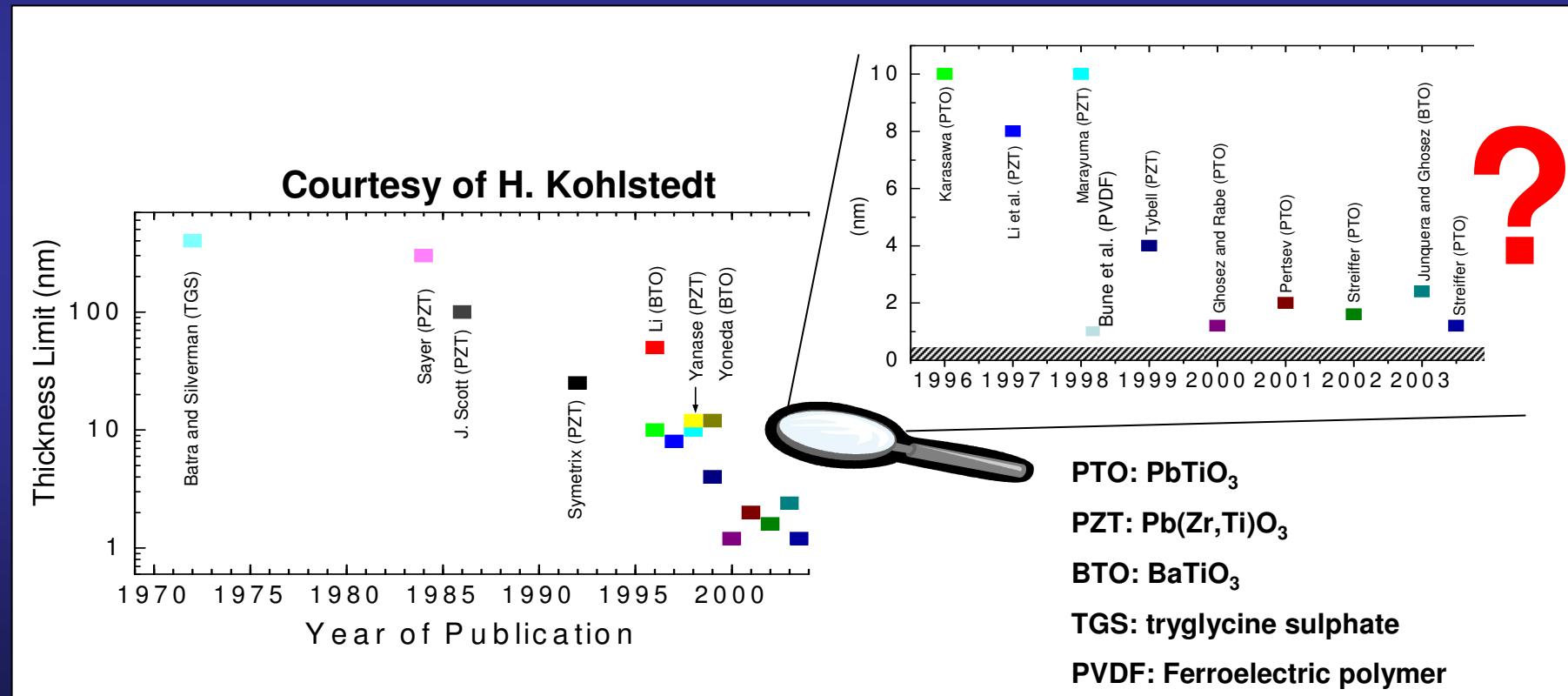


Both interactions strongly affected in small particles and thin films

Finite size effect: a subtle problem

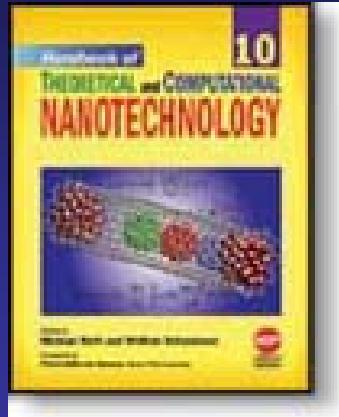
Fundamental motivation: what's the most stable phase for epitaxial ferroelectric ultrathin films?

- Long time question.
- Hot field.



A few unit cells might be ferroelectric!

Recent reviews on state-of-the-art on size effects in ferroelectric nanostructures



Ph. Ghosez and J. Junquera, *First-Principles Modeling of Ferroelectric Oxide Nanostructures*, *Handbook of Theoretical and Computational Nanotechnology*, Vol. 9, Chap. 13, 623-728 (2006)
(<http://xxx.lanl.gov/pdf/cond-mat/0605299>)

First-principles study of ferroelectric oxide epitaxial thin films and superlattices: role of the mechanical and electrical boundary conditions

Javier Junquera

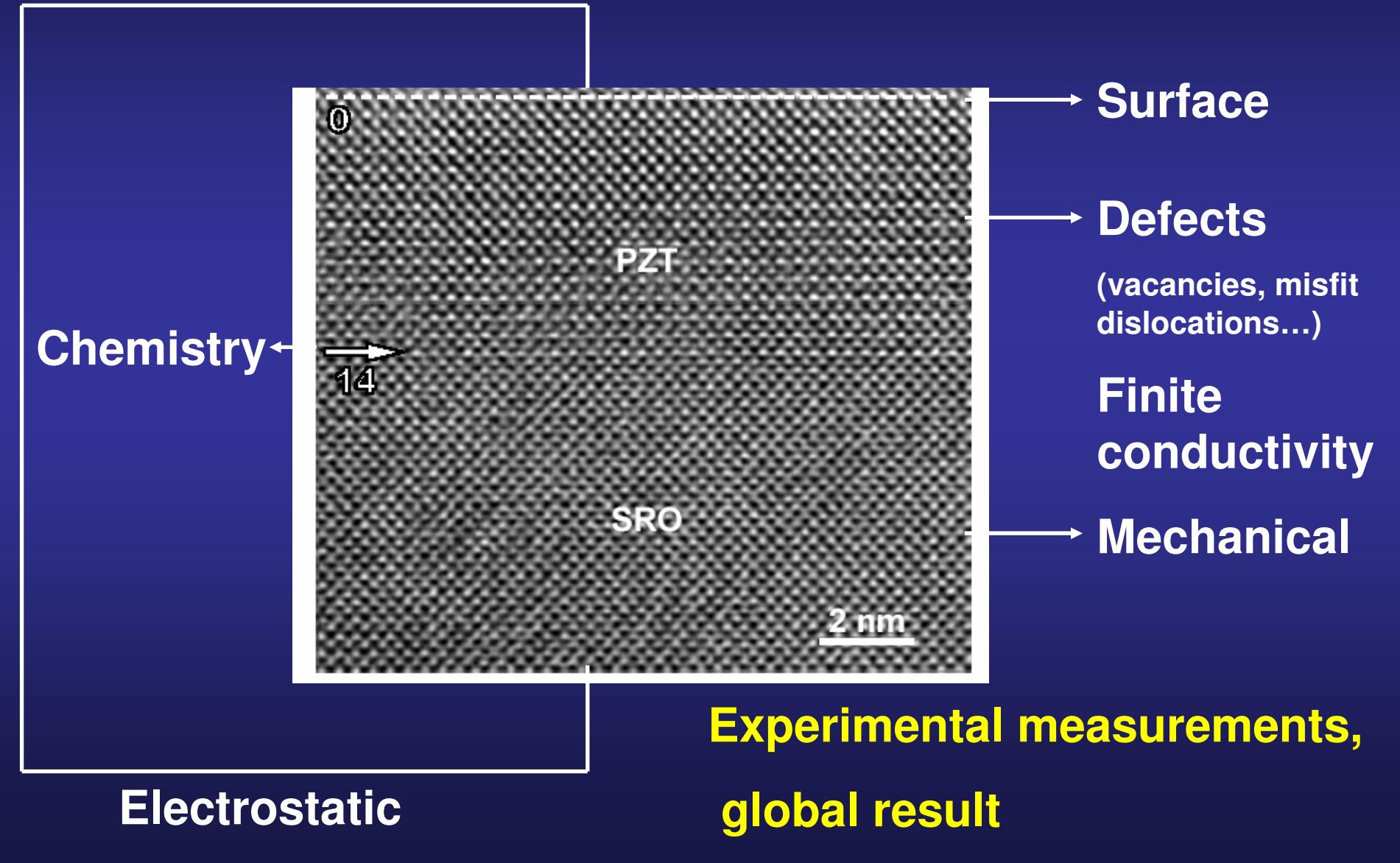
*Departamento de Ciencias de la Tierra y Física de la Materia Condensada,
Universidad de Cantabria, Avda. de los Castros s/n, E-39005 Santander, Spain*

Philippe Ghosez

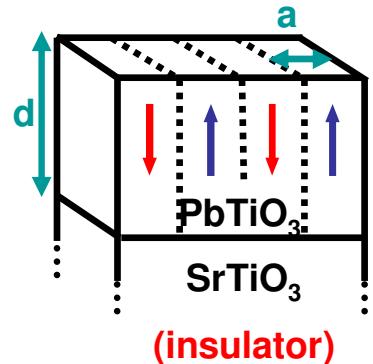
Physique Théorique des Matériaux, Université de Liège, B-4000 Sart Tilman, Belgium

arXiv:0711.4201v1 [cond-mat.mtrl-sci] 27 Nov 2007

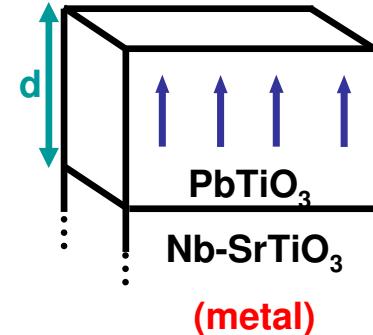
**Many effects might alter the delicate balance
between long and short range forces**



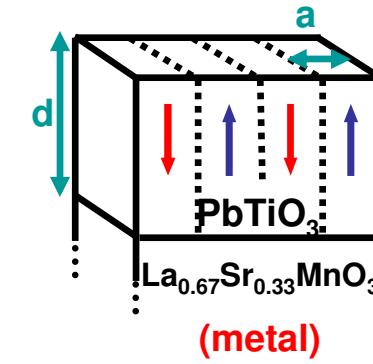
Experimentally: small changes in boundary conditions, great changes in stable state



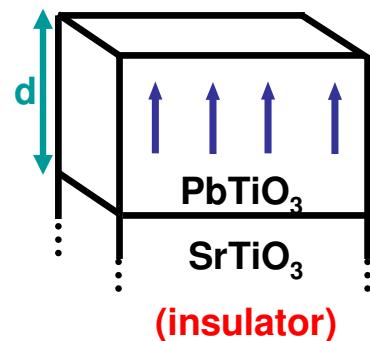
D. D. Fong et al. (2004)
S. K. Streiffer et al. (2002)



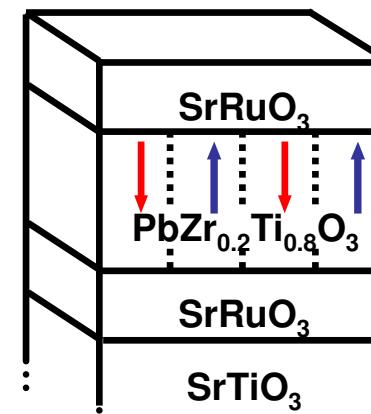
C. Lichtensteiger et al. (2005)
A. T. J. van Helvoort et al. (2005)



C. Lichtensteiger et al. (2007)

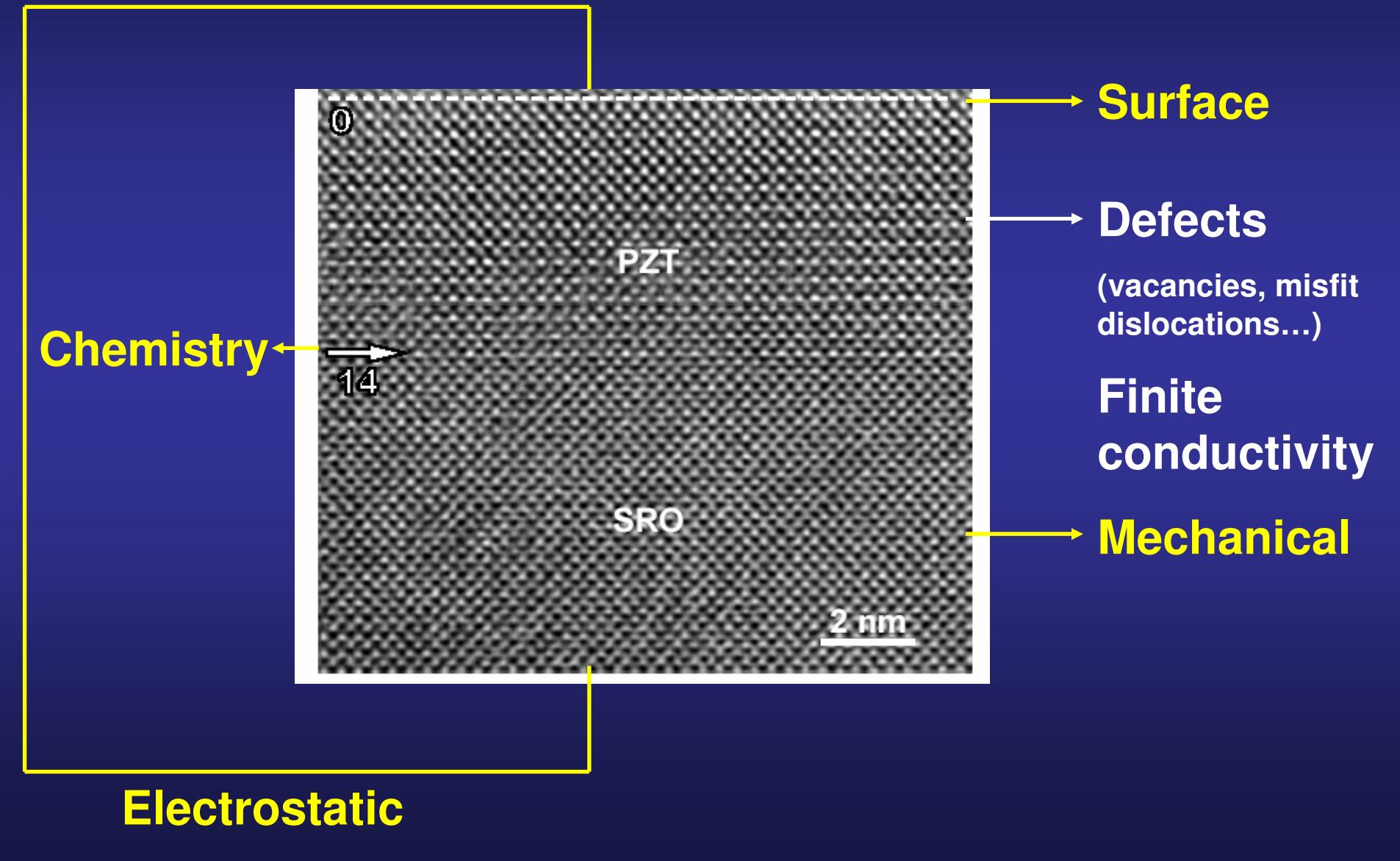


D. D. Fong et al. (2005)



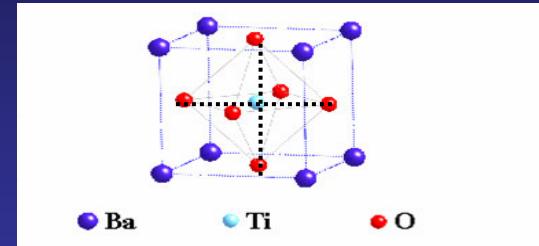
V. Nagarajan et al. (2006)

First-principles calculations allow to isolate their respective influence

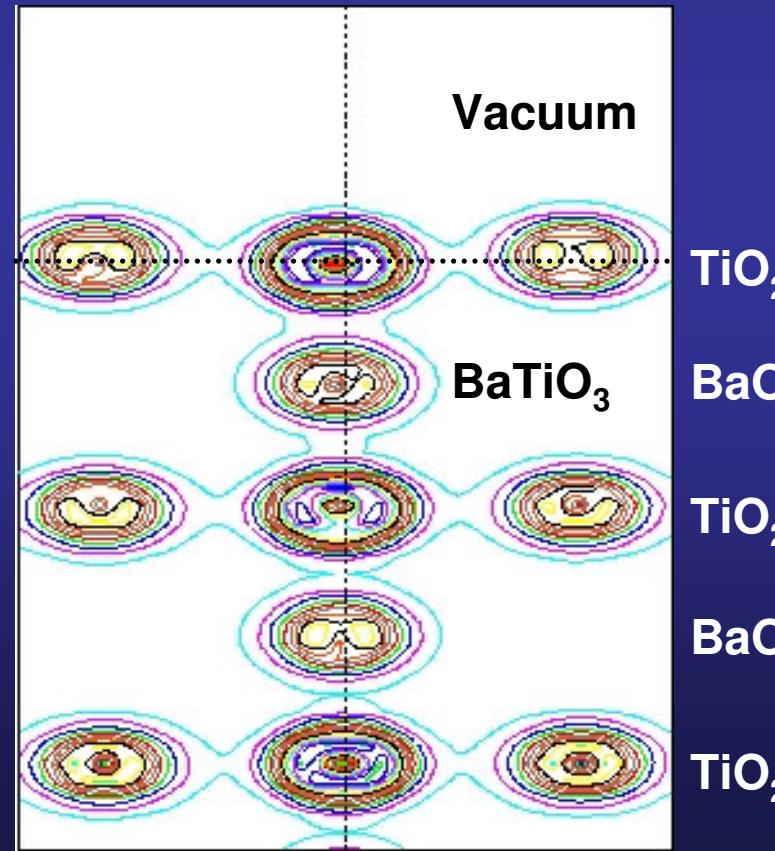


Surface effects

Some questions that might be answered *ab-initio*

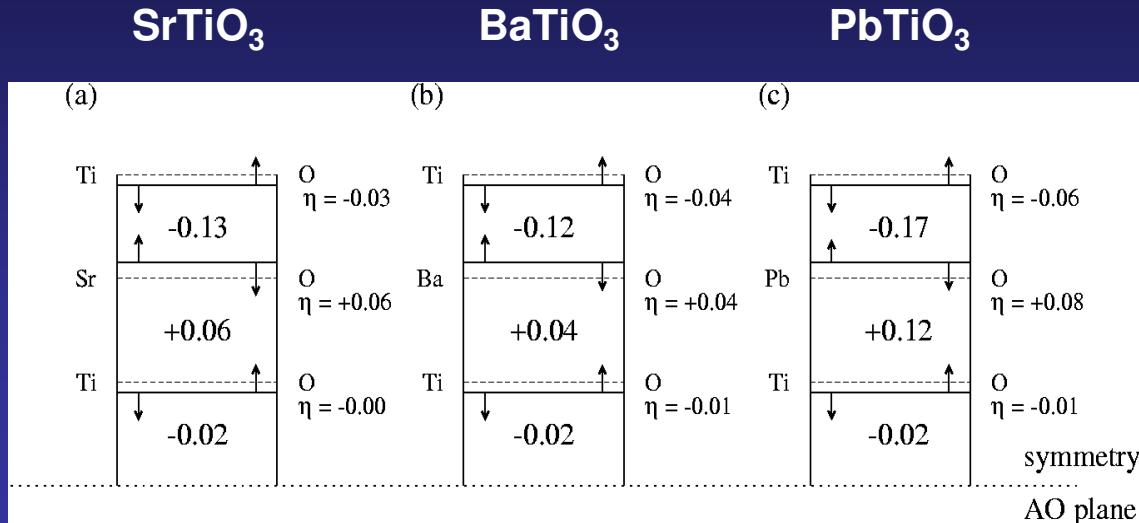


- Missing of Ti 3d-O 2p hybridization
- Intrinsic degradation of the polarization?
- Coupling of the polarization with surface-induced relaxations and reconstructions
- Influence of surface termination

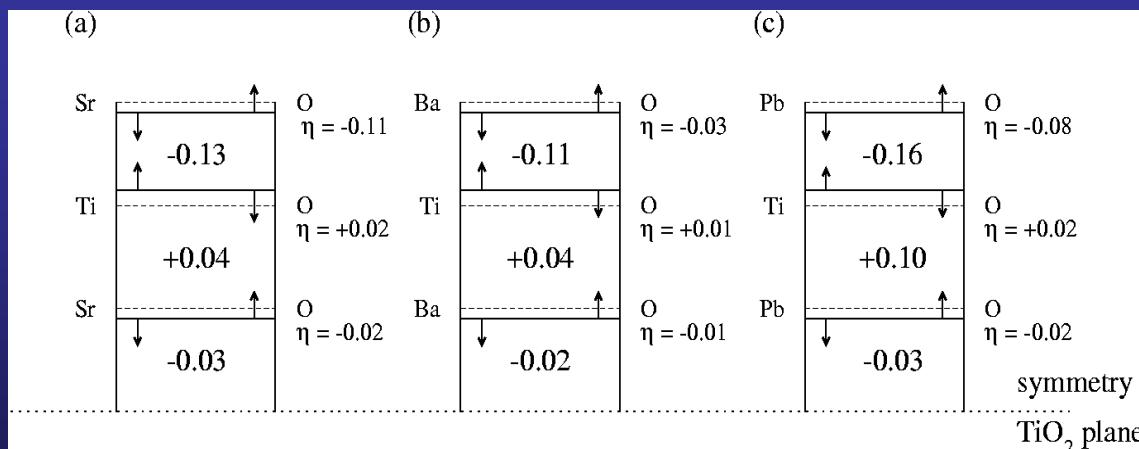


The presence of a surface induces atomic relaxations

(001) TiO_2 -terminated



(001) AO-terminated



J. Padilla and D. Vanderbilt, Surface Science 418, 64 (1998)

J. Padilla and D. Vanderbilt, Phys. Rev. B 56, 1625 (1997)

B. Meyer *et al.*, Faraday Discussions 114, 395 (1999)

Paraelectric structure

Cubic

Theoretical in-plane lattice param.

(1×1) surface reconstruction

Units in Å

•Largest relaxations: surface atoms

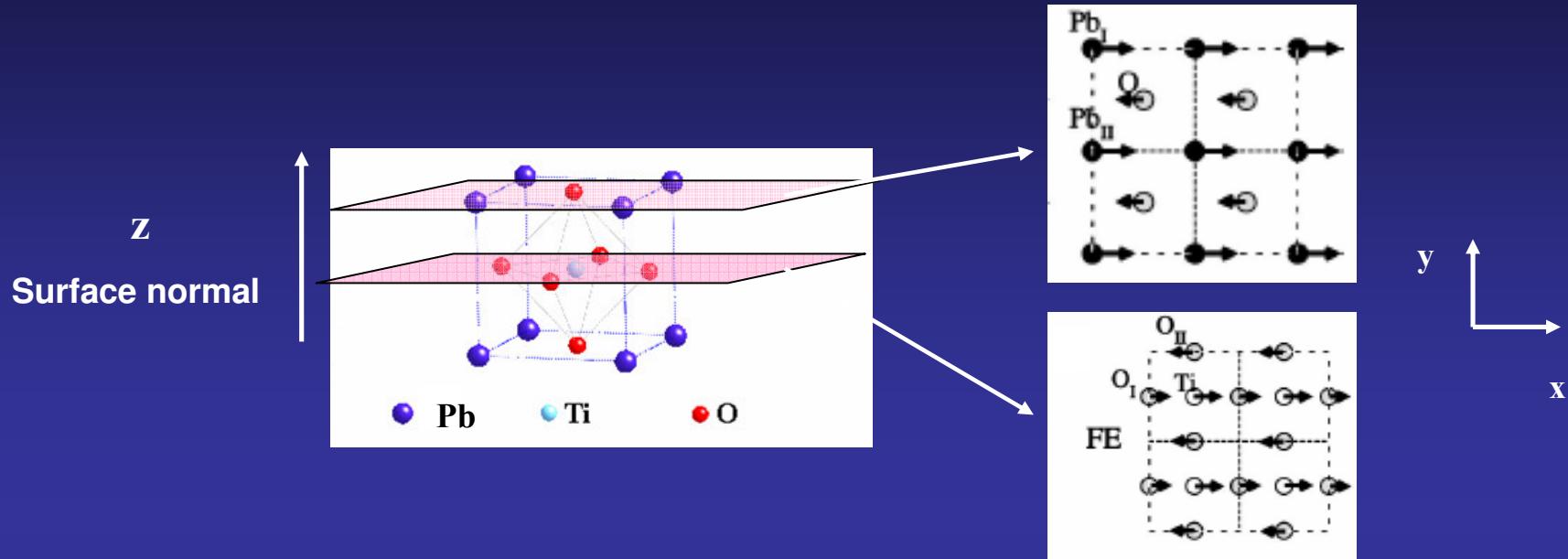
•Surface layer contracts inwards

•Rumpling of the layers gives rise to ionic surface dipole

•Oscillating relaxation pattern

•Relaxation energy (100 meV) >> bulk ferroelectric well (30-50 meV)

Coupling of the surface with in-plane polarization



Small influence of surface relaxation on in-plane ferroelectricity

	BaTiO_3	PbTiO_3	SrTiO_3
TiO ₂ -terminated	Slightly ↑	Slightly ↓	
AO-terminated	Slightly ↓	Slightly ↑	Very modest (likely destroyed by T)

J. Padilla and D. Vanderbilt, Surface Science 418, 64 (1998)

J. Padilla and D. Vanderbilt, Phys. Rev. B 56, 1625 (1997)

B. Meyer *et al.*, Faraday Discussions 114, 395 (1999)

Surface might induced reconstructions to saturate dangling bonds

(001) PbTiO_3

c(2×2) reconstructions in PbO-terminated
substantial enhancement of the AFD distortion

Driving force: shorter PbO bonds



Not observed neither in TiO_2 termination
nor BaTiO_3 surface

A. Munkholm *et al.*, Phys. Rev. Lett. 88, 016101 (2002)

C. Bungaro and K. M. Rabe, Phys. Rev. B 71, 035420 (2005)

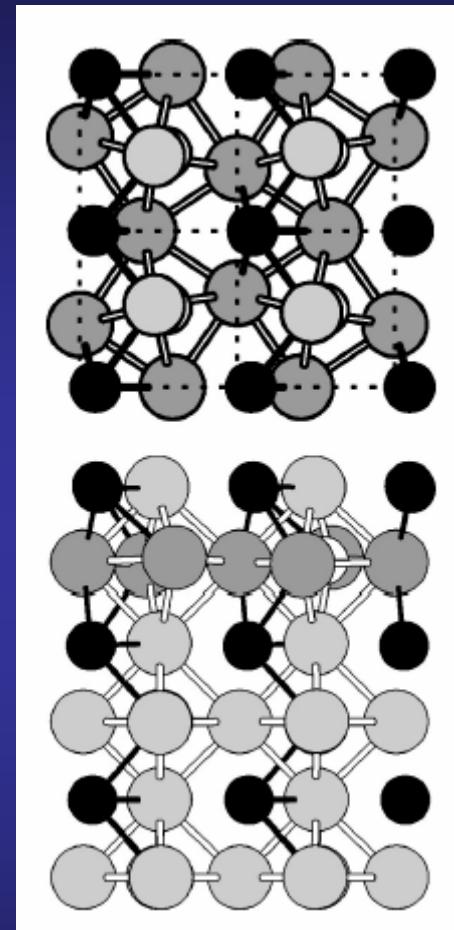
(001) SrTiO_3

Experimentally: (2×1) reconstruction

N. Erdman *et al.* Nature 419, 55 (2002)

Theoretically: (1×1) reconstruction

K. Johnston *et al.*, Phys. Rev. B 70, 085415 (2004)



Top

Lateral

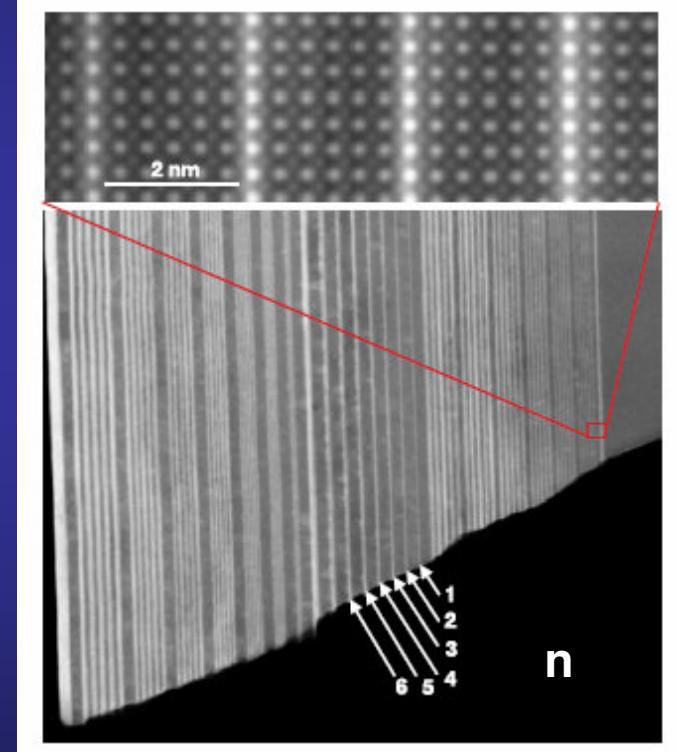
Mechanical effects

Some questions that might be answered *ab-initio*

SrTiO₃/LaTiO₃

(5×n)

n=1



- Strong coupling of homogeneous and inhomogeneous strain with P
- Strain engineering
 - tune specific properties by choosing substrate
 - appearance of new phases
- Role of misfit dislocation

Ohtomo, Nature 419, 378 (2002)

Recent reviews on strain effects in epitaxial ferroelectric oxides



Available online at www.sciencedirect.com



Current Opinion in Solid State and Materials Science 9 (2005) 122–127

Current Opinion in
Solid State &
Materials Science

Theoretical investigations of epitaxial strain effects in ferroelectric oxide thin films and superlattices

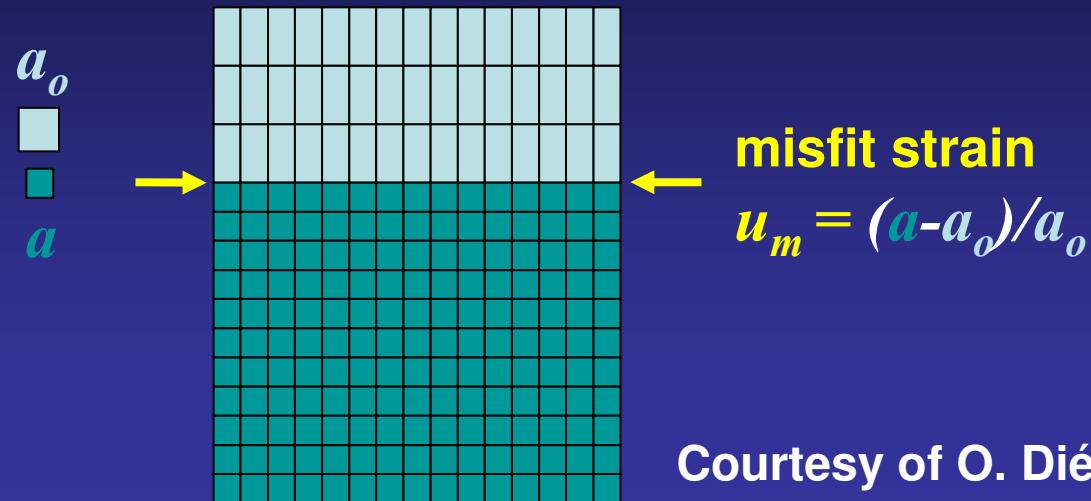
Karin M. Rabe *

Strain Tuning of Ferroelectric Thin Films*

Darrell G. Schlom,^{1,†} Long-Qing Chen,²
Chang-Beom Eom,³ Karin M. Rabe,⁴
Stephen K. Streiffer,⁵ and Jean-Marc Triscone⁶

Annu. Rev. Mater. Res. 2007. 37:589–626

Strain imposed by the substrate affects the properties of ferroelectric materials



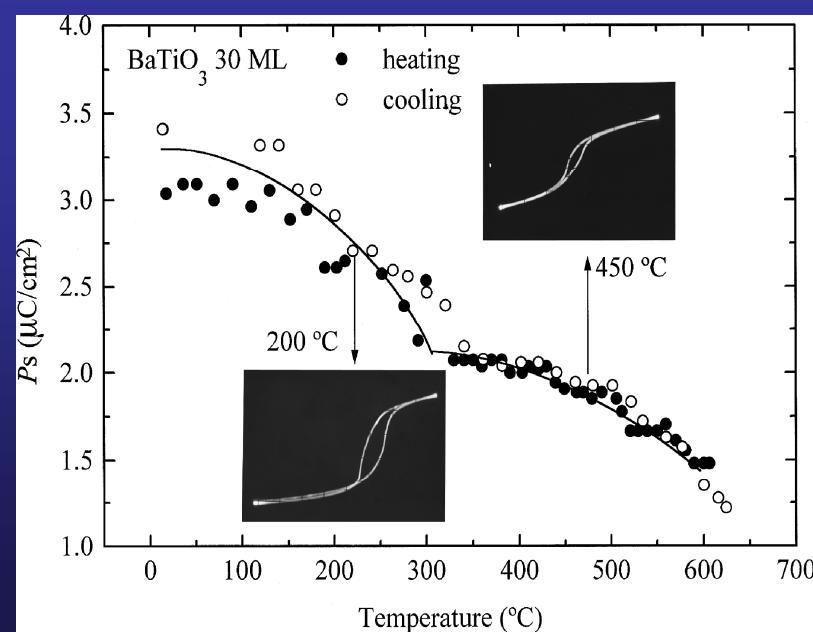
Example:

$$\text{BaTiO}_3 \quad a_o = 4.00 \text{ \AA}$$

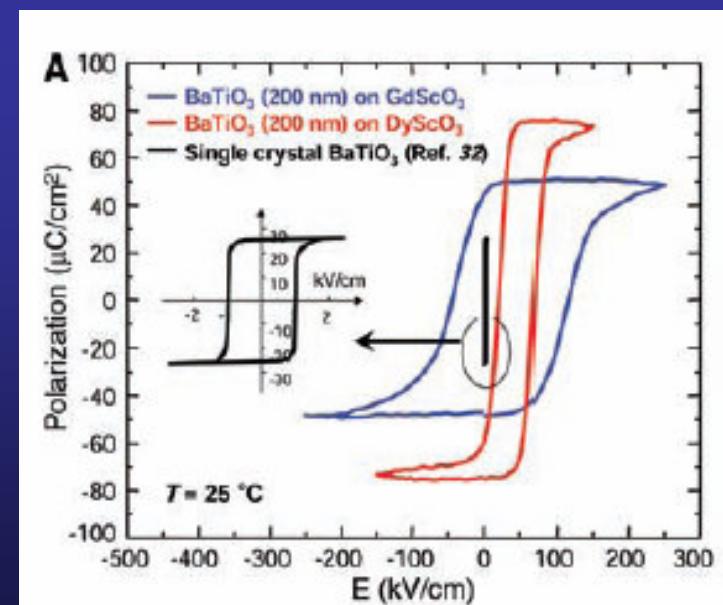
$$\text{SrTiO}_3 \quad a = 3.91 \text{ \AA}$$

$$u_m = -22.5 \times 10^{-3}$$

Courtesy of O. Diéguez



Yoneda *et al.*, J. Appl. Phys. 83, 2458 (1998)



K. J. Choi *et al.*, Science 306, 1005 (2004)

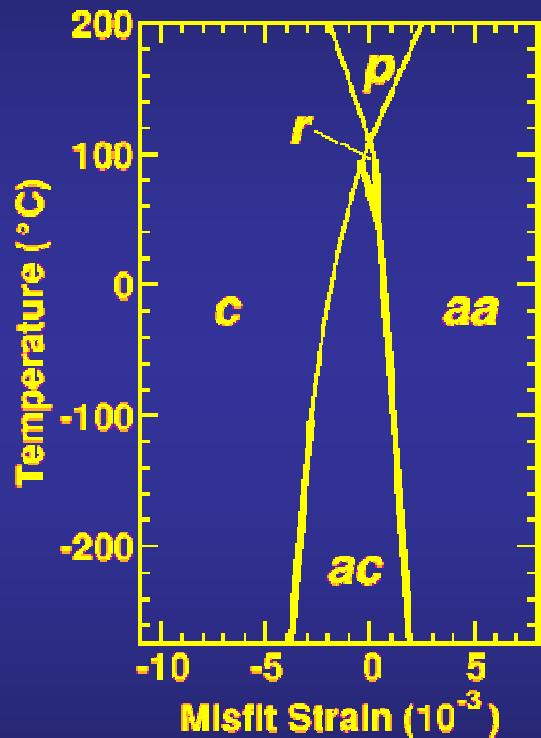
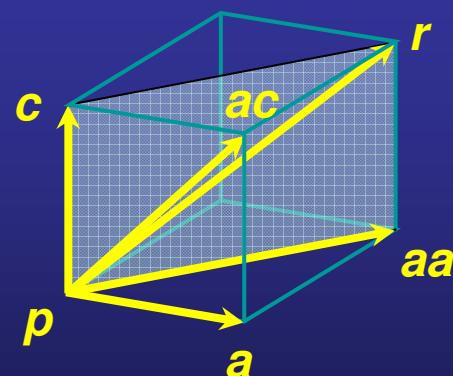
Pertsev *et al.* mapping the equilibrium structure as a function of T and strain

- The free energy is written as a function of polarization and strain.
- Temperature incorporated via a linear dependence of some expansion coefficients
- Infinite solid (no interface nor surface) subject to homogeneous strain
- Parameters are taken from experiments near bulk FE transition
- The most stable phase is found by minimizing the free energy

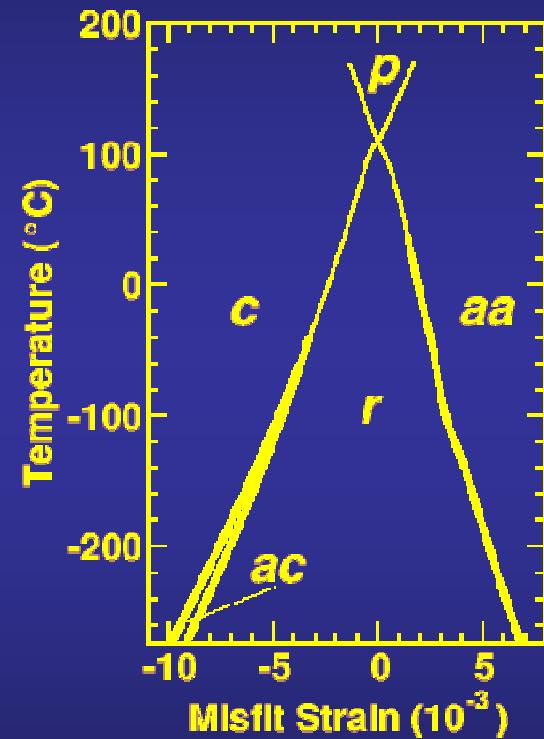
$$\begin{aligned}\tilde{G} = & a_1^*(P_1^2 + P_2^2) + a_3^*P_3^2 + a_{11}^*(P_1^4 + P_2^4) + a_{12}^*P_1^2P_2^2 \\ & + a_{13}^*(P_1^2P_3^2 + P_2^2P_3^2) + a_{33}^*P_3^4 + a_{111}(P_1^6 + P_2^6 + P_3^6) + a_{123}P_1^2P_2^2P_3^2 \\ & + a_{112}[P_1^4(P_2^2 + P_3^2) + P_2^4(P_3^2 + P_1^2) + P_3^4(P_1^2 + P_2^2)] + u_m^2/(s_{11} + s_{12})\end{aligned}$$

$$a_1^* = a_1^*(T, u_m); \quad a_3^* = a_3^*(T, u_m); \quad a_{11}^* = a_{11}^*(T); \quad a_{33}^* = a_{33}^*(T); \quad a_{123} = a_{123}(T)$$

Pertsev *et al.* obtained a semiempirical phase diagram for epitaxial BaTiO₃



Parameters:
PRL 80, 1988 (1998)

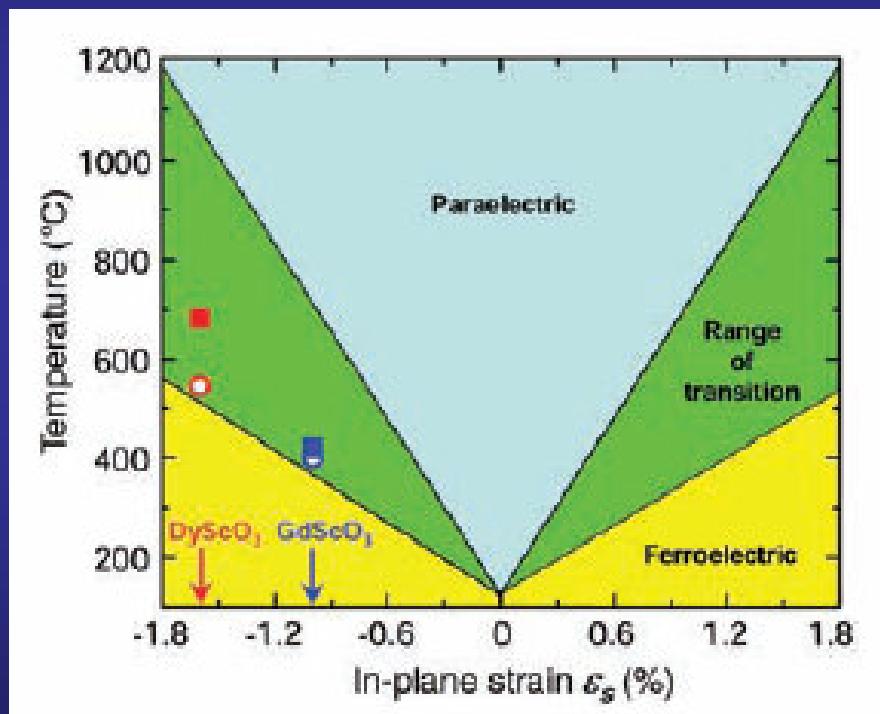


Parameters:
PRB 64, 214103 (2001)

Courtesy of O. Diéguez

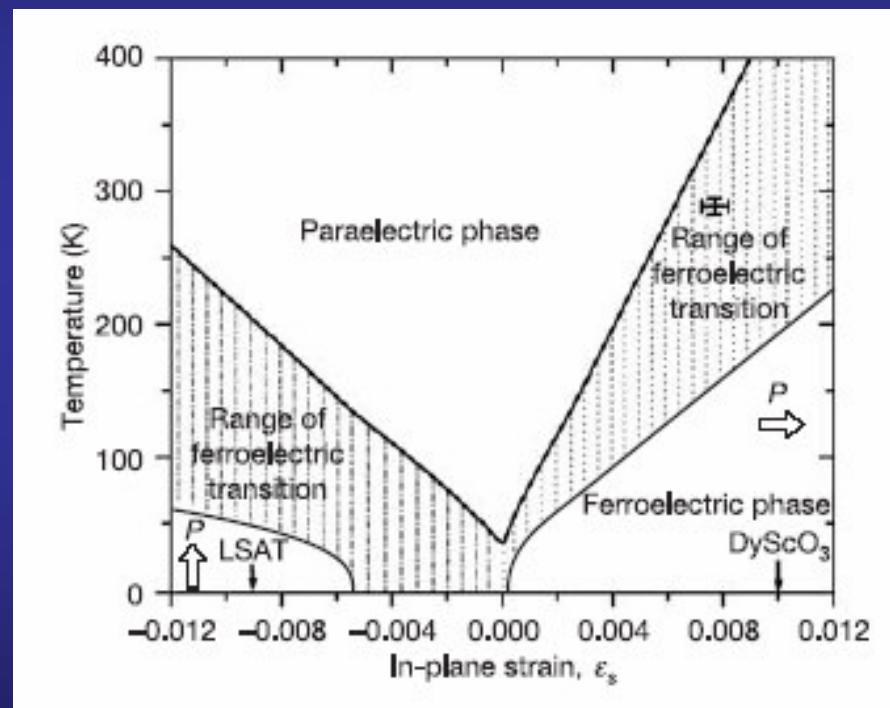
The scattering in the reported parameters produces “range of transitions” rather than clean boundaries

BaTiO_3



K. J. Choi *et al.*, Science 306, 1005 (2004)

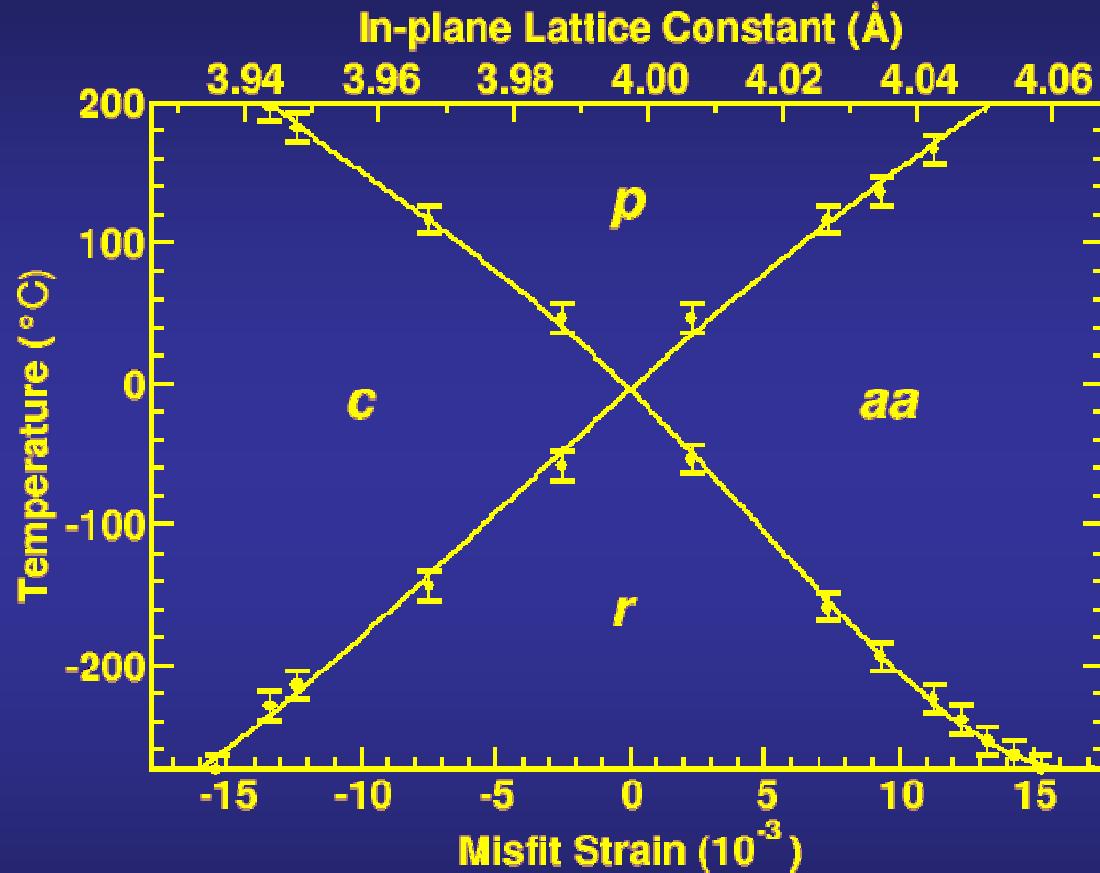
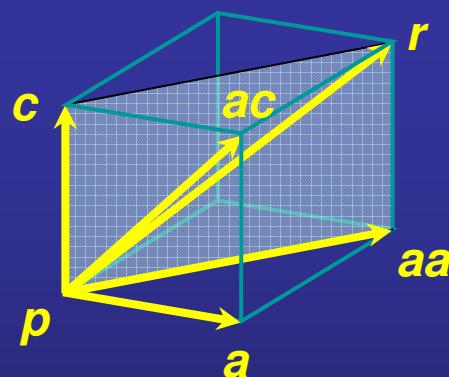
SrTiO_3



J. H. Haeni *et al.*, Nature 430, 758 (2004)

First-principles phase diagram for epitaxial BaTiO₃ resolve earlier discrepancy

No ac phase

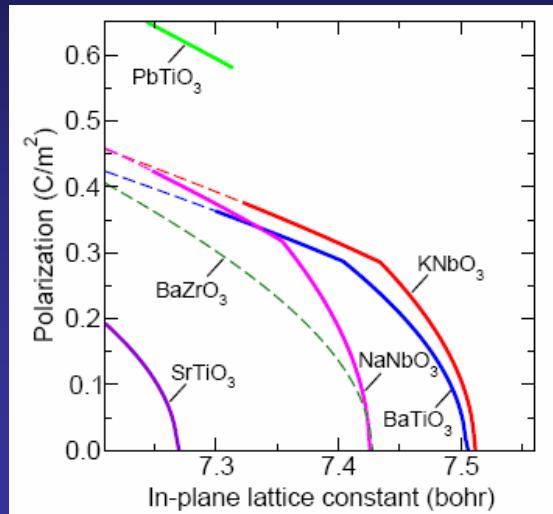


O. Diéguez *et al.*, Phys. Rev. B 69, 212101 (2004)

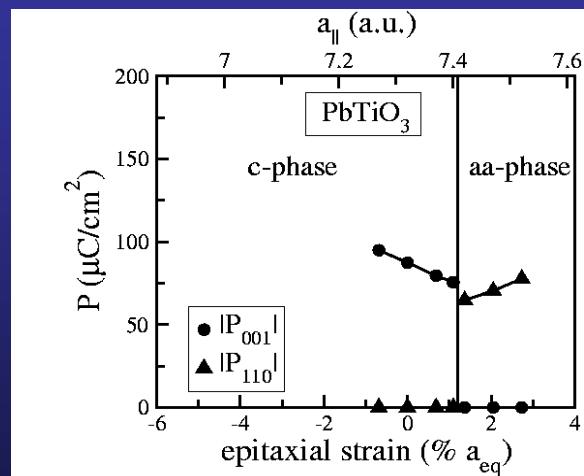
B. Lai *et al.*, Appl. Phys. Lett. 86, 132904 (2005)

Courtesy of O. Diéguez

Other perovskites epitaxially grown on a cubic substrate theoretically explored



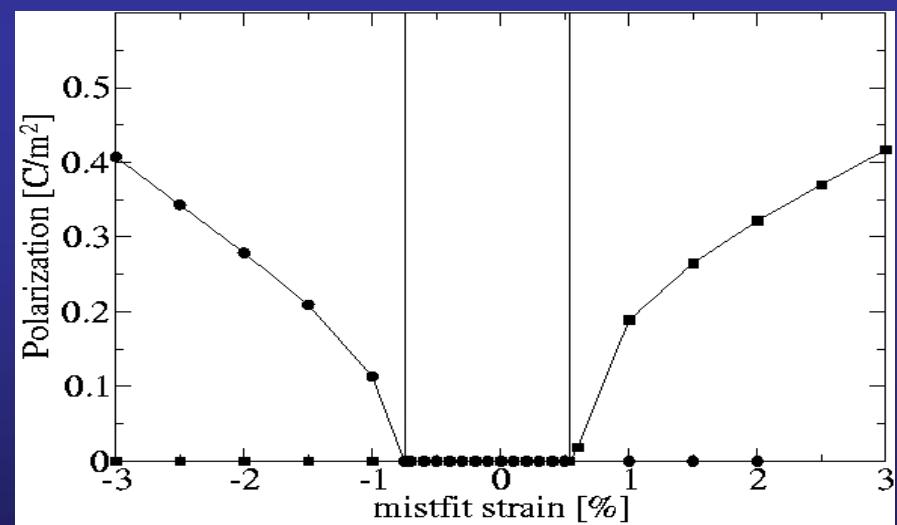
$PbTiO_3$



C. Bungaro *et al.*, PRB 69, 212101 (2004)

O. Diégez *et al.*, Phys. Rev. B 72, 144101 (2005)

$SrTiO_3$



A. Antons *et al.*, PRB 71, 024102 (2005)

Kim *et al.*, Appl. Phys. Lett. 85, 5649 (2004)

T. Schimizu, Solid State Commun. 102, 523 (1997)

Electrostatic effects

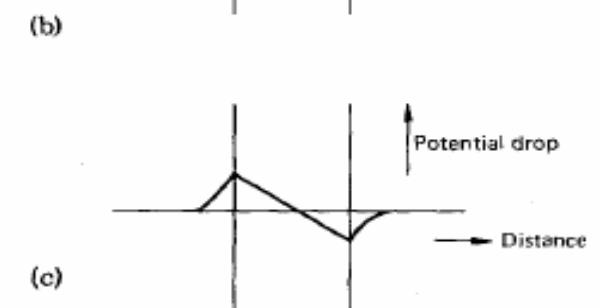
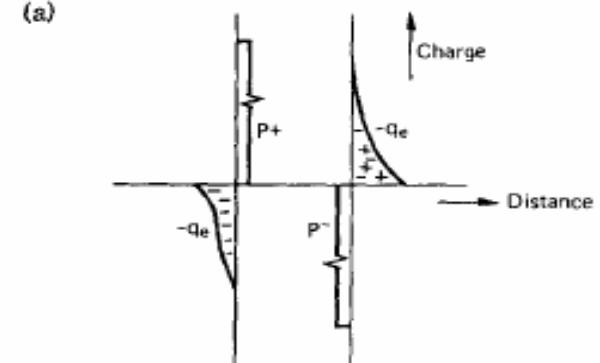
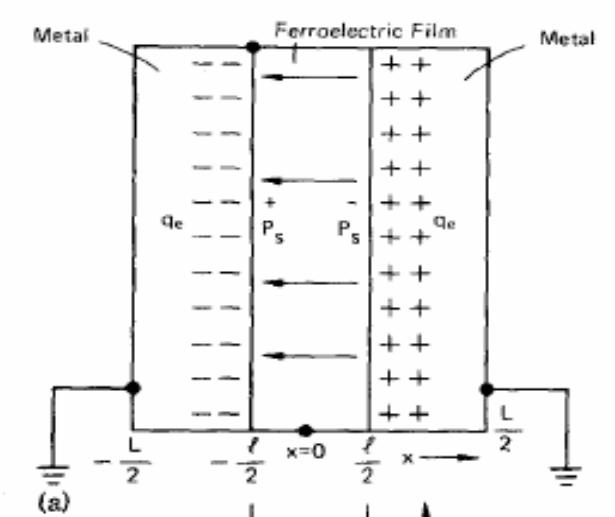
Some questions that might be answered *ab-initio*

- Finite depolarizing field
 - imperfect screening
 - polarization gradient
 - dead layer at the interface

couples with the polarization.

- Dependence of
 - density of free carriers
 - metal/ferroelectric interface
 - partial screening inside the ferroelectric

on the screening mechanism?

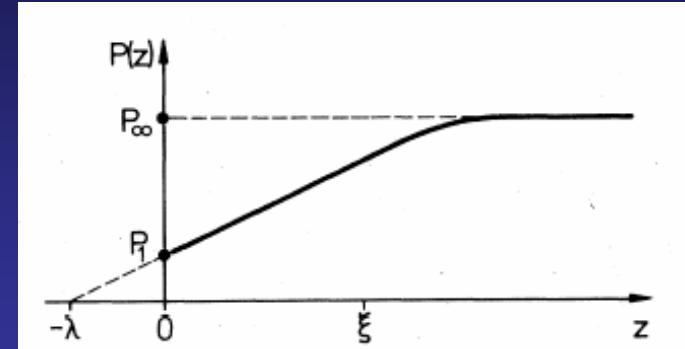


Different mechanisms for the appearance of a depolarizing field

- Inhomogeneity of the polarization distribution

K. Kretschmer and K. Binder, Phys. Rev. B 20, 1065 (1979)

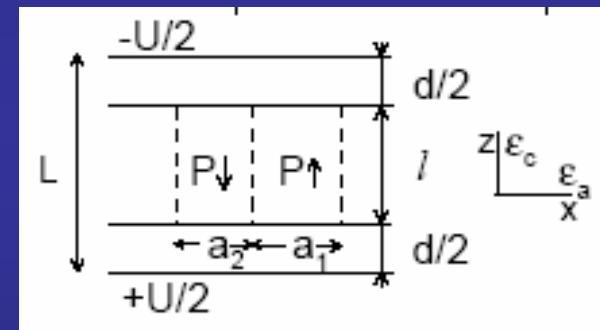
M. D. Glinchuk et al., Physica B 322, 356 (2002)



- Existence of a dead layer at the ferroelectric/electrode interface

A. M. Bratkovsky and A. P. Levanyuk, Phys. Rev. Lett. 84, 3177 (2000)

A. M. Bratkovsky and A. P. Levanyuk, Phys. Rev. B 63, 132103 (2001)

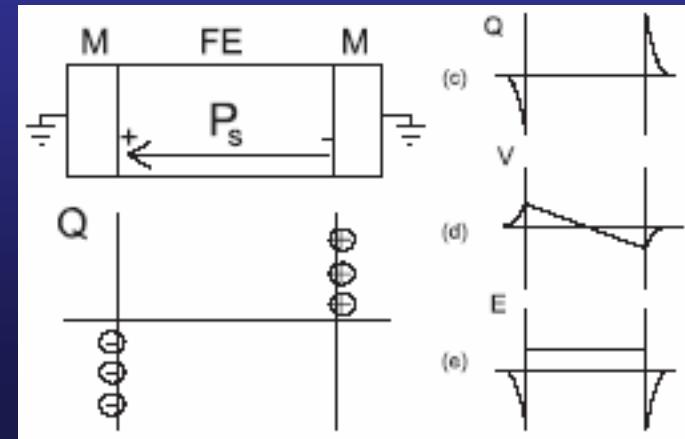


- Incomplete screening by real metallic electrode

I. P. Batra et al., J. Vac. Sci. Technol. 10, 687 (1973)

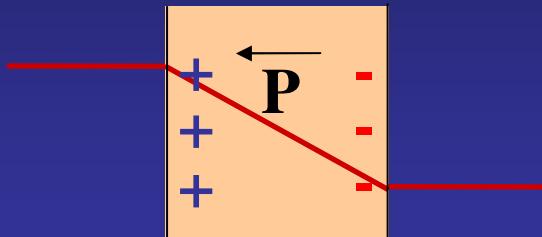
J. Junquera and Ph. Ghosez, Nature 422, 506 (2003)

M. Dawber et al., J. Phys.: Condens. Matter 15, 393 (2003)



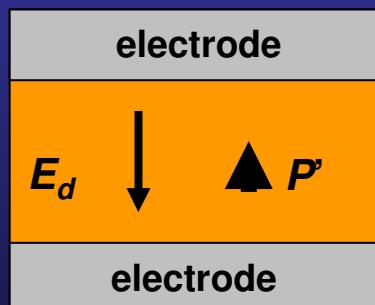
Imperfect screening by real metallic electrodes produces a depolarizing field

Vacuum
no screening



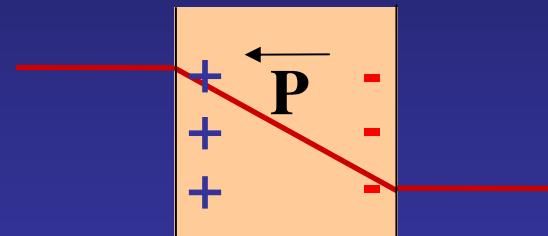
$$\mathcal{E}_d = -4\pi \mathbf{P}$$

Screening by free charges
(electrodes or adsorbates)



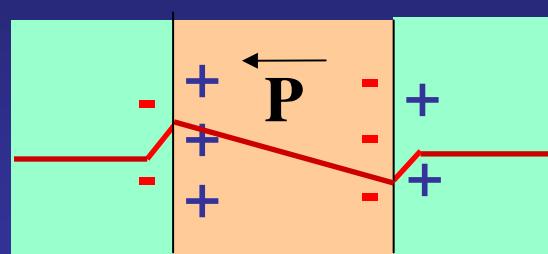
Imperfect screening by real metallic electrodes produces a depolarizing field

Vacuum
no screening



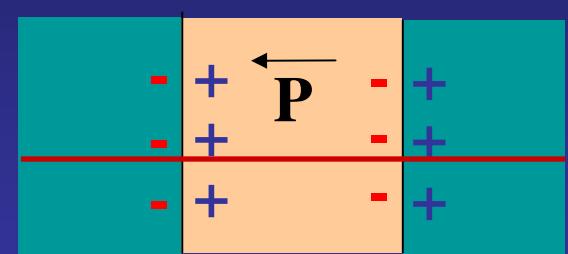
$$\mathcal{E}_d = -4 \pi P$$

Real electrodes
imperfect screening



$$\mathcal{E}_d = -4 \pi \alpha P$$

Ideal electrodes
perfect screening



$$\mathcal{E}_d = 0$$

Depolarizing field \mathcal{E}_d :

$$\mathcal{E}_d = -2 \Delta V / d$$

$$\Delta V = 4 \pi \sigma_{\text{pol}} \lambda_{\text{eff}}$$

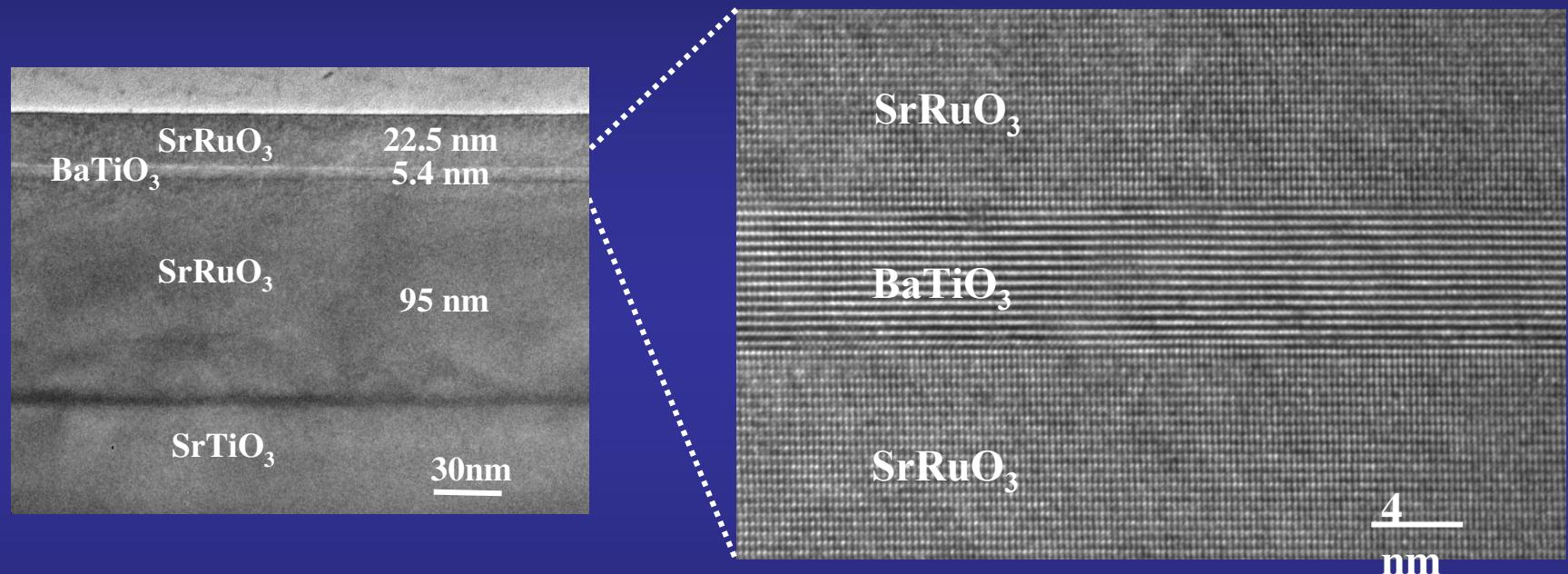
$$\sigma_{\text{pol}} = P \cdot n$$

$$\mathcal{E}_d = -4 \pi \cdot \underbrace{\left[2 \cdot \lambda_{\text{eff}} / d \right]}_{\alpha} \cdot P$$

depends on:

- the metal and interface chemistry: screening length λ_{eff}
- the ferroelectric: the spontaneous polarization P
- the film thickness d

High-resolution TEM of a typical ferroelectric capacitor



13 unit cells BaTiO₃ grown by MBE

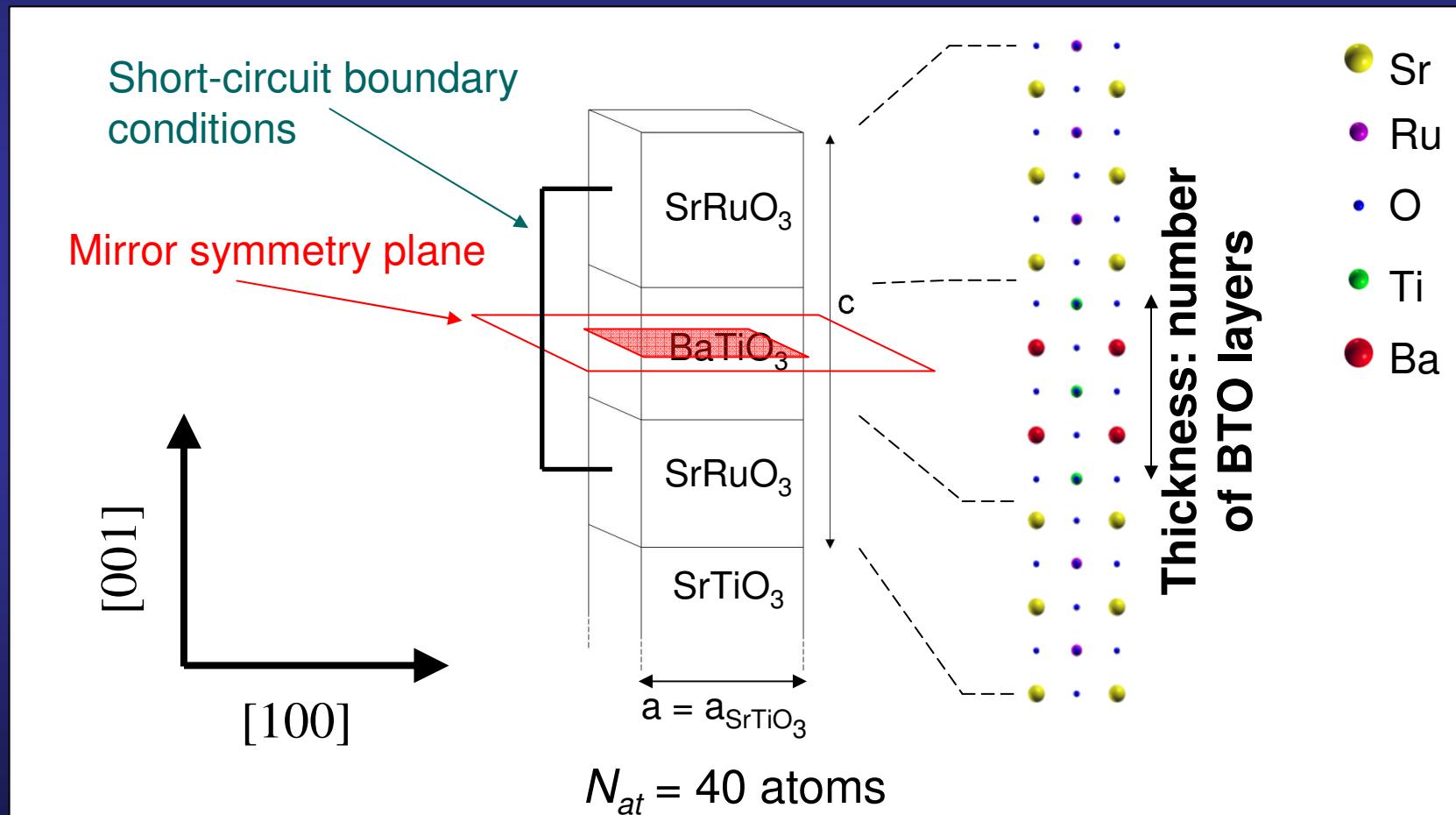
J. Rodriguez Contreras, C. Jia, H. Kohlstedt, D. G. Schlom

Forschungszentrum Jülich

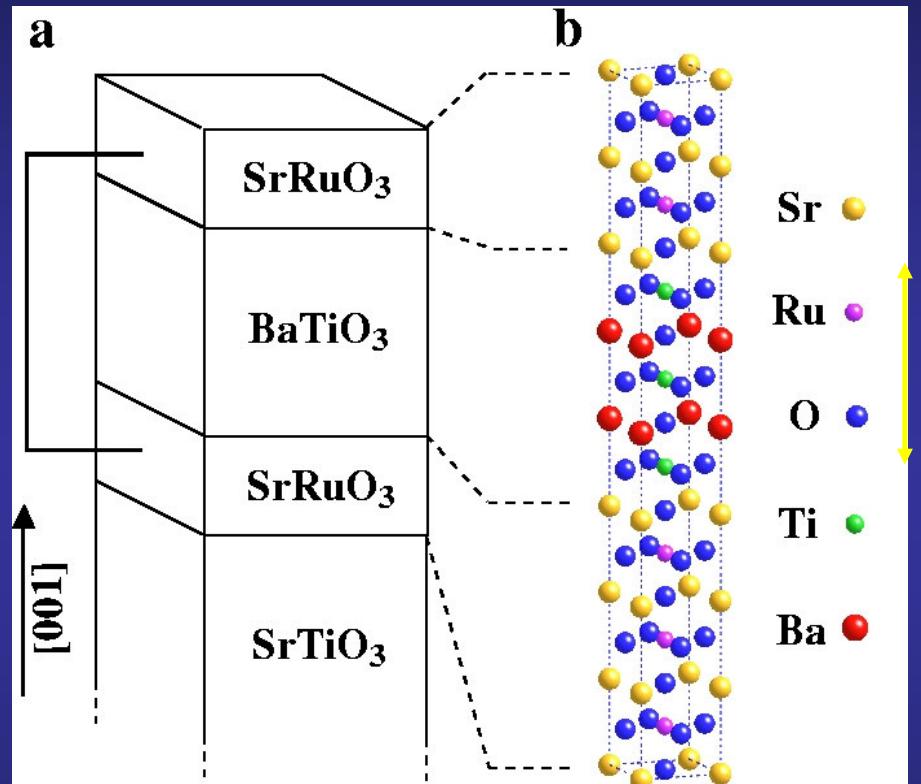
Institut für Festkörperforschung – Elektrokeramische Materialien



Simulations of ferroelectric nanocapacitors from first-principles: Building the paraelectric unit cell



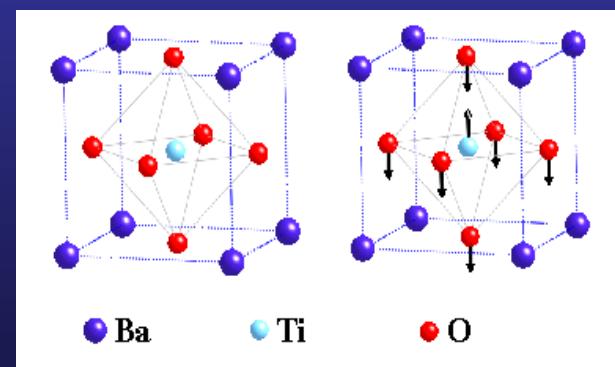
Simulations of ferroelectric nanocapacitors from first-principles



J. Junquera and Ph. Ghosez, Nature 422, 506 (2003)

Thickness:
m number of BTO cells

Polarization control:
 ξ percentage bulk soft mode



$\xi=0$

$\xi=1$

The depolarizing field is directly proportional to the induced polarization

- Charge density *changes* for $\xi \neq 0$:

Complex pattern of charge at the interface

Beyond simple Thomas-Fermi screening
(with screening length λ)

- Electrostatic potential *changes*
(electrons + ions) for $\xi \neq 0$:

Potential drop at the interface:

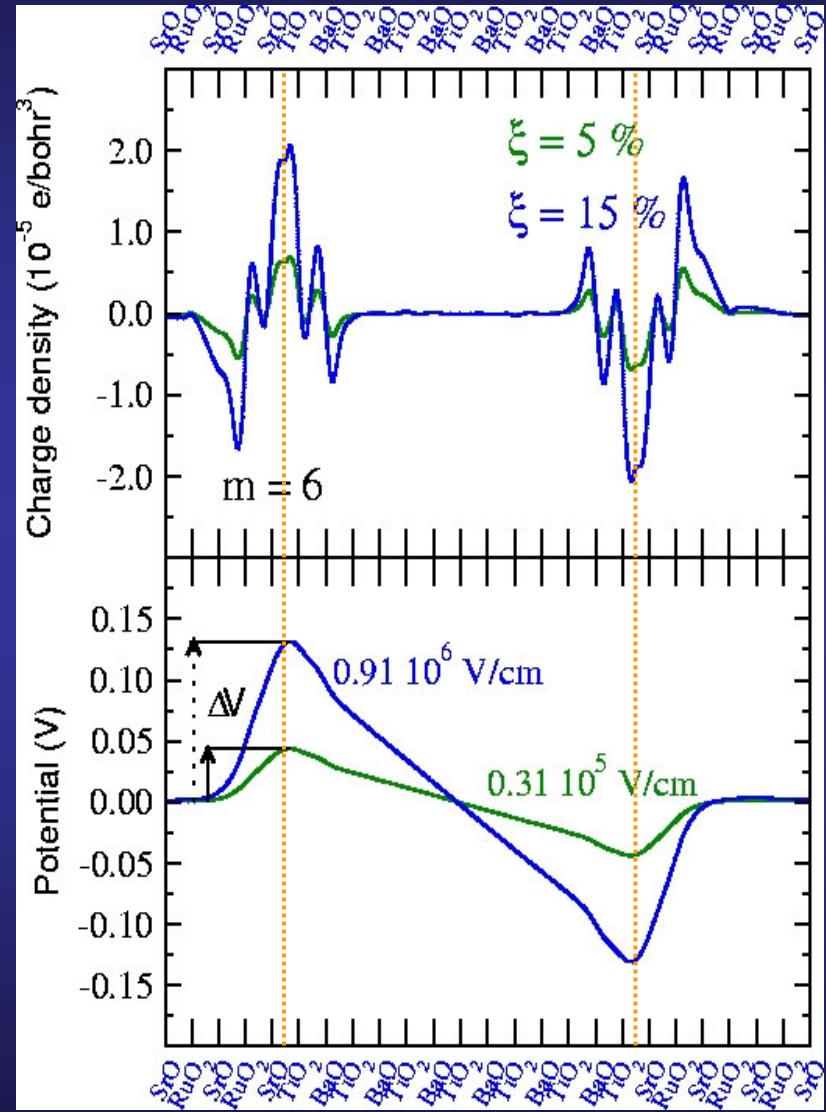
$$\Delta V \text{ linear with } \sigma_{\text{pol}} = P \cdot n$$

Effective screening length :

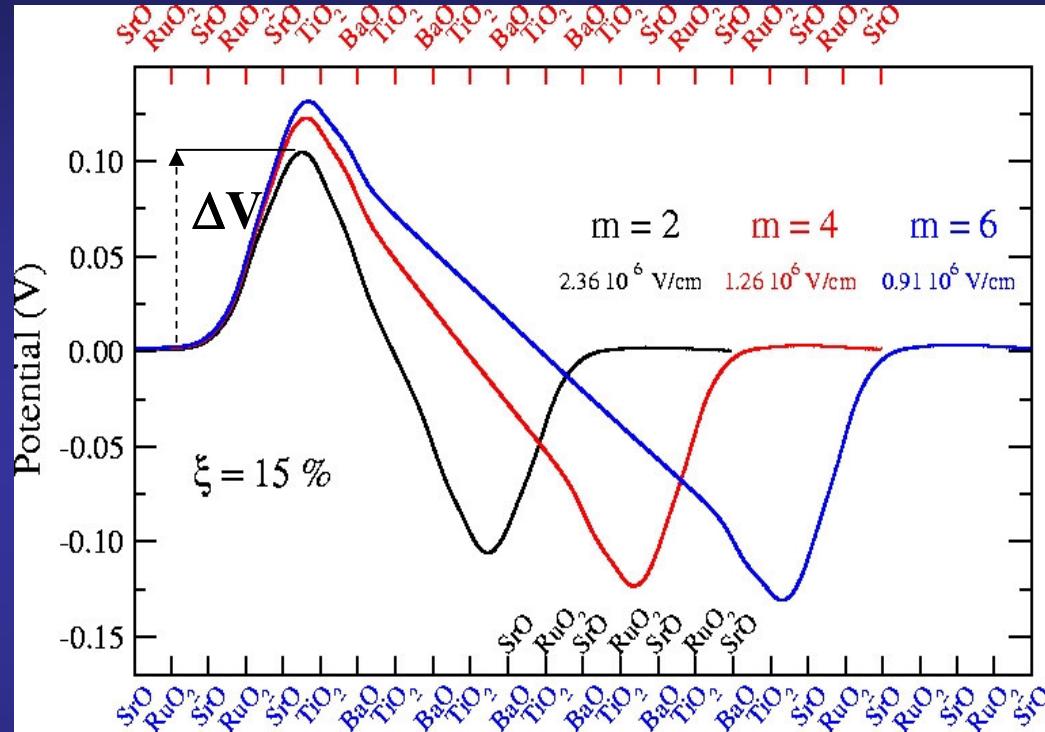
$$\Delta V = 4\pi \lambda_{\text{eff}} \cdot \sigma_{\text{pol}} \quad (\lambda_{\text{eff}} \sim 0.23 \text{ \AA})$$

Depolarizing field :

$$\mathcal{E}_d = -2 \cdot \Delta V / (m \cdot a_{\text{cell}})$$

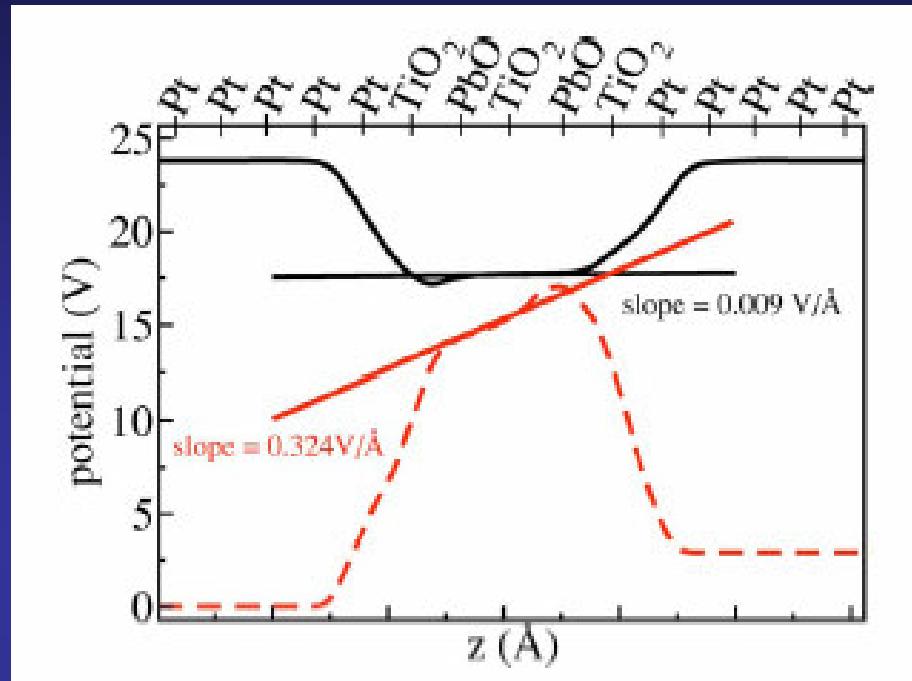


The depolarizing field is inversely proportional to the thickness



- Depolarizing field \mathcal{E}_d evolves with thickness m :
$$\mathcal{E}_d = -2 \cdot \Delta V / (m \cdot a_{cell})$$
- Potential drop ΔV :
$$\Delta V = 4 \pi \lambda_{eff} \cdot \sigma_{pol}$$

The depolarizing field depends on the interface



Na Sai *et al.*, Phys. Rev. B 72, 020101 (2005)

$\text{SrRuO}_3/\text{BaTiO}_3$ } Incomplete screening

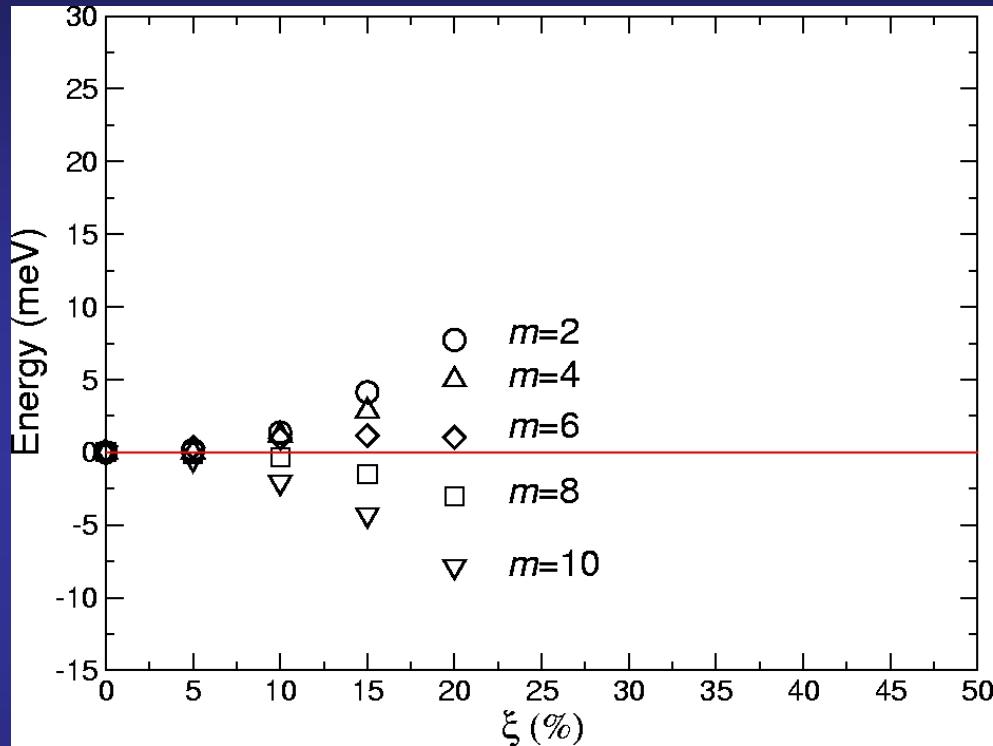
$\text{SrRuO}_3/\text{PbTiO}_3$ }

Pt/PbTiO_3 } “Perfect” screening

Pt/BaTiO_3 }

Existence of a critical thickness in monodomain films

DFT results



Critical thickness for $m \approx 6$

Smaller t_c if relaxation of
all the atoms is allowed

J. Junquera and Ph. Ghosez, Nature 422, 506 (2003)

$m = 2$: full atomic relaxation starting from a *ferroelectric* state
→ the structure went back to the *paraelectric* state

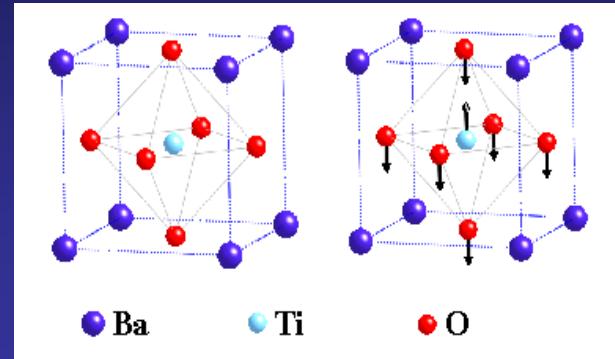
Existence of a critical thickness in monodomain films

Electrostatic model

Bulk:

$$U = A \xi^2 + B \xi^4$$

$$\xi=0$$



$$\xi=1$$

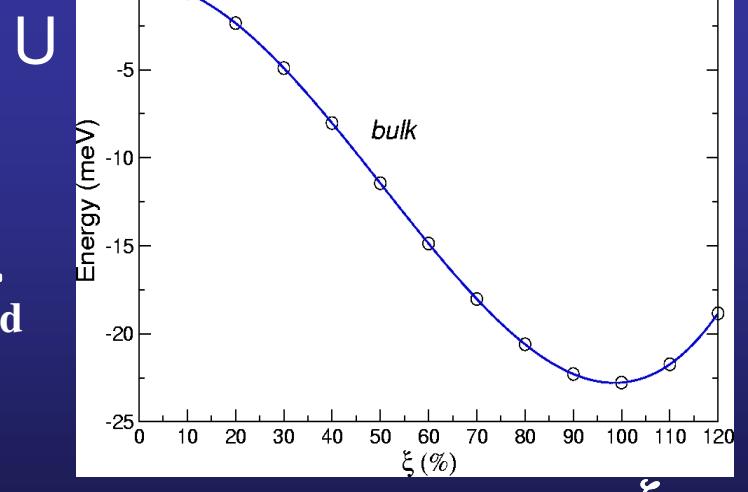
Thin film:

$$E = U - \epsilon_d \cdot P$$

$U \approx$ bulk
double-well
energy

$$P = Z_T^* \cdot \xi / \Omega_0 + \chi^\infty \cdot \epsilon_d$$

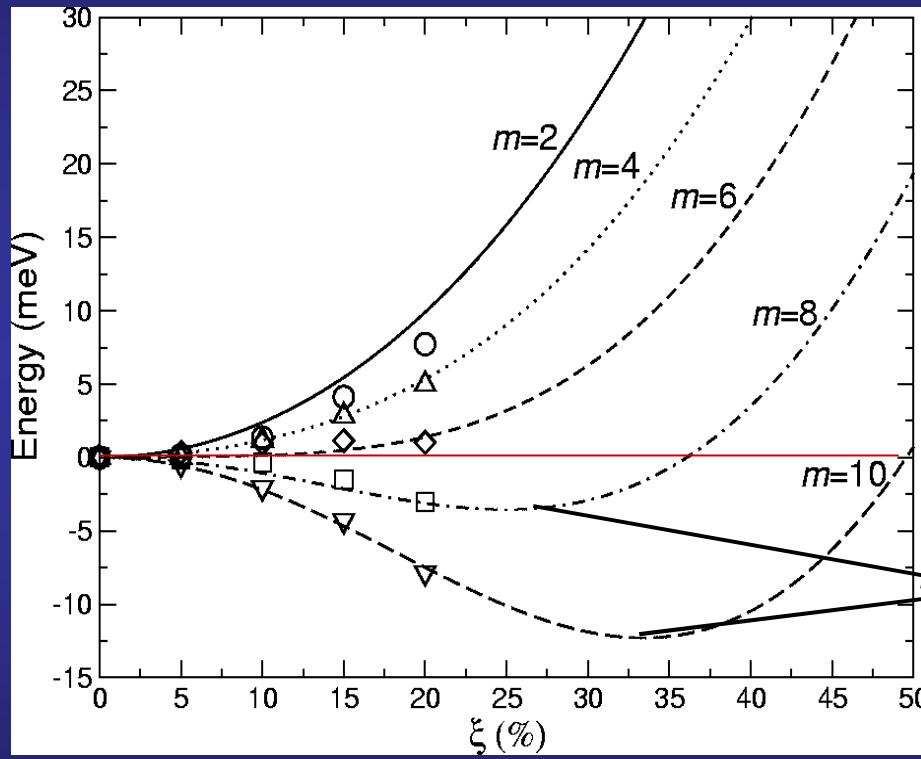
$$\epsilon_d \approx 2 \cdot \Delta V / (m \cdot a_{\text{cell}})$$



$$\xi$$

Existence of a critical thickness in monodomain films DFT versus model results

$$E = U - \mathcal{E}_d \cdot P$$



Minima below
bulk ($\xi = 1$)
 P_s deduced
from ξ_{\min}

J. Junquera and Ph. Ghosez, Nature 422, 506 (2003)

Behavior can be explained by *electrostatic* effects.
The *chemistry* of the interface buried in λ_{eff} .

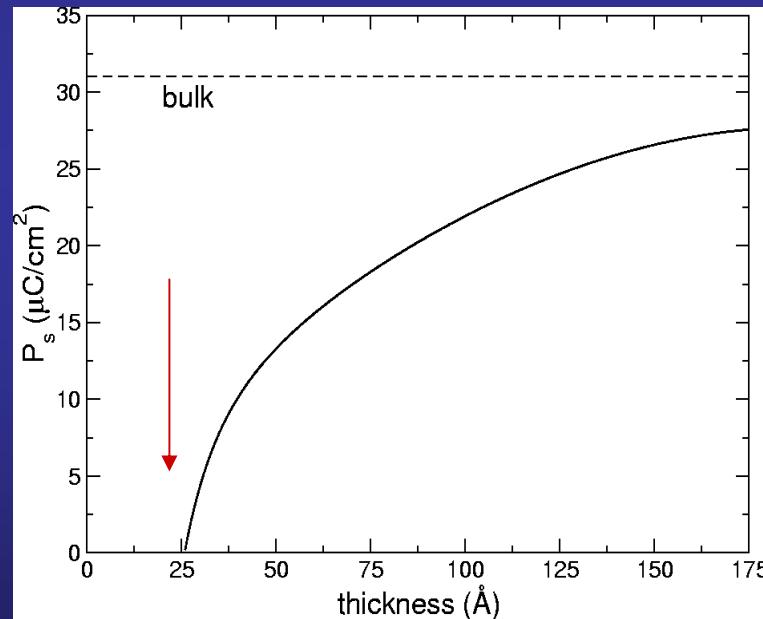
Twofold effect of the depolarizing field in monodomain films

$$\mathcal{E}_d = -4\pi\alpha P$$

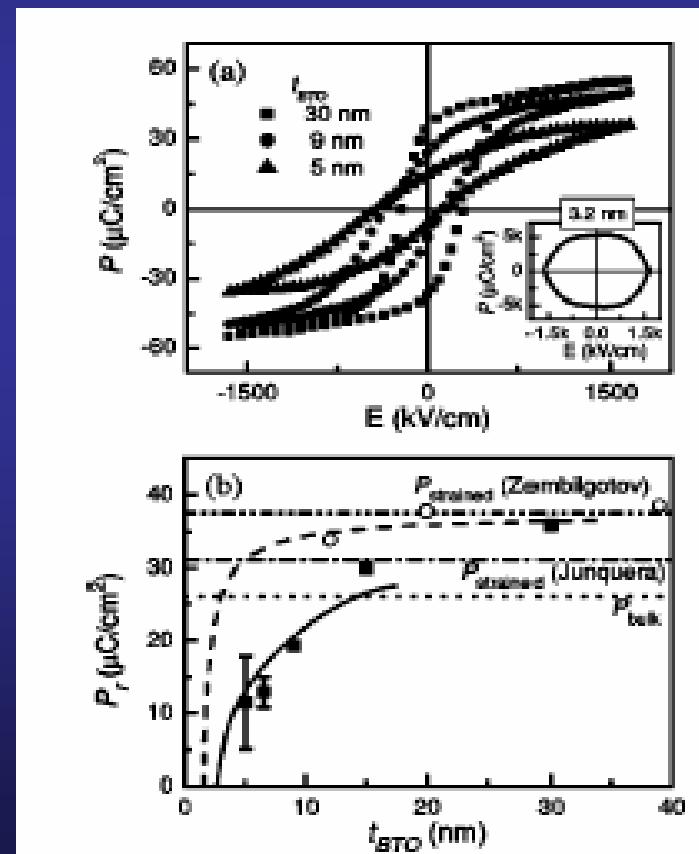
$$E = U - \mathcal{E}_d \cdot P$$

Below the critical thickness: suppression of the ferroelectricity

Above the critical thickness: reduction of spontaneous polarization



J. Junquera and Ph. Ghosez, Nature 422, 506 (2003)



Y. S. Kim et al., Appl. Phys. Lett. 86, 102907 (2005)

Many DFT first-principles computations on size effects in ferroelectric ultrathin films

PHYSICAL REVIEW B 72, 020101(R) (2005)

Ferroelectricity in ultrathin perovskite films

Na Sai, Alexie M. Kolpak, and Andrew M. Rappe

PRL 96, 107603 (2006)

PHYSICAL REVIEW LETTERS

week ending
17 MARCH 2006

Ionic Polarizability of Conductive Metal Oxides and Critical Thickness for Ferroelectricity in BaTiO₃

G. Gerra,^{1,*} A. K. Tagantsev,¹ N. Setter,¹ and K. Parlinski²

PHYSICAL REVIEW B 74, 060101(R) (2006)

Ab initio study of the critical thickness for ferroelectricity in ultrathin Pt/PbTiO₃/Pt films

Yoshitaka Umeno,^{1,2} Bernd Meyer,³ Christian Elsässer,^{4,1} and Peter Gumbsch^{1,4}

Interface Effect on Ferroelectricity at the Nanoscale

Chun-Gang Duan,^{†,‡,§} Renat F. Sabirianov,^{‡,§} Wai-Ning Mei,^{‡,§}
Sitaram S. Jaswal,^{†,§} and Evgeny Y. Tsymbal^{†,‡,§}

NANO
LETTERS

2006
Vol. 6, No. 3
483–487

PRL 96, 127601 (2006)

PHYSICAL REVIEW LETTERS

week ending
31 MARCH 2006

Stabilization of Monodomain Polarization in Ultrathin PbTiO₃ Films

D. D. Fong,¹ A. M. Kolpak,² J. A. Eastman,¹ S. K. Streiffer,¹ P. H. Fuoss,¹ G. B. Stephenson,¹ Carol Thompson,³
D. M. Kim,⁴ K. J. Choi,⁴ C. B. Eom,⁴ I. Grinberg,² and A. M. Rappe²

Many DFT first-principles computations on size effects in ferroelectric ultrathin films

Reference	Heterostructure	Method	Functional	Interface	a_{\parallel}	t_c		
Junquera <i>et al.</i> [56]	SrRuO ₃ /BaTiO ₃ /SrRuO ₃	NAO	LDA (CA)	SrO-TiO ₂	3.874 Å ($a_{\text{SrTiO}_3}^{\text{th}}$)	6		
Junquera <i>et al.</i>	SrRuO ₃ /PbTiO ₃ /SrRuO ₃	NAO	LDA (CA)	SrO-TiO ₂	3.874 Å ($a_{\text{SrTiO}_3}^{\text{th}}$)	6		
Gerra <i>et al.</i> [63]	SrRuO ₃ /BaTiO ₃ /SrRuO ₃	PW	GGA (PW91)	SrO-TiO ₂	3.94 Å ($a_{\text{SrTiO}_3}^{\text{th}}$)	3		
Umeno <i>et al.</i> [89]	Pt/PbTiO ₃ /Pt	MBPP	LDA (CA)	Pt-PbO	3.845 Å ($a_{\text{SrTiO}_3}^{\text{th}}$)	4		
				Pt-TiO ₂		6		
			GGA (PW91)	Pt-PbO	3.905 Å ($a_{\text{PbTiO}_3}^{\text{exp}}$)	No		
				Pt-TiO ₂		No		
Duan <i>et al.</i> [86]	SrRuO ₃ /KNbO ₃ /SrRuO ₃	PW	LDA (CA)	SrO-NbO ₂	3.905 Å ($a_{\text{SrTiO}_3}^{\text{exp}}$)	4		
				Pt-NbO ₂		2		
	Pt/KNbO ₃ /Pt		GGA	SrO-TiO ₂	3.991 Å ($a_{\text{BaTiO}_3}^{\text{exp}}$)	> 4		
				RuO ₂ -BaO		> 4		
Na Sai <i>et al.</i> [64,90]	SrRuO ₃ /BaTiO ₃ /SrRuO ₃	PW	GGA	Pt-TiO ₂		> 4		
				Pt-BaO		> 4		
				SrO-TiO ₂	3.905 Å ($a_{\text{PbTiO}_3}^{\text{exp}}$)	No		
				RuO ₂ -PbO		No		
	Pt/BaTiO ₃ /Pt			Pt-TiO ₂		No		
				Pt-BaO		No		
				SrO-TiO ₂	3.905 Å ($a_{\text{PbTiO}_3}^{\text{exp}}$)	No		
				RuO ₂ -PbO		No		
D. D. Fong <i>et al.</i> [47]	SrRuO ₃ /PbTiO ₃ /vacuum	PW	GGA	Pt-TiO ₂		No		
	SrRuO ₃ /PbTiO ₃ /OH, O or H			Pt-PbO		No		
	SrRuO ₃ /PbTiO ₃ /CO ₂			SrO-TiO ₂	$a_{\text{PbTiO}_3}^{\text{th}}$	> 3		
	SrRuO ₃ /PbTiO ₃ /H ₂ O					< 3		
						~ 3		
						> 3		

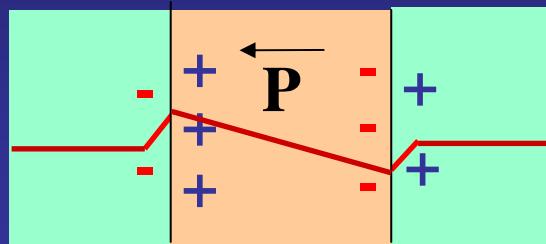
Be careful with the functional used... GGA overestimates tetragonality and double-well depth in bulk PbTiO₃

	Cubic phase				Tetragonal phase				ΔE
	a	E_{gap}	a	c/a	$u_z(\text{Ti})$	$u_z(\text{O}_1)$	$u_z(\text{O}_3)$	E_{gap}	
LDA, MBPP	3.880	1.55	3.853	1.050	0.5312	0.0923	0.6012	1.62	-0.053
LDA, PAW	3.894	1.48	3.867	1.043	0.5334	0.0883	0.6018		-0.056
LDA ^a	3.894		3.858	1.051					
PW91, MBPP	3.957	1.69	3.827	1.247	0.5571	0.1938	0.6670	2.04	-0.196
PW91, PAW	3.969	1.61	3.841	1.233	0.5559	0.1859	0.6660		-0.192
PBE, MBPP	3.962	1.69	3.836	1.244	0.5579	0.1949	0.6675	2.05	-0.208
PBE ^a	3.971		3.857	1.230					
Expt. (298 K) ^b	3.969		3.905	1.064	0.539	0.114	0.617	3.5	

...responsible for the absence of critical thickness in PbTiO₃ nanocapacitors?

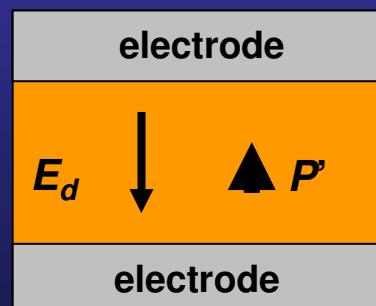
Until today, monodomain studies, goal of this work: multidomain simulations

Real electrodes
imperfect screening

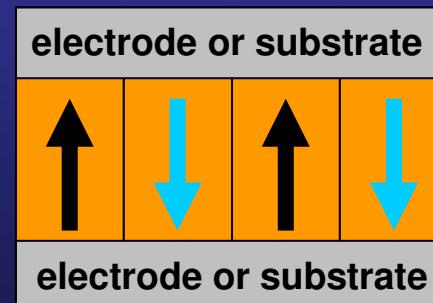


$$\mathcal{E}_d = - 4 \pi \cdot [2 \cdot \lambda_{eff} / d] \cdot \mathbf{P}$$

Screening by free charges
(electrodes or adsorbates)



Formation of domains
(no net charge at surface)



Goal of this work

Main questions addressed in this work

- Is the phase transition as a function of thickness from...
homogeneous polarization to paraelectric?
homogeneous polarization to inhomogeneous polarization?

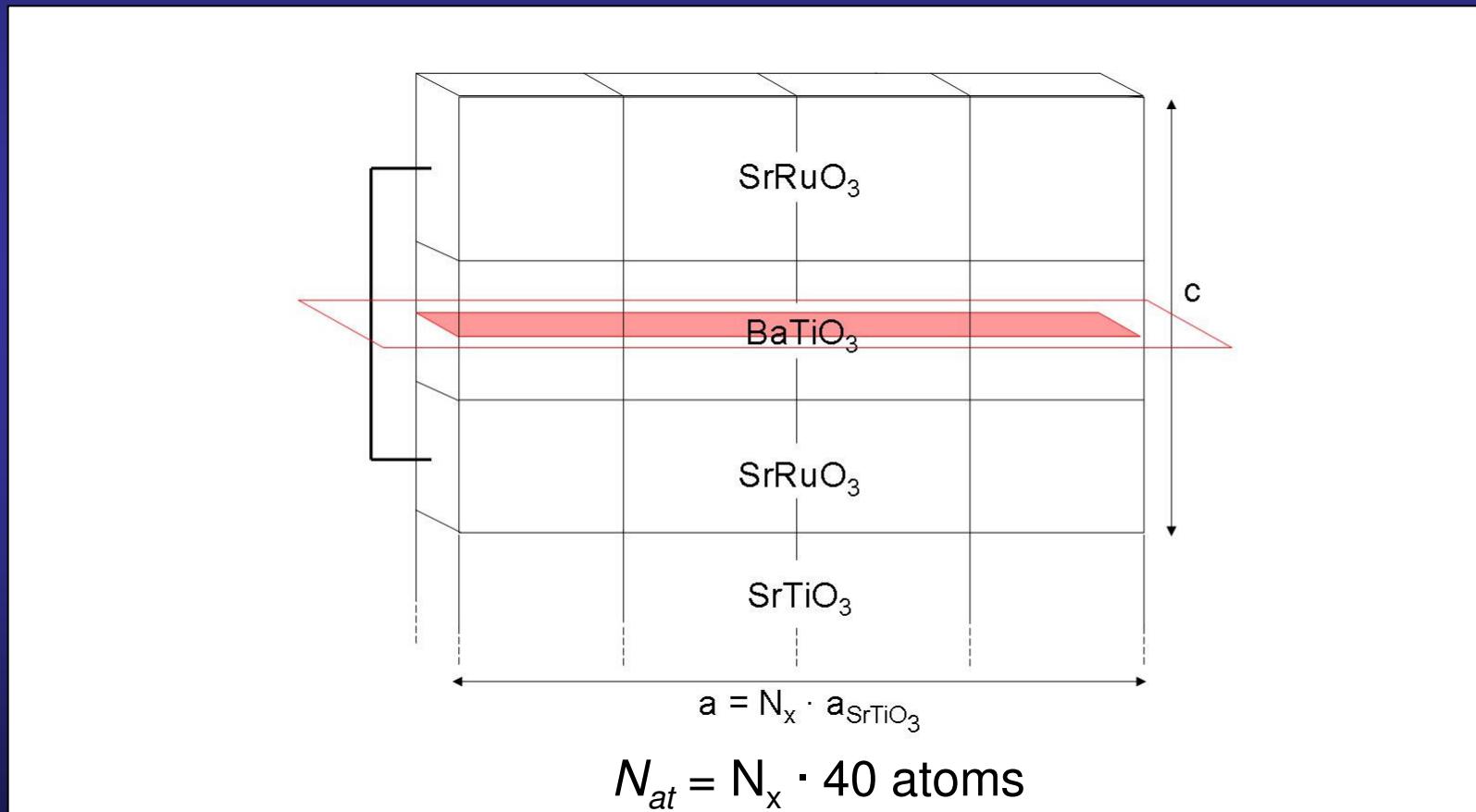
“It is not certain yet whether this instability in a single-domain ground state results in paraelectricity or in many small domains”

J. F. Scott, J. Phys.: Condens. Matter 18, R361 (2006)

- If the second is true, do the domains have a defined structure?

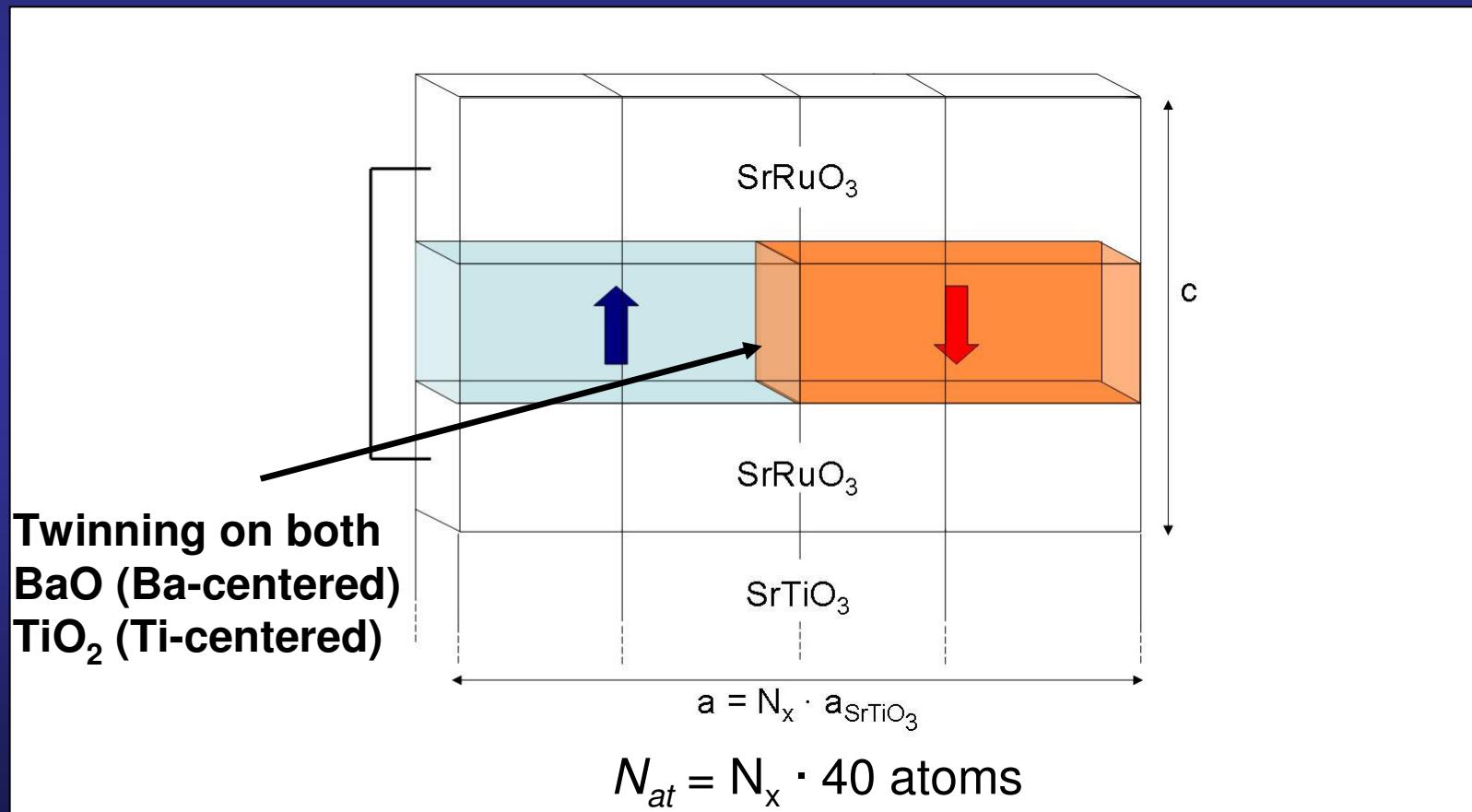
Building the cell: replicating the paraelectric structure

- N_x repetitions in [100] direction.
- The energies of these cells as references.



Building the cell: inducing a polarization by hand

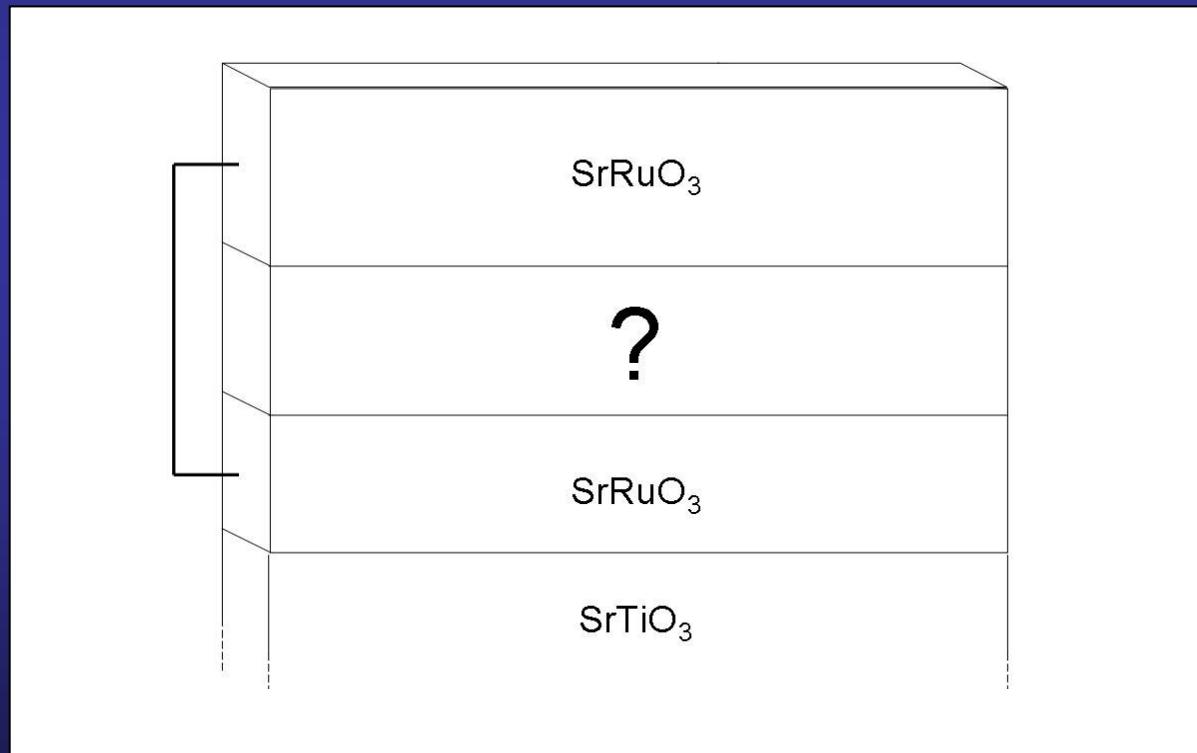
- Chosing a domain wall.
- Inducing a polarization by hand in the FE layer displacing the atoms a percentage of the bulk soft mode.



**Relaxing all the atomic coordinates,
both in the ferroelectric layer and the electrodes**

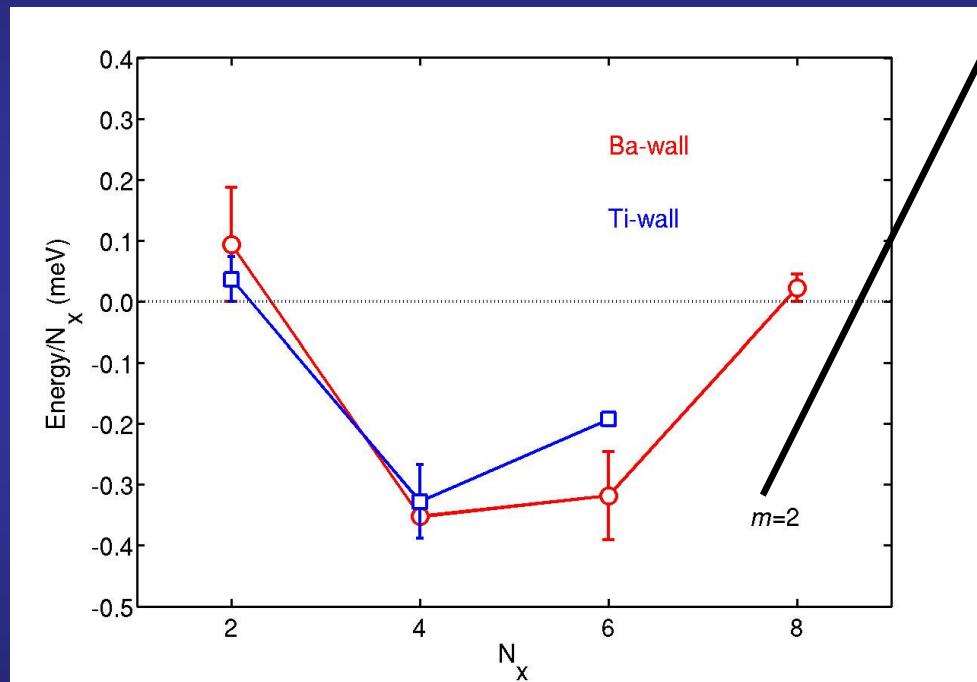
Forces smaller than 0.01 eV/Å

No constraints imposed on the atomic positions



Polydomain phases more stable than paraelectric structure for $2 < N_x < 8$

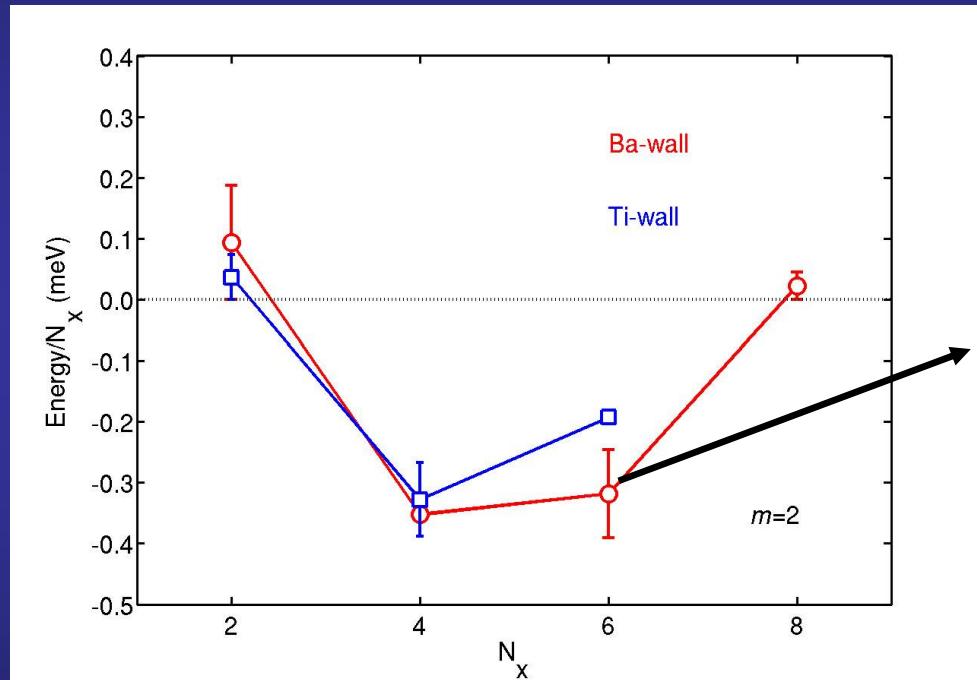
2-unit-cells thick BaTiO₃ layer



Polar domains stabilized below critical thickness for the monodomain configuration

Polydomain phases more stable than paraelectric structure for $2 < N_x < 8$

2-unit-cells thick BaTiO₃ layer

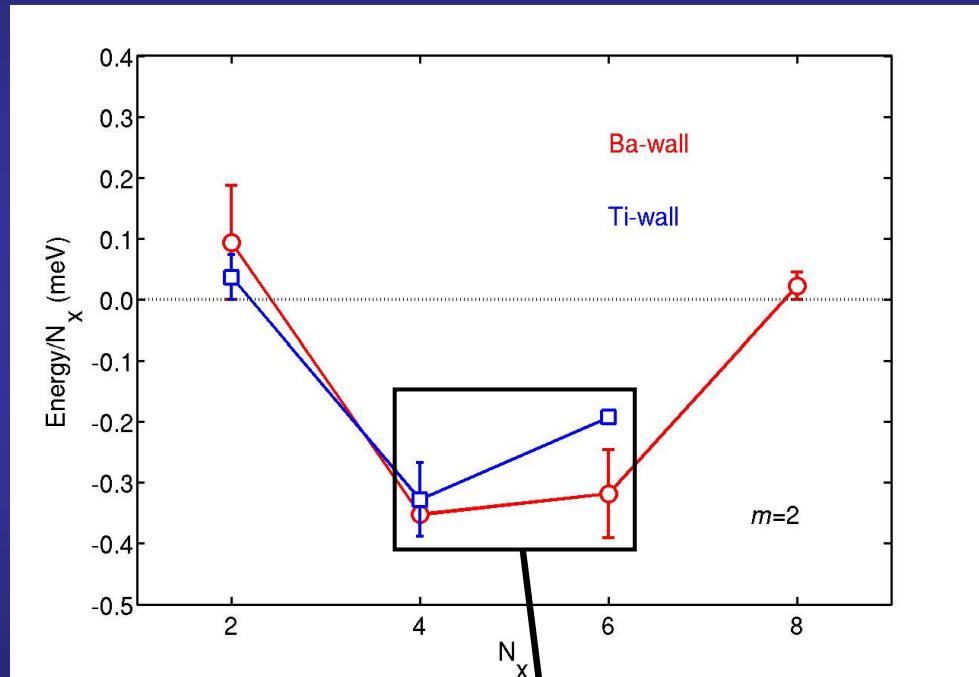


Polar domains stabilized below critical thickness for the monodomain configuration

As 180° domains in bulk,
Ba centered domain wall preferred

Polydomain phases more stable than paraelectric structure for $2 < N_x < 8$

2-unit-cells thick BaTiO₃ layer



Polar domains stabilized below critical thickness for the monodomain configuration

As 180° domains in bulk,
Ba centered domain wall preferred

No energy difference between $N_x = 4$ and $N_x = 6$

Both of them might be equally present in an sample

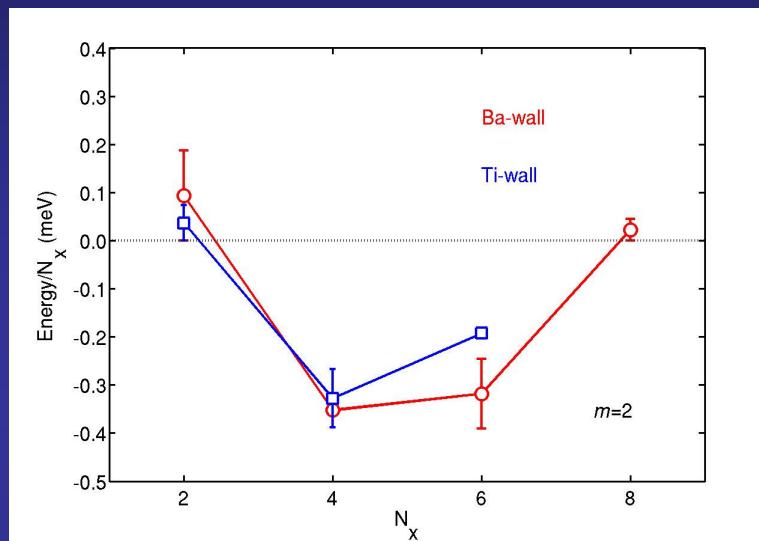
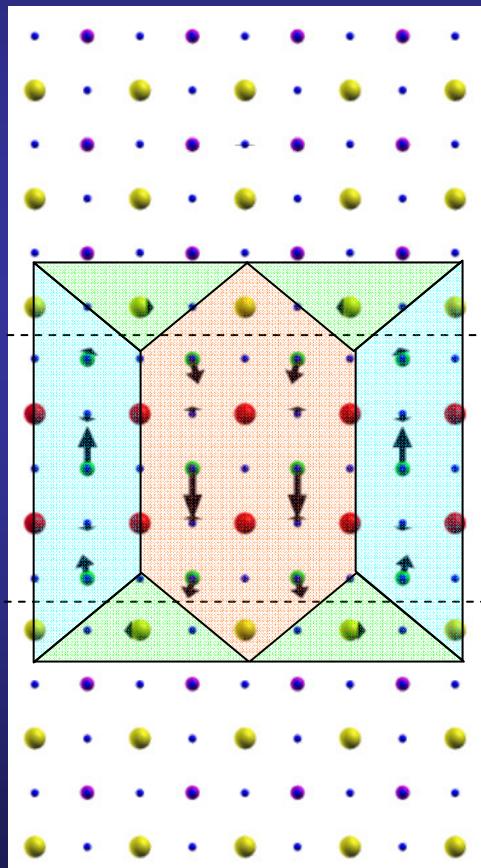
(α and β phases in PbTiO₃/SrTiO₃ interfaces?)

D. D. Fong *et al.*, Science 304, 1650 (2004)

Polydomain phases adopt the form of a “domain of closure”, common in ferromagnets

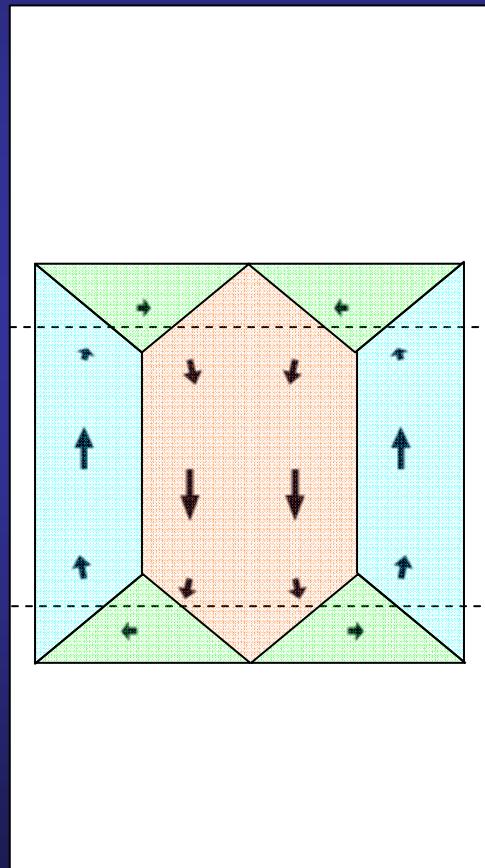
$N_x = 4$

BaO domain walls

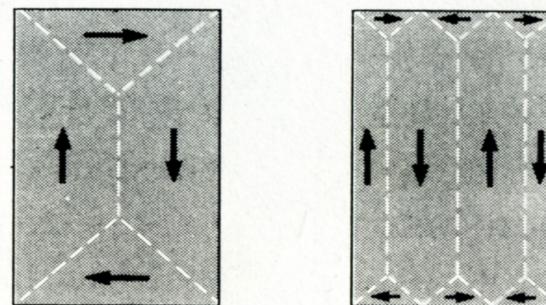


$N_x = 4$

BaO domain walls

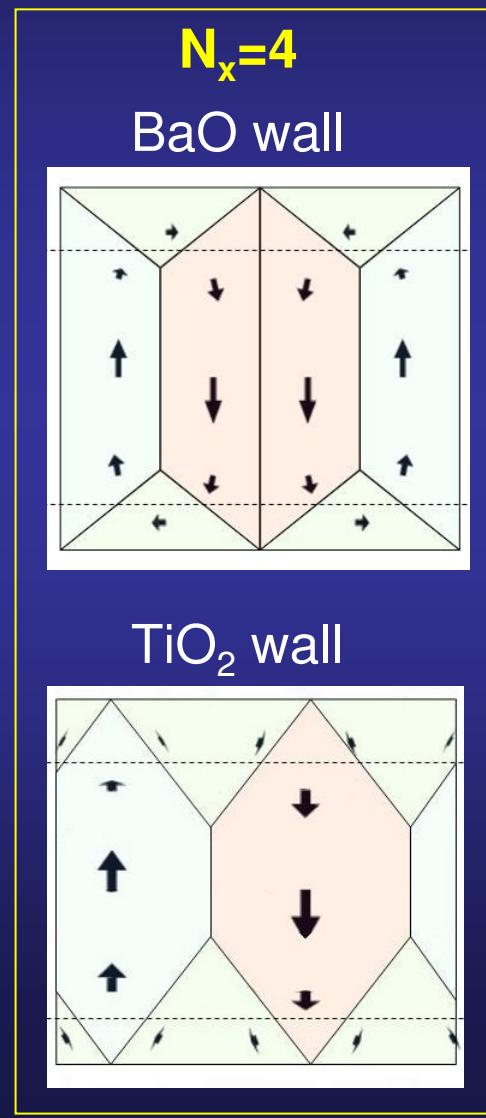


Ferromagnetic domains

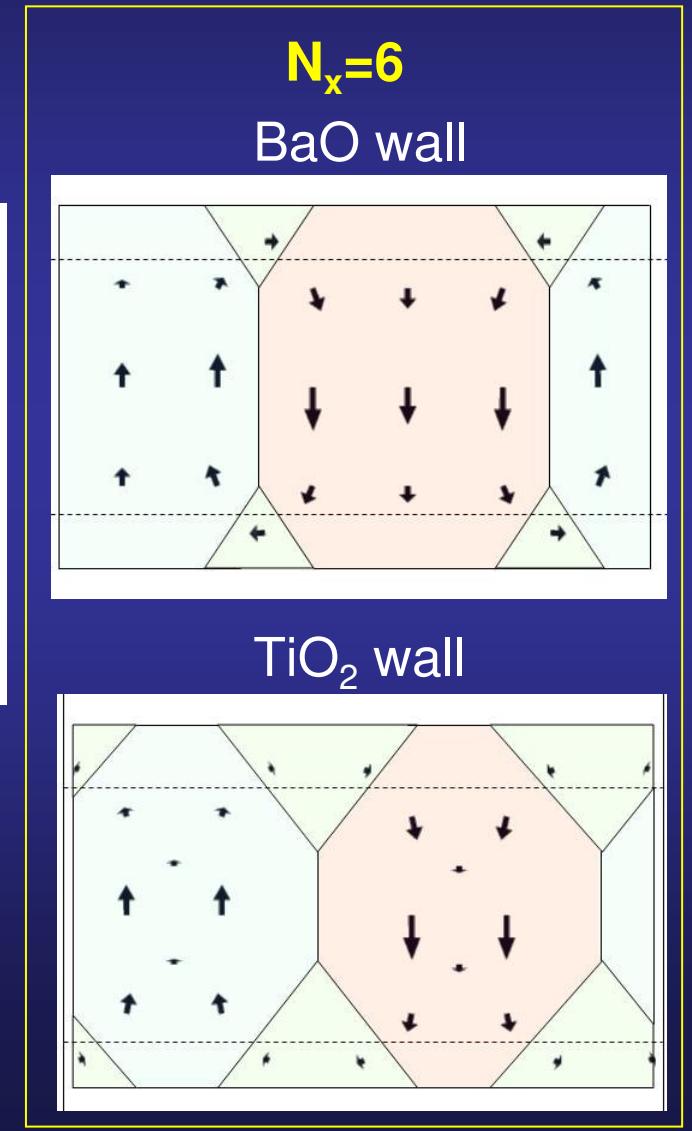
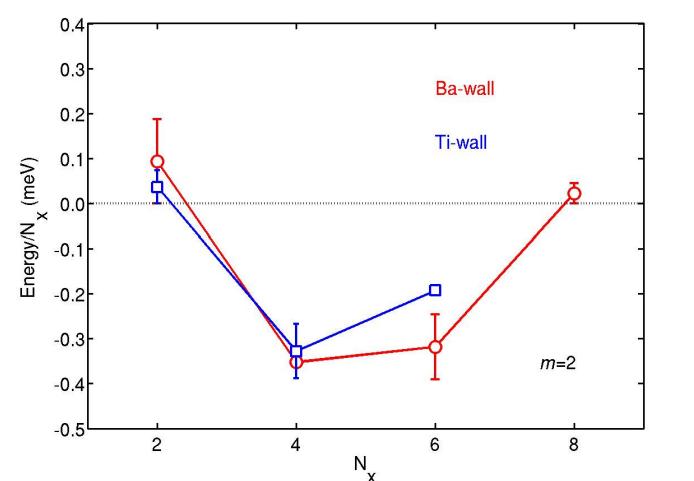


C. Kittel (1946)

Polydomain phases adopt the form of a “domain of closure”, common in ferromagnets

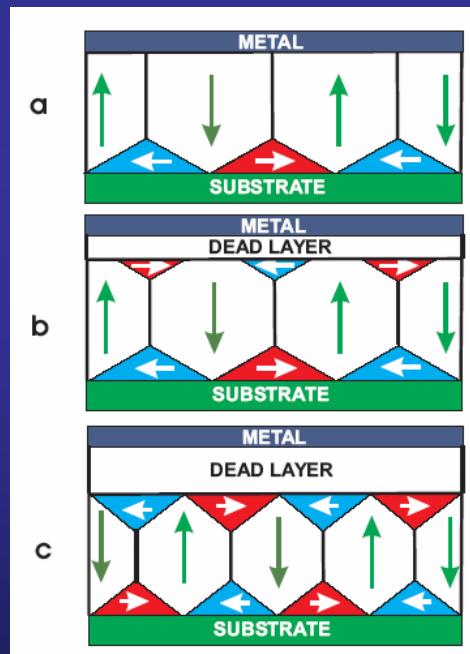


2-unit-cells thick BaTiO₃ layer



Domains of closure recently predicted using a model hamiltonian approach

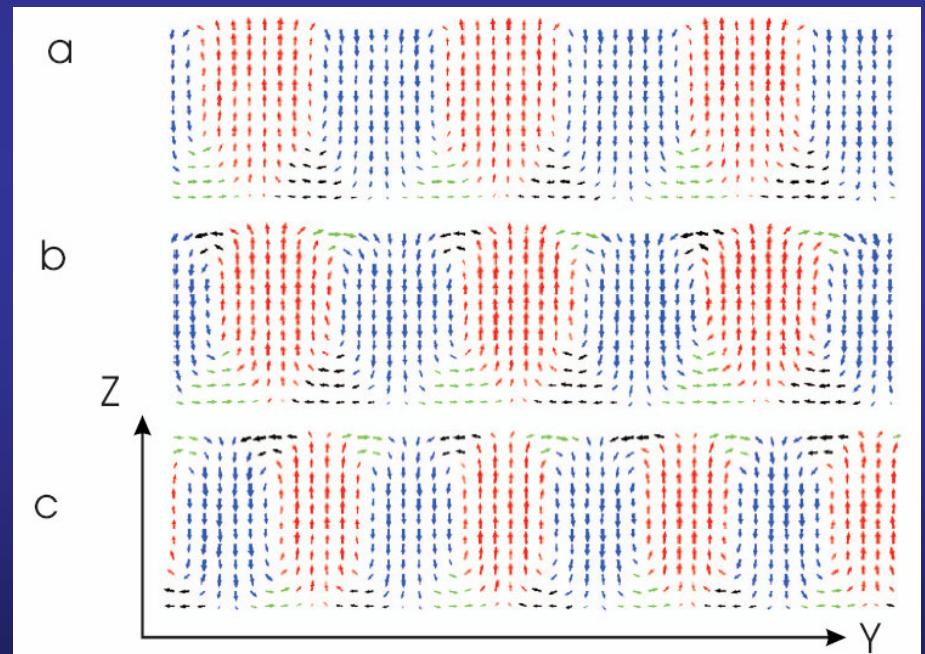
48 Å thick $\text{PbZr}_{0.4}\text{Ti}_{0.6}\text{O}_3$ thin films
sandwiched with a nongrounded metallic plate (top) and a non-conductive substrate (bottom)



$d = 0$

$d = 0.3 a$

$d = 0.5 a$

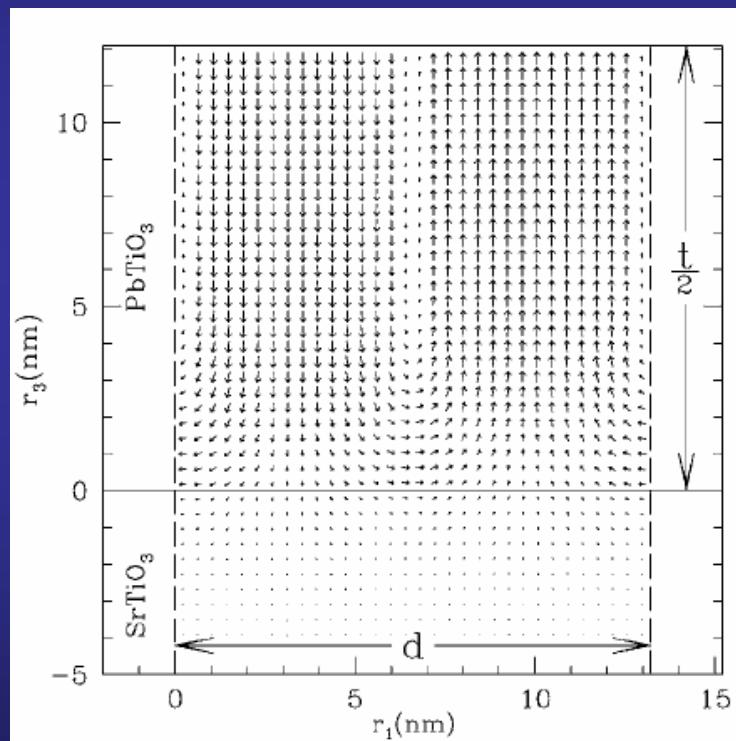


Dead layer thickness

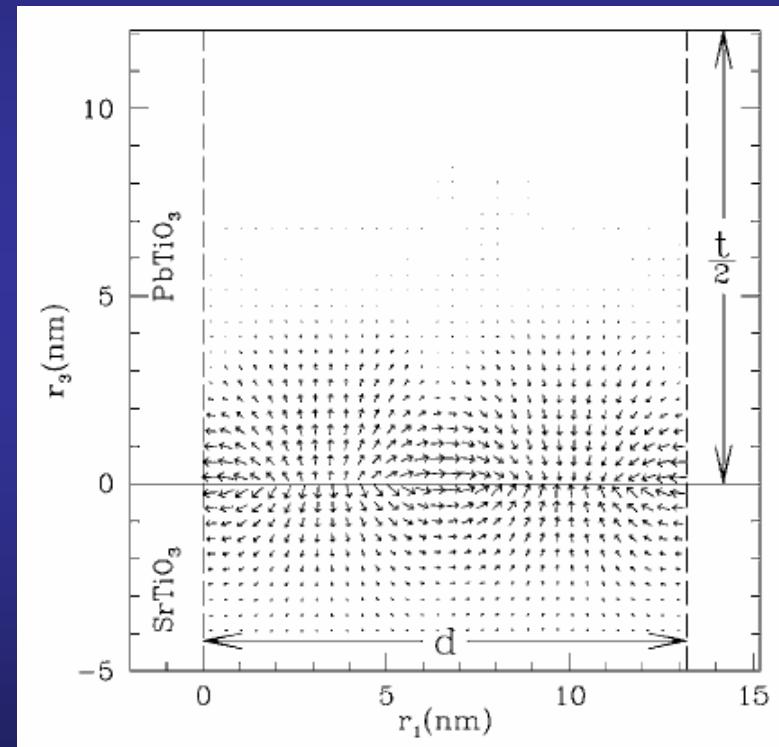
S. Prosandeev and L. Bellaiche, Phys. Rev. B 75, 172109 (2007)

Domains of closure recently predicted using a phenomenological thermodynamic potential

242 Å thick PbTiO_3 thin films
sandwiched with a nonconducting SrTiO_3 electrodes @ 700 K
stripe period 132 Å



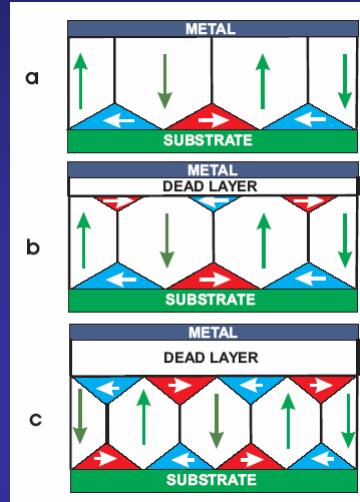
Polarization distribution



Equilibrium field distribution

Full first-principles simulations: the domains of closure structure is more general than expected

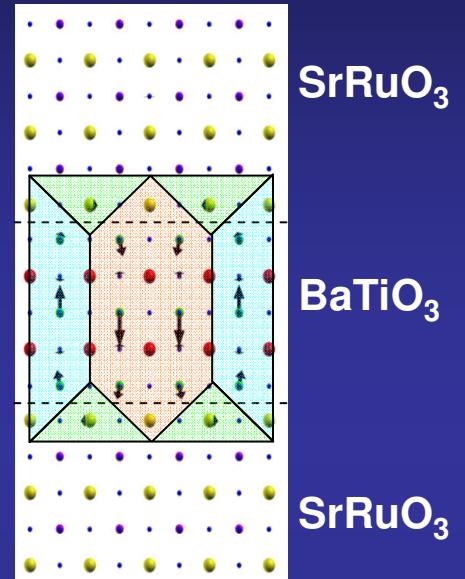
Domains of closure appear even with symmetric metallic electrode



Case I: SrTiO_3	Case II: Conductor	Case III: Vacuum
PbTiO_3	PbTiO_3	PbTiO_3

S. Prosandeev and L. Bellaiche,
Phys. Rev. B 75, 172109 (2007)

G. B. Stephenson and K. R. Elder,
J. Appl. Phys. 100, 051601 (2006)



This work

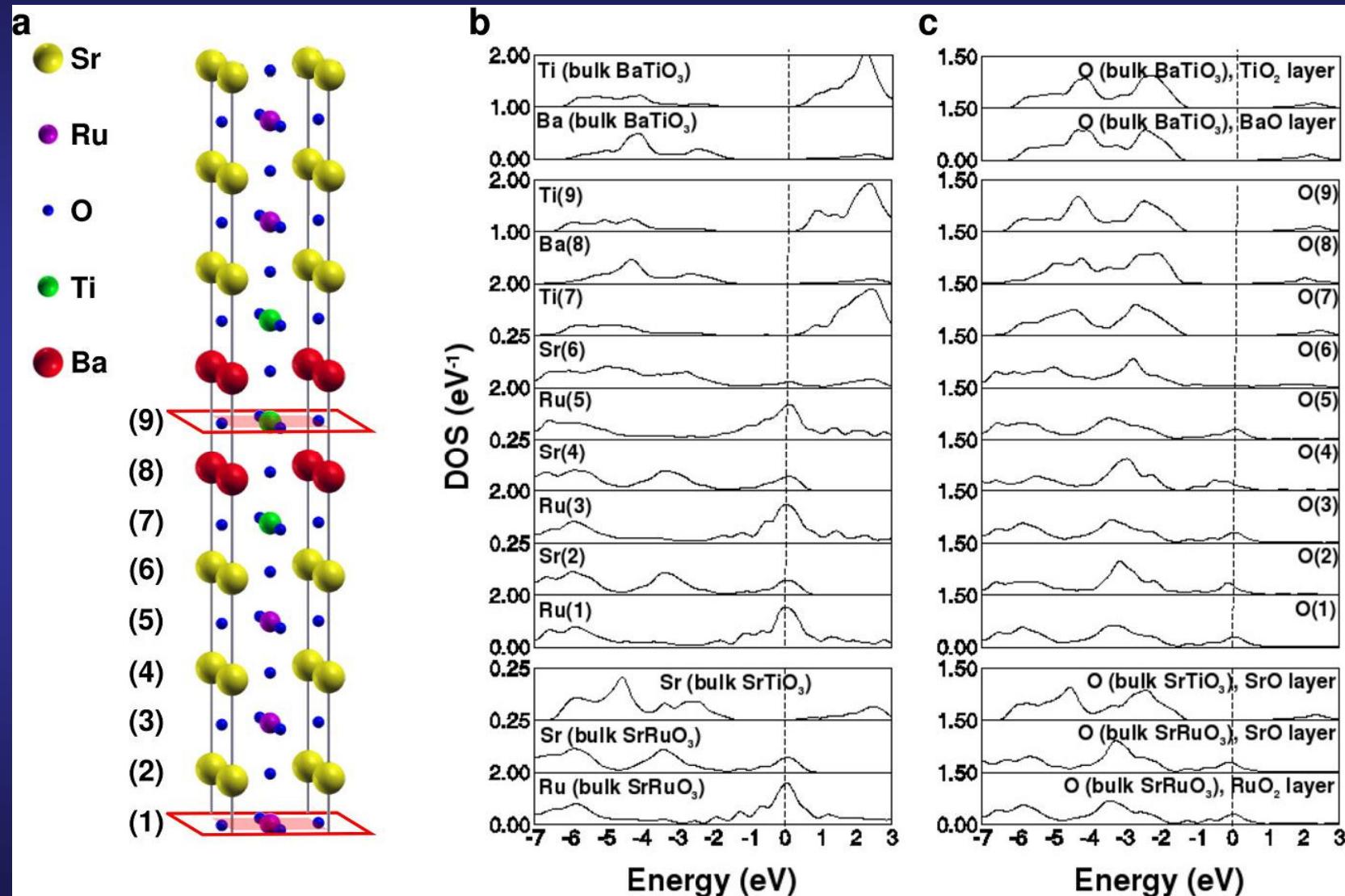
Domains of closure appear even in BaTiO_3 ferroelectric capacitors

“ BaTiO_3 profoundly dislike significantly rotating and in-plane dipole”

“ BaTiO_3 with the PZT configuration is thermodynamically unstable because it directly transforms into 180 stripe domains after a couple of Monte Carlo sweeps”

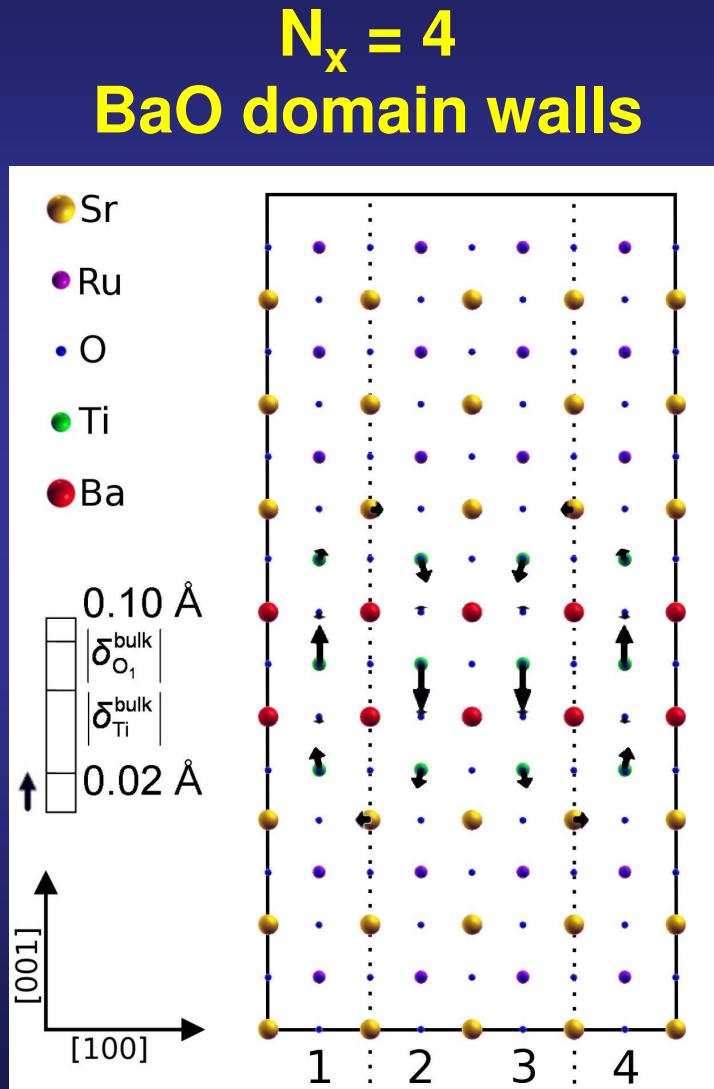
B. –K. Lai et al., Phys. Rev. B 75, 085412 (2007)

SrO layer at the interface behaves more like SrTiO₃ than SrRuO₃ \Rightarrow highly polarizable

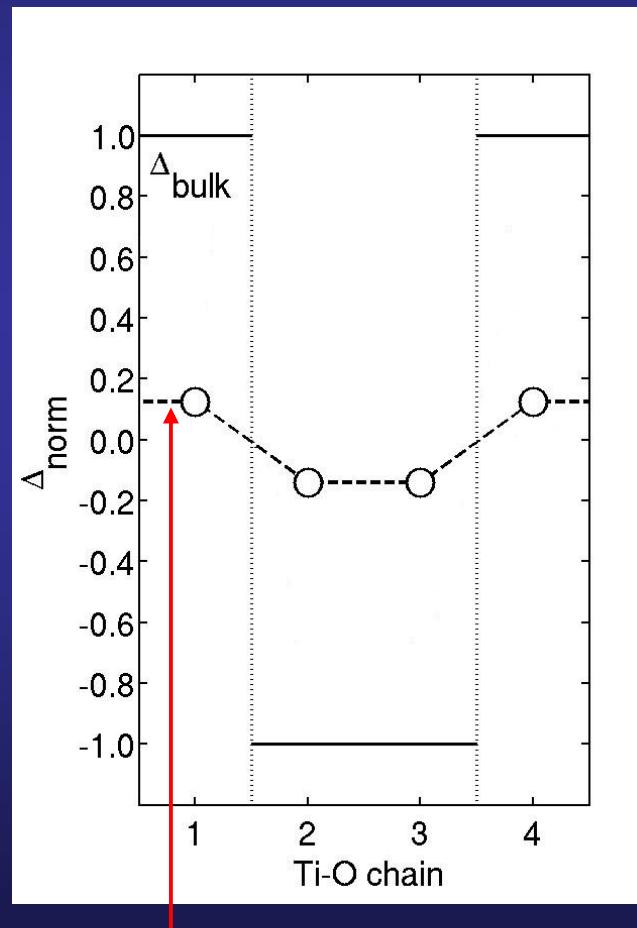


Projected Density of States in the reference paraelectric structure

Resulting phases show in-plane displacements and small polarization



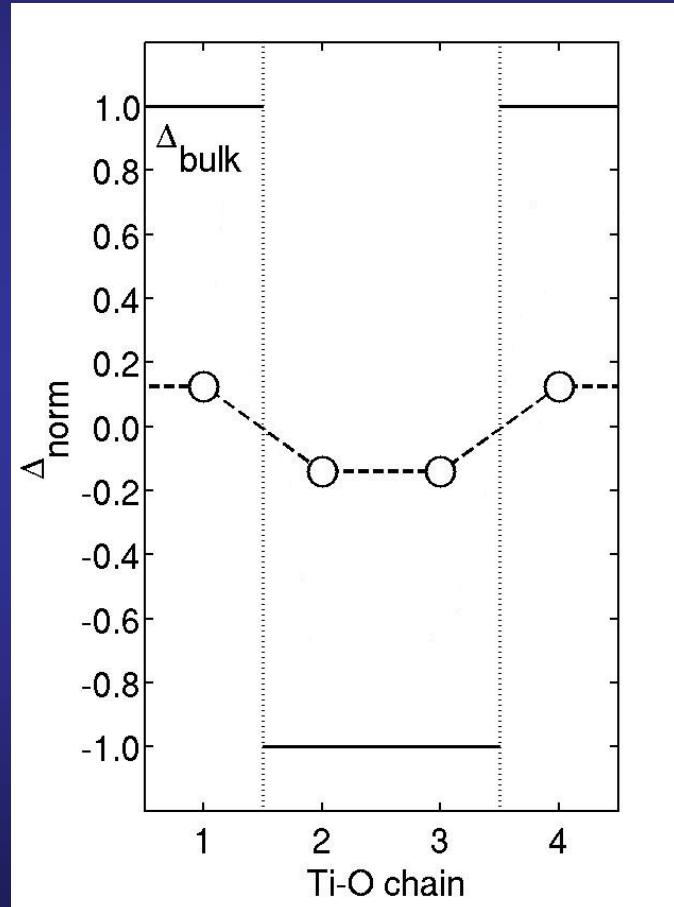
Small polarization inside the domains



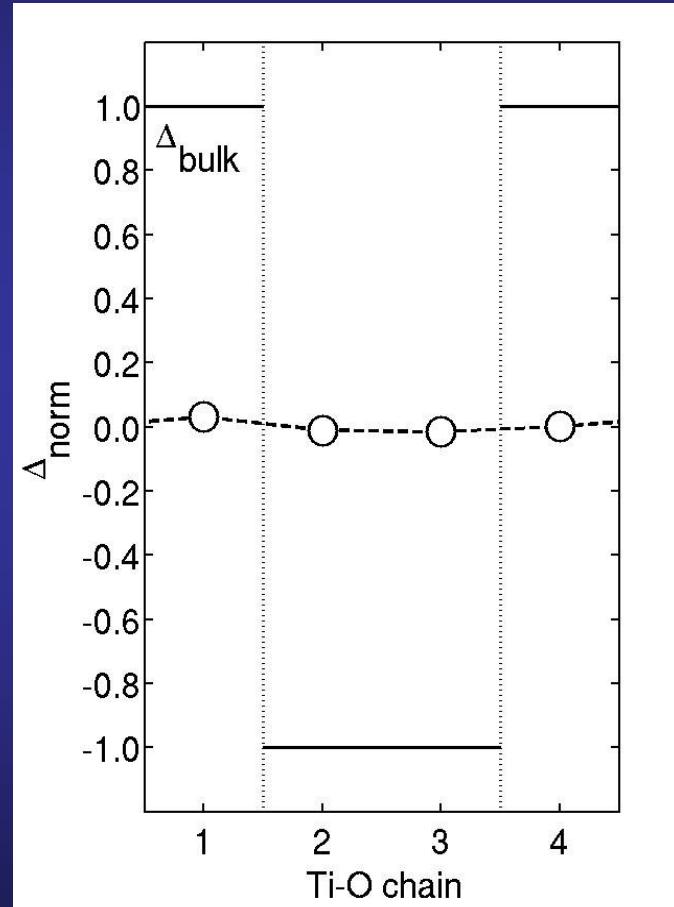
About 1/10 of bulk soft-mode polarization

In-plane displacements are very important to stabilize the domains

In-plane displacements: ON

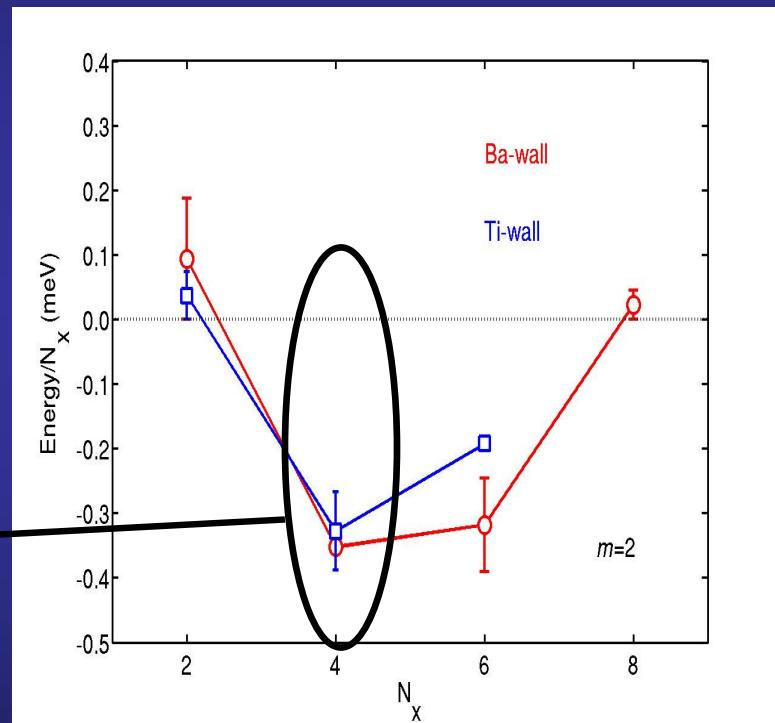
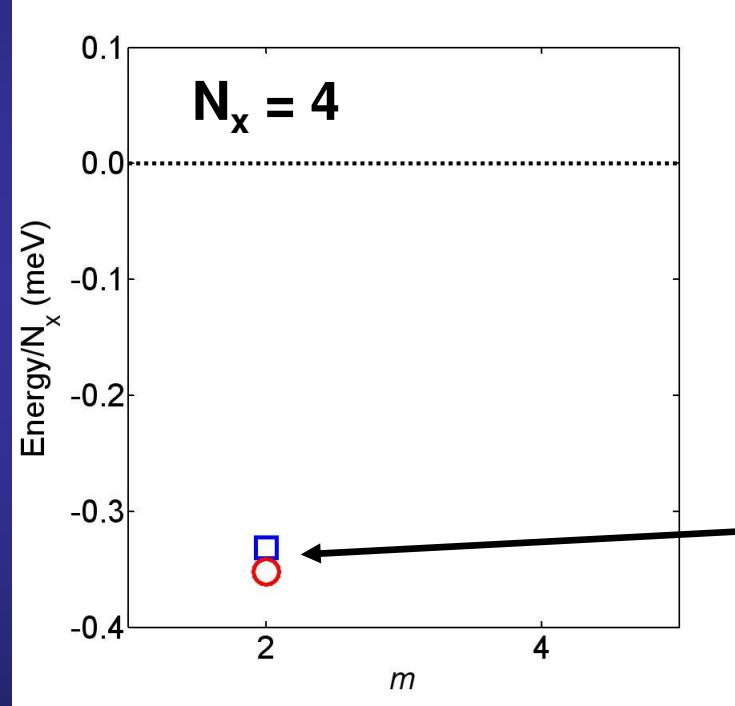


In-plane displacements: OFF

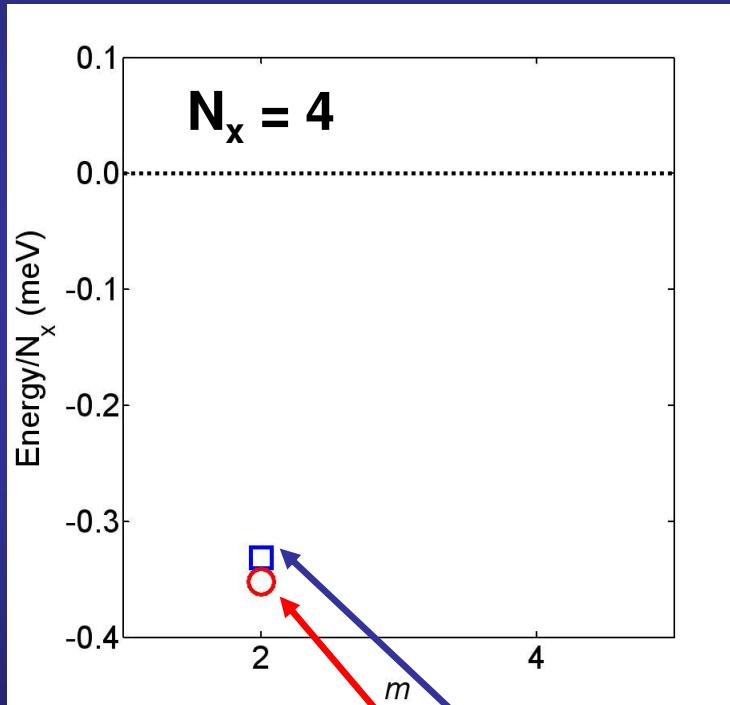


**When in-plane coordinates are fixed,
structure goes back to the paraelectric phase**

Relevant energy differences very small in the ultrathin $m = 2$ capacitors



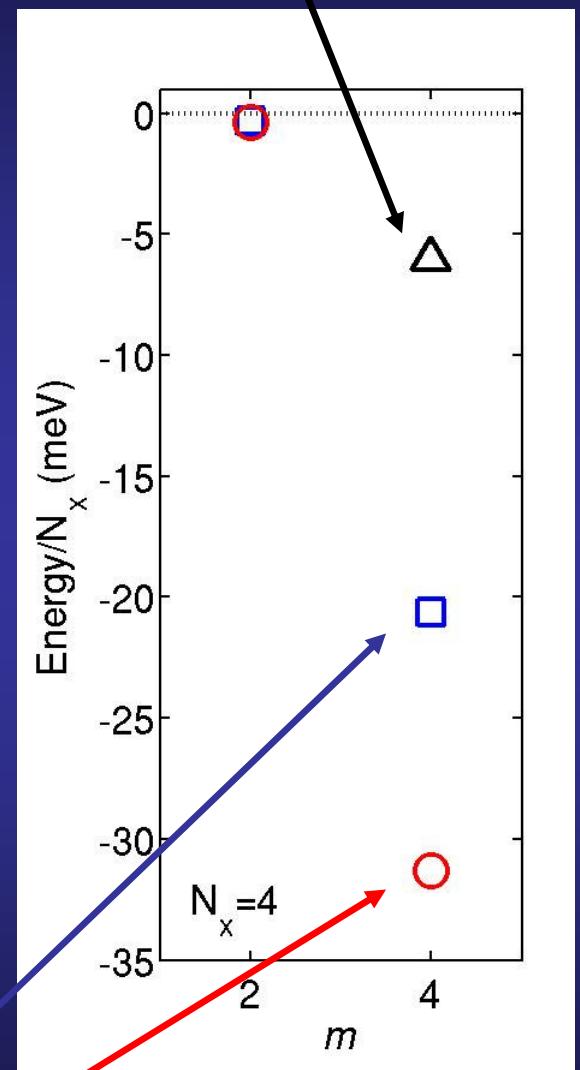
Relevant energy differences increase with thickness



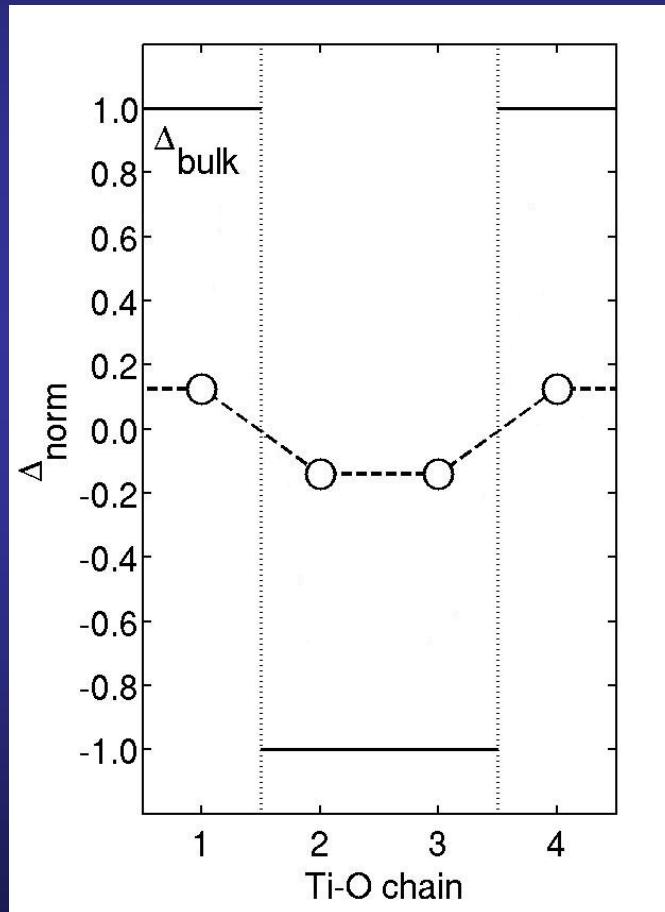
Ti-centered domains

Ba-centered domains

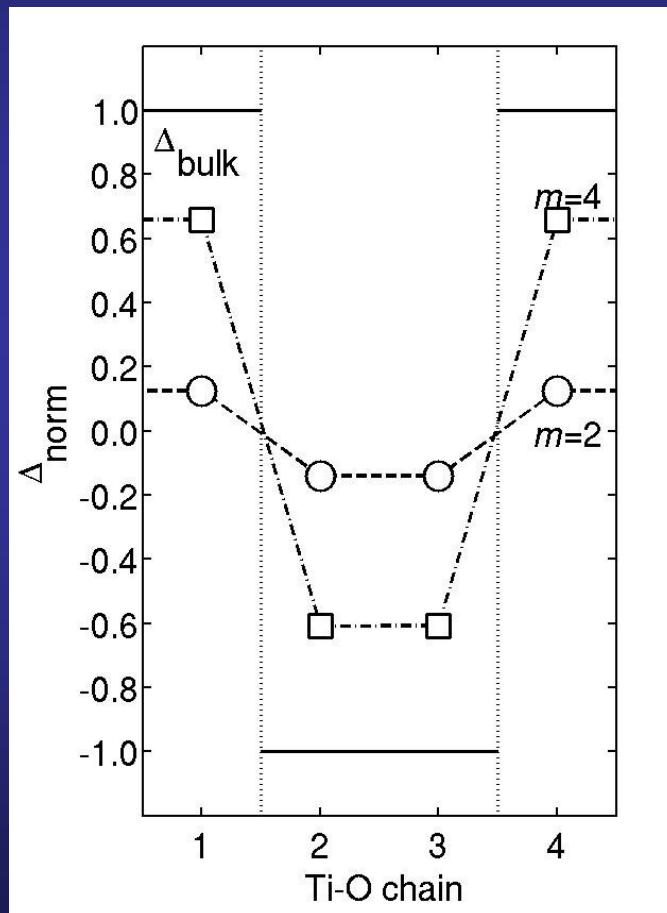
Monodomain



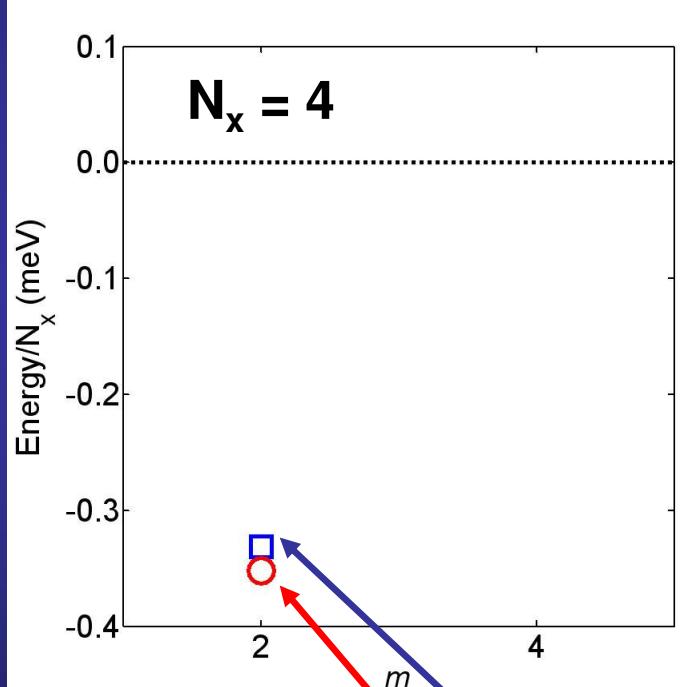
Transition from vortices to standard 180° domains. 4-unit-cell thick layer, great increase in polarization



Transition from vortices to standard 180° domains. 4-unit-cell thick layer, great increase in polarization



In-plane displacements, contribute to stabilize domains

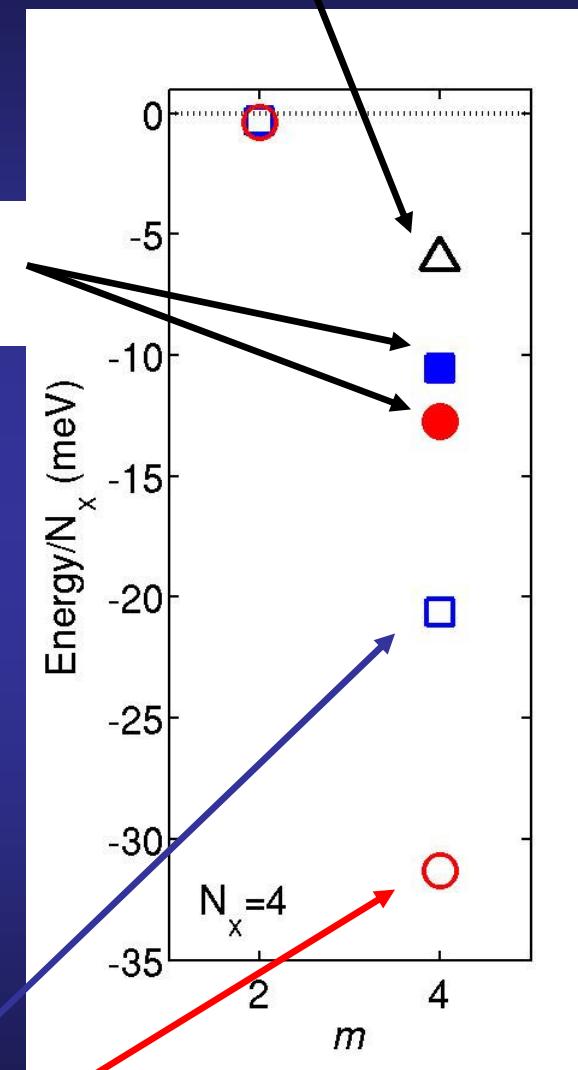


In-plane
constraint

Ti-centered domains

Ba-centered domains

Monodomain

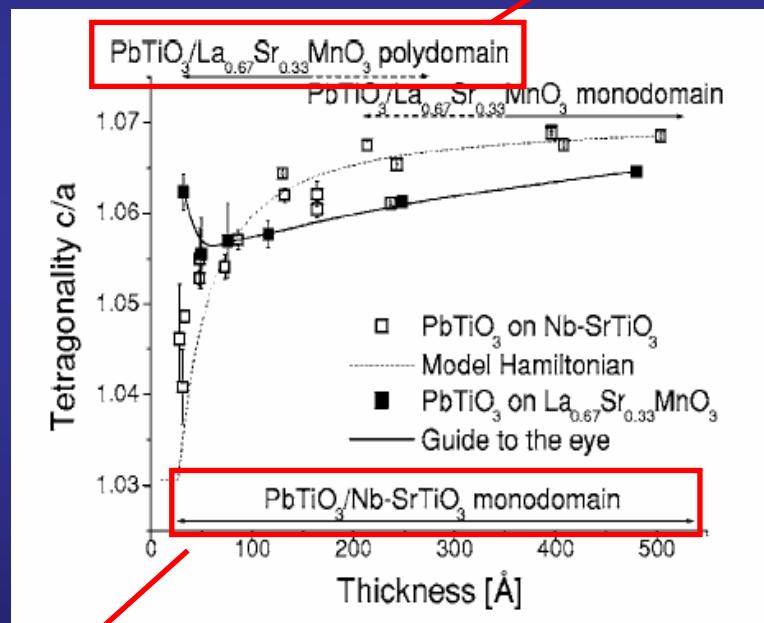


Changing the electrode, the ground state of PbTiO_3 changes from monodomain to polydomain

APPLIED PHYSICS LETTERS 90, 052907 (2007)

Monodomain to polydomain transition in ferroelectric PbTiO_3 thin films with $\text{La}_{0.67}\text{Sr}_{0.33}\text{MnO}_3$ electrodes

Lichtensteiger, et al.



PRL 94, 047603 (2005)

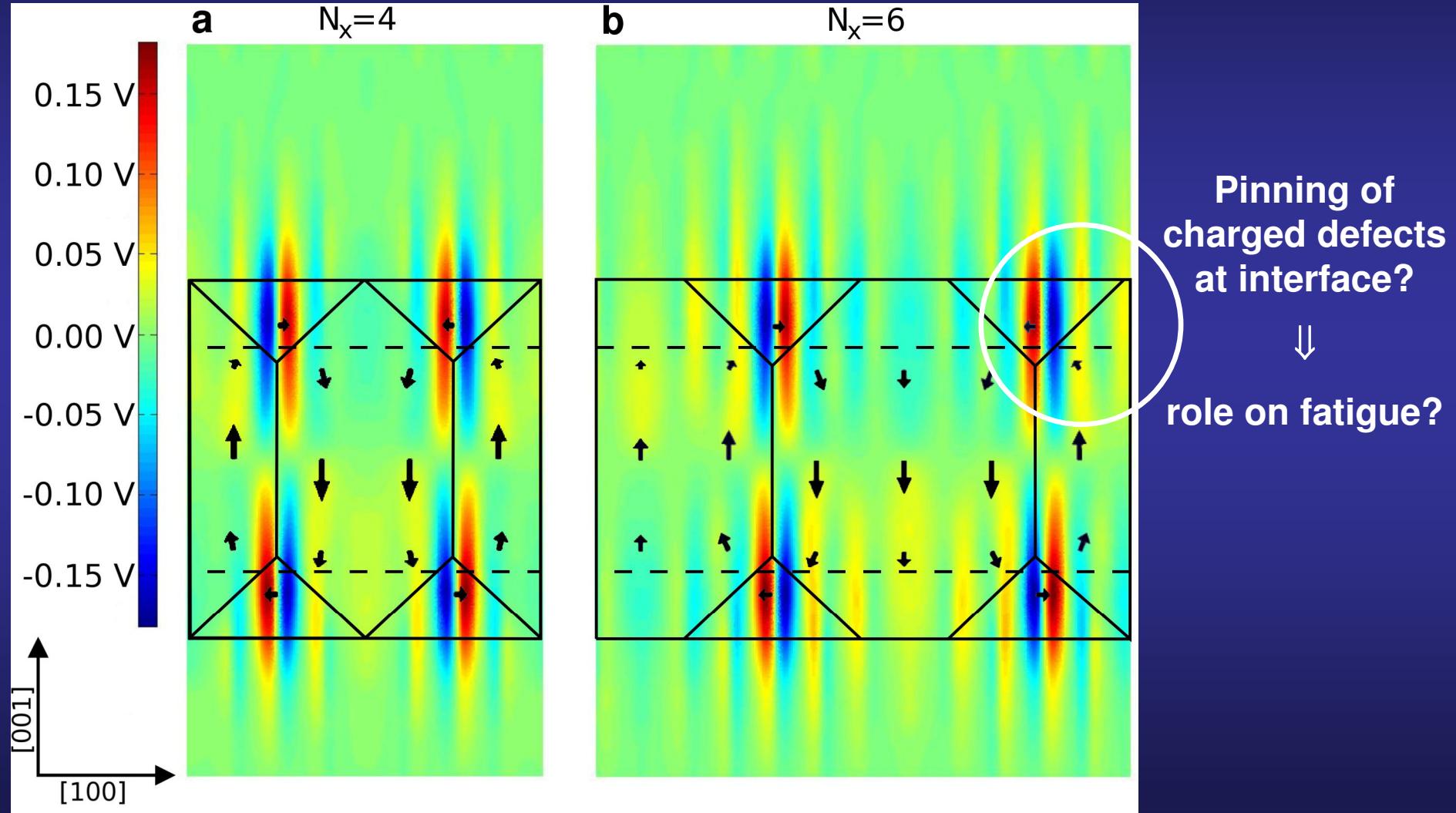
PHYSICAL REVIEW LETTERS

week ending
4 FEBRUARY 2005

Ferroelectricity and Tetragonality in Ultrathin PbTiO_3 Films

Lichtensteiger, Triscone, Junquera, Ghosez.

Analysis of the electrostatic potential: large field in x at the interface, residual depolarizing field in z



Two unit cells thick of BaTiO_3

Preliminary results on $\text{SrRuO}_3/\text{PbTiO}_3/\text{SrRuO}_3$
 $m = 2, N_x = 6$ remain paraelectric

Good agreement with experiment

Ferroelectricity in Ultrathin Perovskite Films

Dillon D. Fong,¹ G. Brian Stephenson,^{1*} Stephen K. Streiffer,¹
Jeffrey A. Eastman,¹ Orlando Auciello,¹ Paul H. Fuoss,¹
Carol Thompson²

At 1

and 2 unit cells, no satellites are observed at any temperature, indicating that the samples remain in the paraelectric phase.

Conclusions

- Many effects affect the delicate balance between short and long range forces in thin films:

Surface

Mechanical (epitaxial strain)

Electrical (depolarizing field)

Chemical

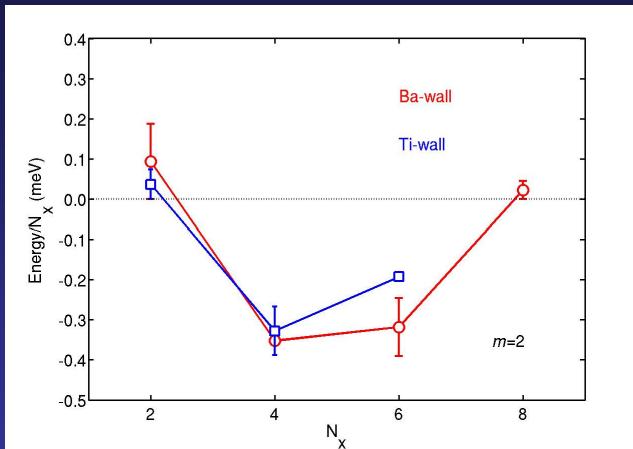
- As a result of the different interactions, wealthy of phase diagrams
- The question of suppression of ferroelectricity in ultrathin films cannot be answered in general but, instead, must be addressed independently for each individual system.

Slides available at: <http://personales.unican.es/junqueraj>

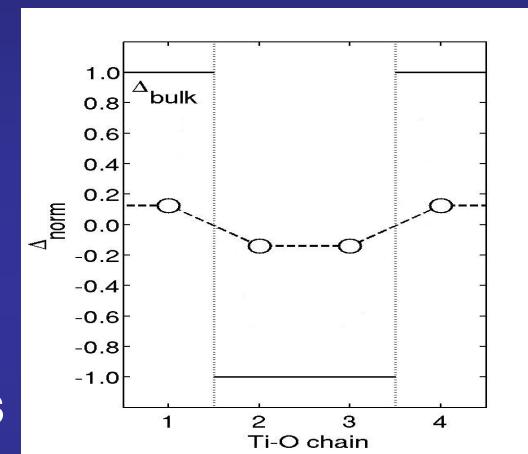
Contact: pablo.aguado@unican.es

javier.junquera@unican.es

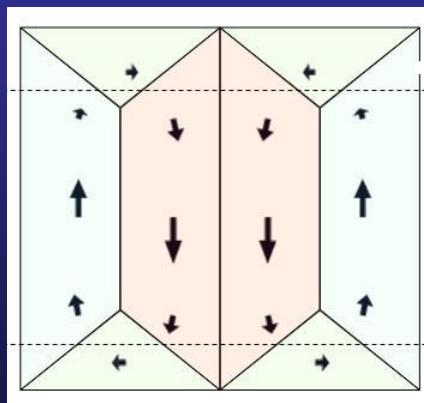
Conclusions



- Polydomain phases in ultrathin FE films are stabilized below critical thickness in monodomain configurations.



- The chemical interaction through the interface is an essential factor since it affects the in-plane mobility of the atoms.



Polydomains phases have a structure: Closure domains

Slides available at: <http://personales.unican.es/junqueraj>

Contact: pablo.aguado@unican.es

javier.junquera@unican.es

Preprint available in cond-mat 0710.1515

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Philippe Ghosez



Alberto García



Experimental collaborators

Céline Lichtensteiger, Jean-Marc Triscone



Valanoor Nagarajan, R. Ramesh

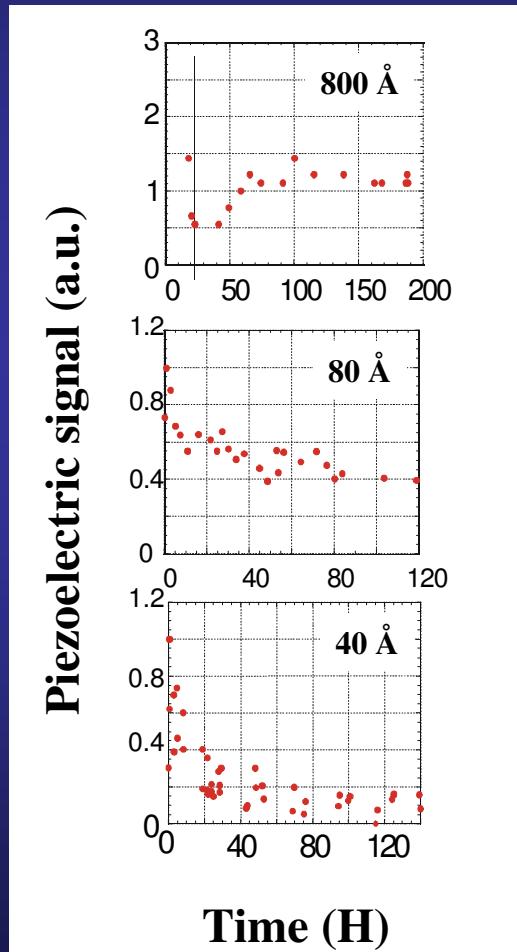


More information ...

Size effects in ferroelectrics

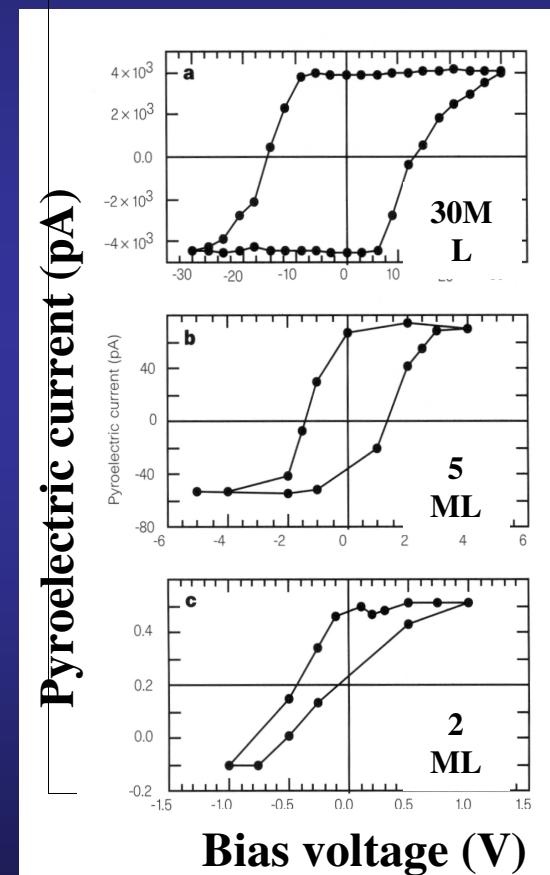
Two works that challenged the standard viewpoint

10 unit-cells thick
 $\text{Pb}(\text{Zr}_{0.2}\text{Ti}_{0.8})\text{O}_3$



Th. Tybell, Ch. Ahn and J.-M. Triscone
Appl. Phys. Lett. 75, 856 (1999)

2 monolayers thick
random copolymer



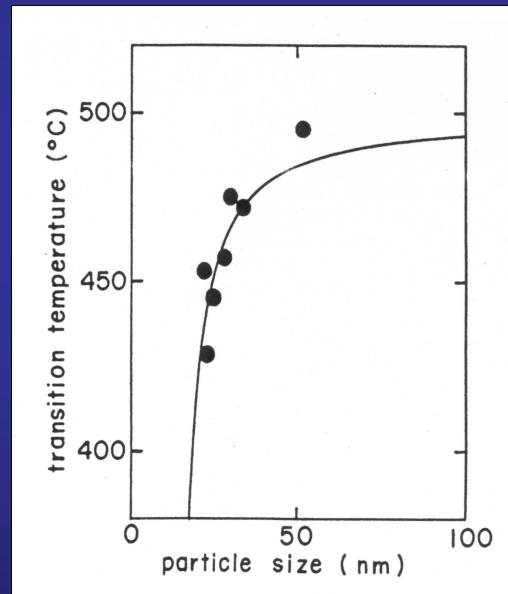
A.V. Bune et al.
Nature 391, 874 (1998)

Size effects in ferroelectrics

Standard view until the end of the nineties

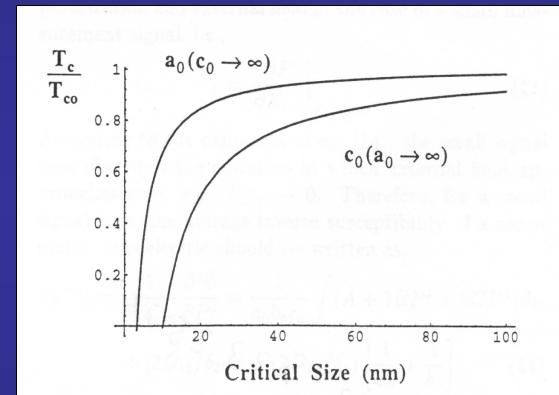
PbTiO₃ ultrafine particles

Experiment



ABO₃ ultrathin films

Anisotropic mean-field calculations



Critical thickness :

Pb(Zr_{0.5}Ti_{0.5})O₃:~ 200Å @ RT

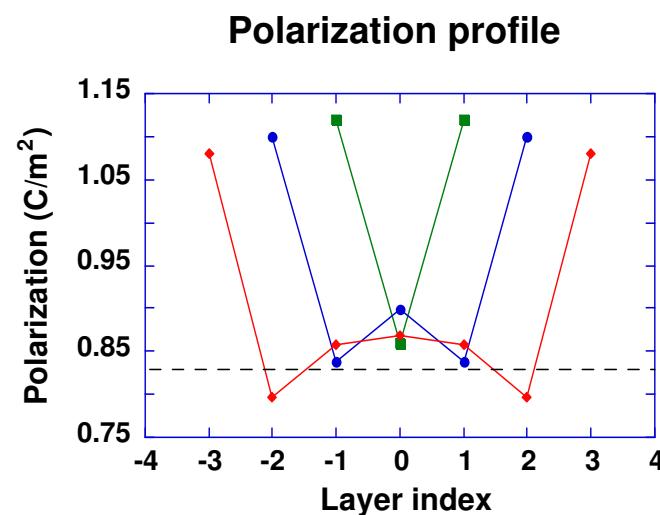
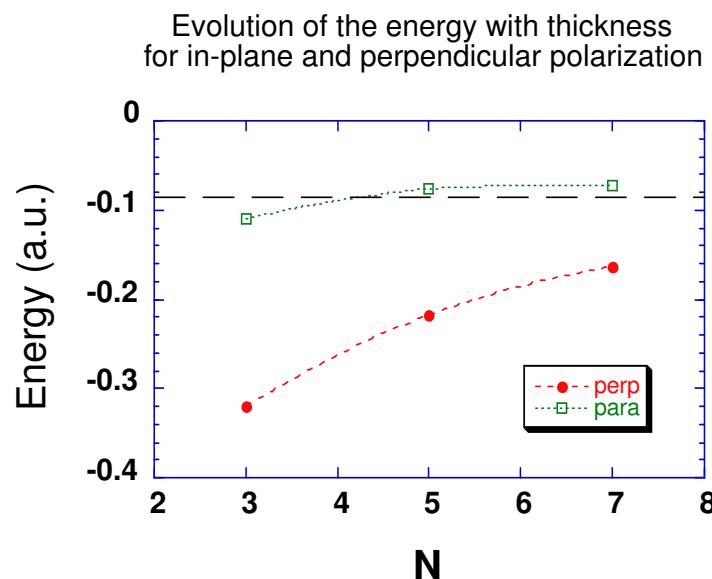
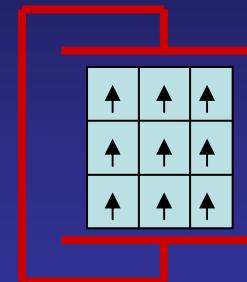
PbTiO₃ : ~ 80Å @ RT

K. Ishikawa, K. Yoshikawa, and N. Okada,
Phys. Rev. B 37, 5852 (1988)

S. Li et al.
Jpn. J. Appl. Phys. 36, 5169 (1997)

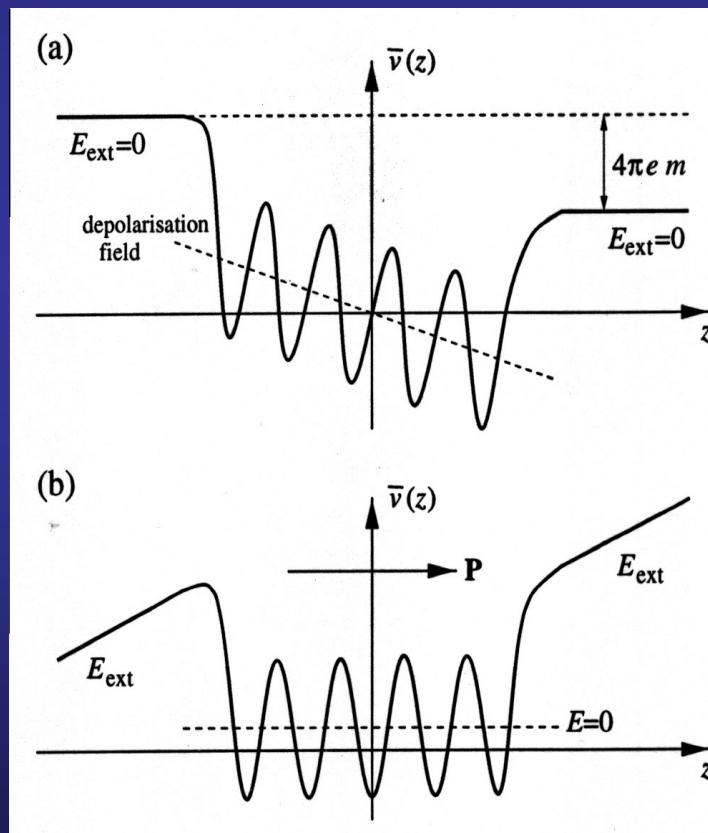
First-principles simulations on ferroelectric thin films model Hamiltonian approaches

PbTiO₃ free standing slabs under stress free and short-circuit boundary conditions are ferroelectric



First-principles simulations on ferroelectric thin films full first-principles simulations

BaTiO₃ and PbTiO₃ free-standing slabs
under external electric fields to screen
the depolarizing field



B. Meyer and D. Vanderbilt,
Phys. Rev. B 63, 193201 (2001)

